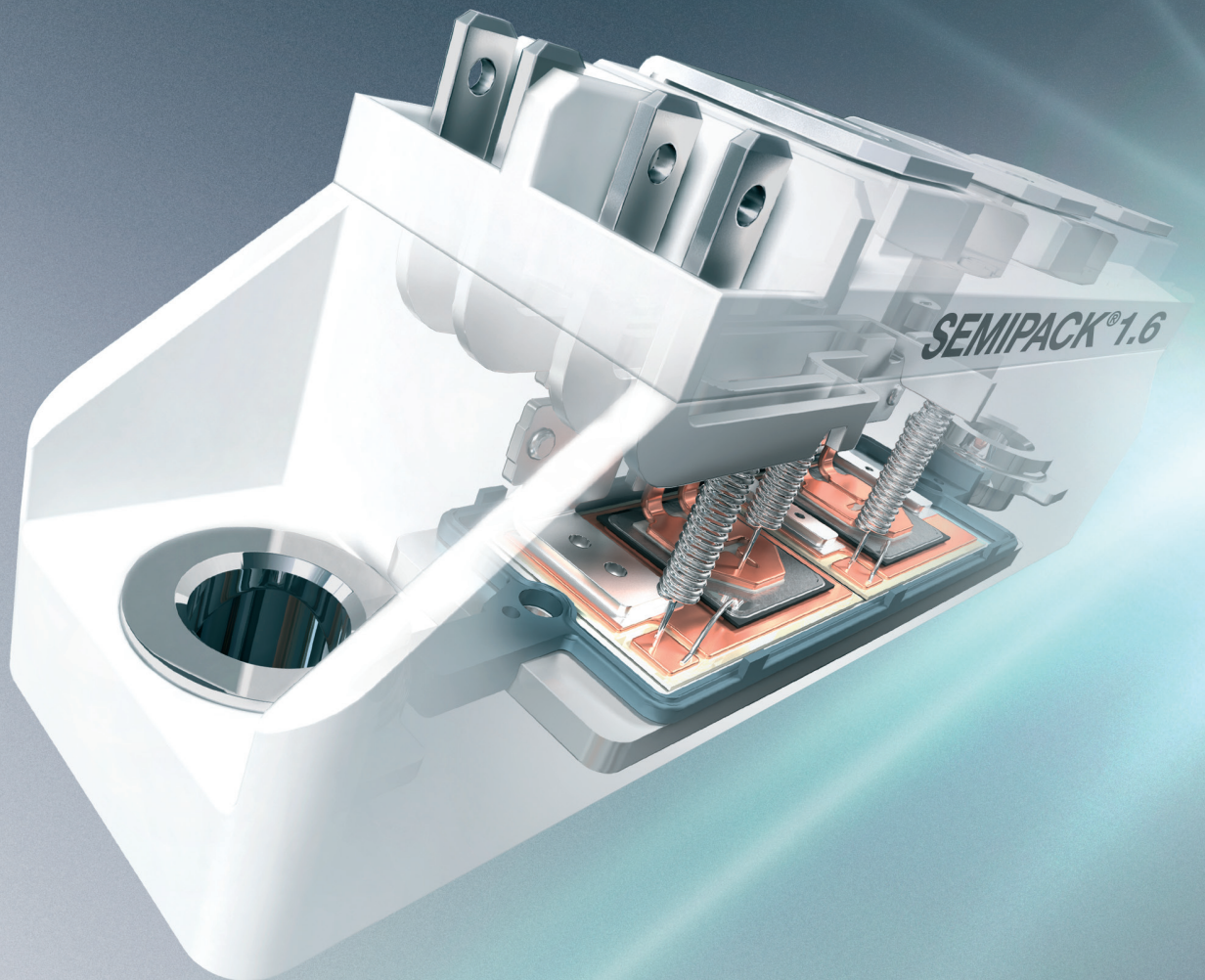


Catalogue 2013 / 2014



More than 60 years of experience in the field of power electronics, a comprehensive portfolio of chips, solutions and inverter systems, a global network of production plants and sales offices as well as our highly qualified staff – these are our success factors. SEMIKRON's power electronics components and systems primarily address the medium and high performance segment (approx. 1 kW up to 10 MW). Applications include speed-controlled industrial drive units, automation technology, welding equipment and elevators. Other applications include uninterrupted power supply (UPS), renewable energies (wind, solar) as well as electrification of commercial vehicles, conveyances, sports cars and material handling.

Note:

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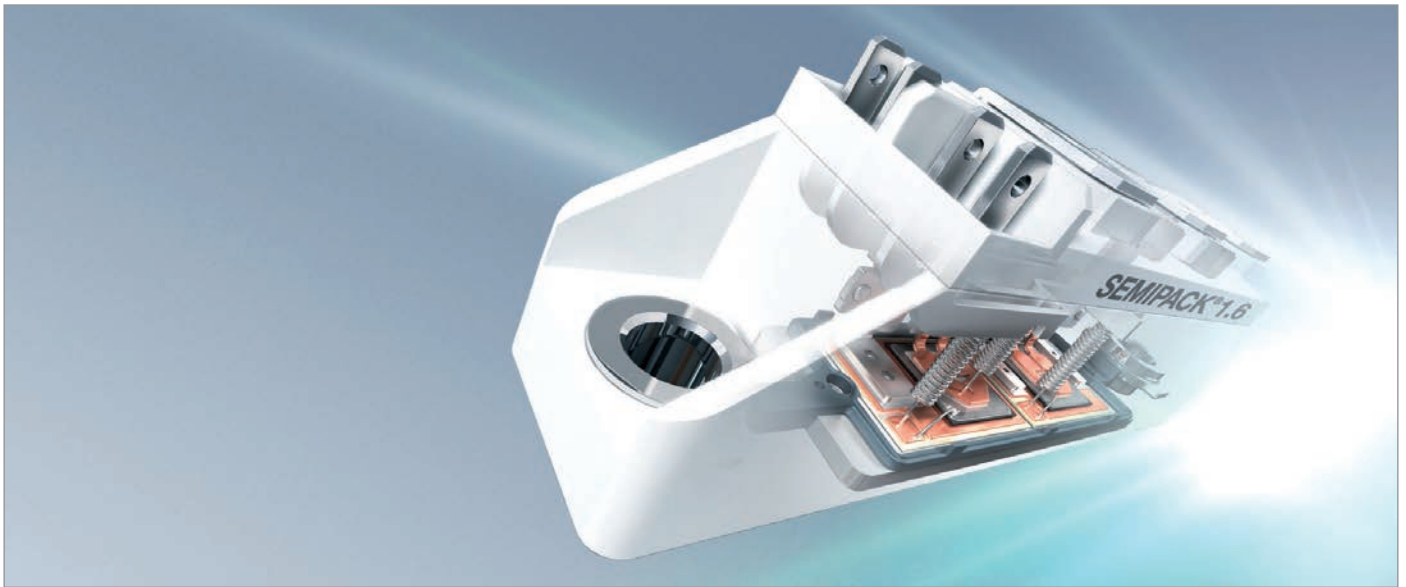
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Title: SEMIPACK 6th generation

Comprehensive product range – industrial standard

Applications

The target applications for the thyristor, thyristor/diode or diode modules include input rectifiers (single-phase, three-phase, un-controlled, half-controlled or controlled) for frequency inverters or UPS systems, soft start applications, lighting control systems in theatres and temperature control systems in furnaces.

Product range

The SEMIPACK product line offers a comprehensive product range with seven module lines: with voltages from 800 V to 2200 V, insulation voltages of 3.6kV, 4.8 kV@1s and a current range from 15 to 1200 A. Uncontrolled, half-controlled and controlled rectifier modules are available as well as single thyristor or diode modules. Also, fast diodes come in SEMIPACK modules. Furthermore, different contact technologies - soldered contact, bonded contact or pressure contact modules - are available.

Benefits

SEMIPACK was the first insulated module on the market, and almost 40 years later, it is still state-of-the-art. It is a well-established industrial standard with regard to footprint and module outlines. Due to the comprehensive product range, the optimal solution for each application can be found. With SemiSel, the free online calculation and simulation tool for losses and temperature, the power electronic system developer is able to make the perfect power module choice.

IGBT Modules

SEMiX®

half bridge
6-pack
chopper



600V
up to
1700V

I_{Cnom} in A

0 20 40 60 80 100 300 600 900

SEMITRANS®

half bridge
6-pack
chopper
single switch



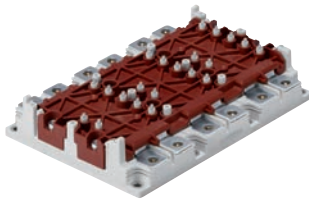
600V
up to
1700V

I_{Cnom} in A

0 20 40 60 80 100 300 600 900

SKiM®63/93

6-pack



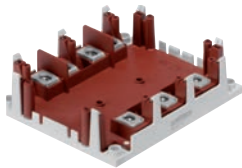
600V
up to
1700V

I_{Cnom} in A

0 20 40 60 80 100 300 600 900

SKiM®4/5

6-pack
3-level



600V
up to
1700V

I_{Cnom} in A

0 20 40 60 80 100 300 600 900

MiniSKiiP®

6-pack
3-level
H-bridge
CIB



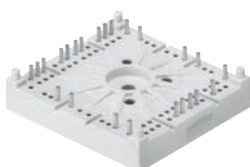
600V
up to
1200V

I_{Cnom} in A

0 20 40 60 80 100 300 600 900

SEMITOP®

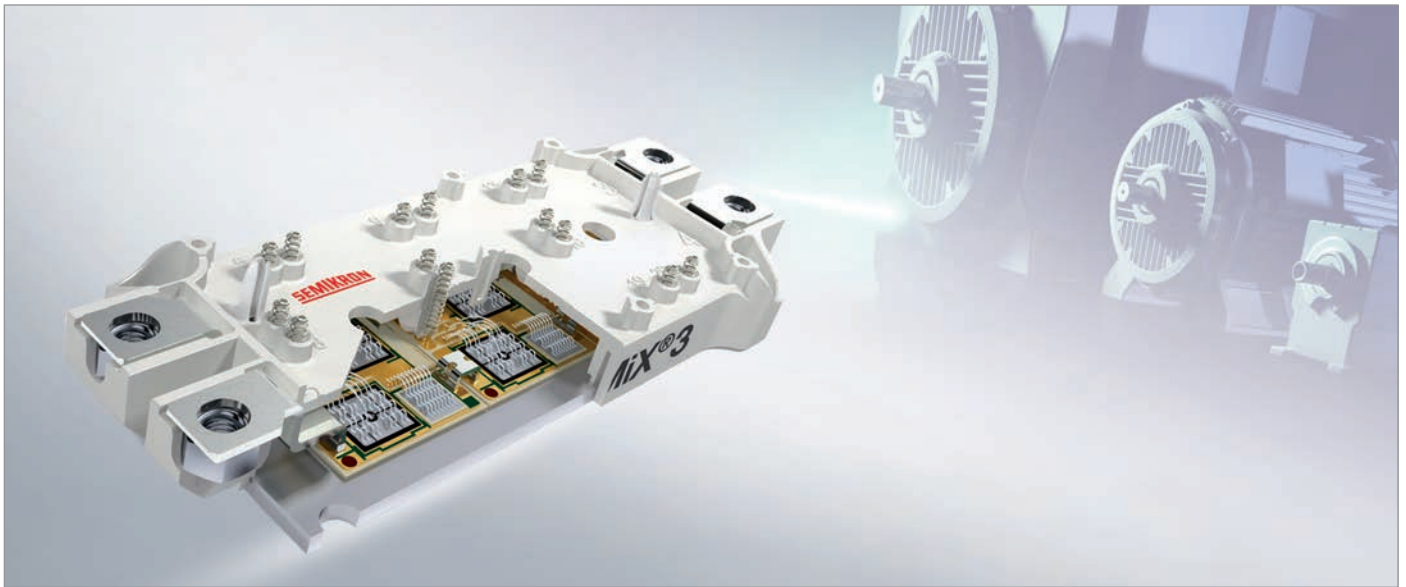
half bridge
6-pack
3-level
chopper
H-bridge
CIB



600V
up to
1200V

I_{Cnom} in A

0 20 40 60 80 100 300 600 900



IGBT and rectifier module family for solder-free assemblies

Applications

SEMIX is a flexible and application-oriented module. On the basis of a scalable platform concept, modern chip technology is integrated into IGBT and rectifier modules which are used in a wide variety of applications, such as AC motor drives, switching power supplies and current source inverters. Other typical applications include matrix converters, uninterruptible power supplies and electronic welding devices.

Product range

Six different housing sizes are available in voltage classes 600 V, 1200 V and 1700 V for the IGBT modules. Half-bridge, six-pack and chopper topologies are available for a current range from 75 A to 600 A. Besides IGBT3 and IGBT4 chips, the 1200 V range also includes a series with V-IGBT devices. Controlled, semi-controlled and uncontrolled rectifier modules with an identical footprint and 17 mm module height are also available.

Benefits

- Fast, one-directional assembly from above
- Solder-free connection to control unit using reliable spring contacts
- Separation of control unit, AC and DC terminals
- Direct driver assembly
- Same-height (17 mm) of IGBT and rectifier modules
- Flat and compact inverter design
- Optimised production at customer site
- Easy service

Modules - IGBT - SEMiX

Type	IGBT						Diode				Case		Circuit
	I_C @ $T_C=25^\circ\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_j=25^\circ\text{C}$ typ.	E_{on}	E_{off}	$R_{th(j-c)}$	I_F @ $T_C=25^\circ\text{C}$	V_F @ $T_j=25^\circ\text{C}$ typ.	E_{rr}	$R_{th(j-c)}$	Case	$R_{th(c-s)}$	
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W		K/W	
600 V - IGBT 3 (Trench)													
SEMiX402GAL066HDs	502	400	1.45	22	24	0.12	543	1.4	10	0.15	2s	0.045	
SEMiX603GAL066HDs	720	600	1.45	12	43	0.087	771	1.4	13	0.11	3s	0.04	
SEMiX402GAR066HDs	502	400	1.45	22	24	0.12	543	1.4	10	0.15	2s	0.045	
SEMiX603GAR066HDs	720	600	1.45	12	43	0.087	771	1.4	13	0.11	3s	0.04	
SEMiX202GB066HDs	274	200	1.45	6	8	0.21	291	1.4	6.5	0.27	2s	0.045	
SEMiX302GB066HDs	379	300	1.45	11.5	15	0.16	419	1.4	7.5	0.19	2s	0.045	
SEMiX402GB066HDs	502	400	1.45	22	24	0.12	543	1.4	10	0.15	2s	0.045	
SEMiX603GB066HDs	720	600	1.45	12	43	0.087	771	1.4	13	0.11	3s	0.04	
SEMiX101GD066HDs	139	100	1.45	3	4	0.41	151	1.4	4.5	0.51	13	0.04	
SEMiX151GD066HDs	200	150	1.45	3.8	6.1	0.29	219	1.4	5.8	0.36	13	0.04	
SEMiX201GD066HDs	259	200	1.45	5	8	0.23	284	1.4	7.5	0.28	13	0.04	
1200 V - V-IGBT													
SEMiX151GAL12Vs ¹⁾	231	150	1.75	19.4	17.1	0.19	189	2.1	11.5	0.31	1s	0.075	
SEMiX151GB12Vs	231	150	1.75	19.4	17.1	0.19	189	2.14	11.5	0.31	1s	0.075	
SEMiX202GB12Vs	310	200	1.75	24.9	24.1	0.14	229	2.2	14.5	0.26	2s	0.045	
SEMiX223GB12Vs	323	225	1.85	19.9	27.2	0.14	263	2.2	16.4	0.23	3s	0.04	
SEMiX302GB12Vs	448	300	1.75	37.3	36.1	0.1	356	2.1	21.8	0.17	2s	0.045	
SEMiX303GB12Vs	448	300	1.75	26.5	36.3	0.1	327	2.2	21.4	0.19	3s	0.04	
SEMiX404GB12Vs	596	400	1.75	39.1	52.3	0.075	440	2.2	34.3	0.14	4s	0.03	
SEMiX453GB12Vs	673	450	1.75	39.8	54.4	0.067	516	2.1	32.7	0.12	3s	0.04	
SEMiX603GB12Vs ¹⁾	800	600	1.85	50	83	0.057	516	2.4	40	0.12	3s	0.04	
SEMiX604GB12Vs	880	600	1.75	58.7	78.5	0.051	707	2.1	49.5	0.086	4s	0.03	
SEMiX101GD12Vs	159	100	1.75	12.9	11.4	0.27	121	2.2	7.7	0.48	13	0.04	
SEMiX151GD12Vs	231	150	1.75	19.4	17.1	0.19	189	2.1	11.5	0.31	13	0.04	
SEMiX223GD12Vc	323	225	1.85	19.9	27.2	0.14	263	2.2	16.4	0.23	33c	0.014	
SEMiX303GD12Vc	448	300	1.75	26.5	36.3	0.1	327	2.2	21.4	0.19	33c	0.014	
SEMiX453GD12Vc	673	450	1.75	39.8	54.4	0.067	516	2.1	32.7	0.12	33c	0.014	

Modules - IGBT - SEMiX

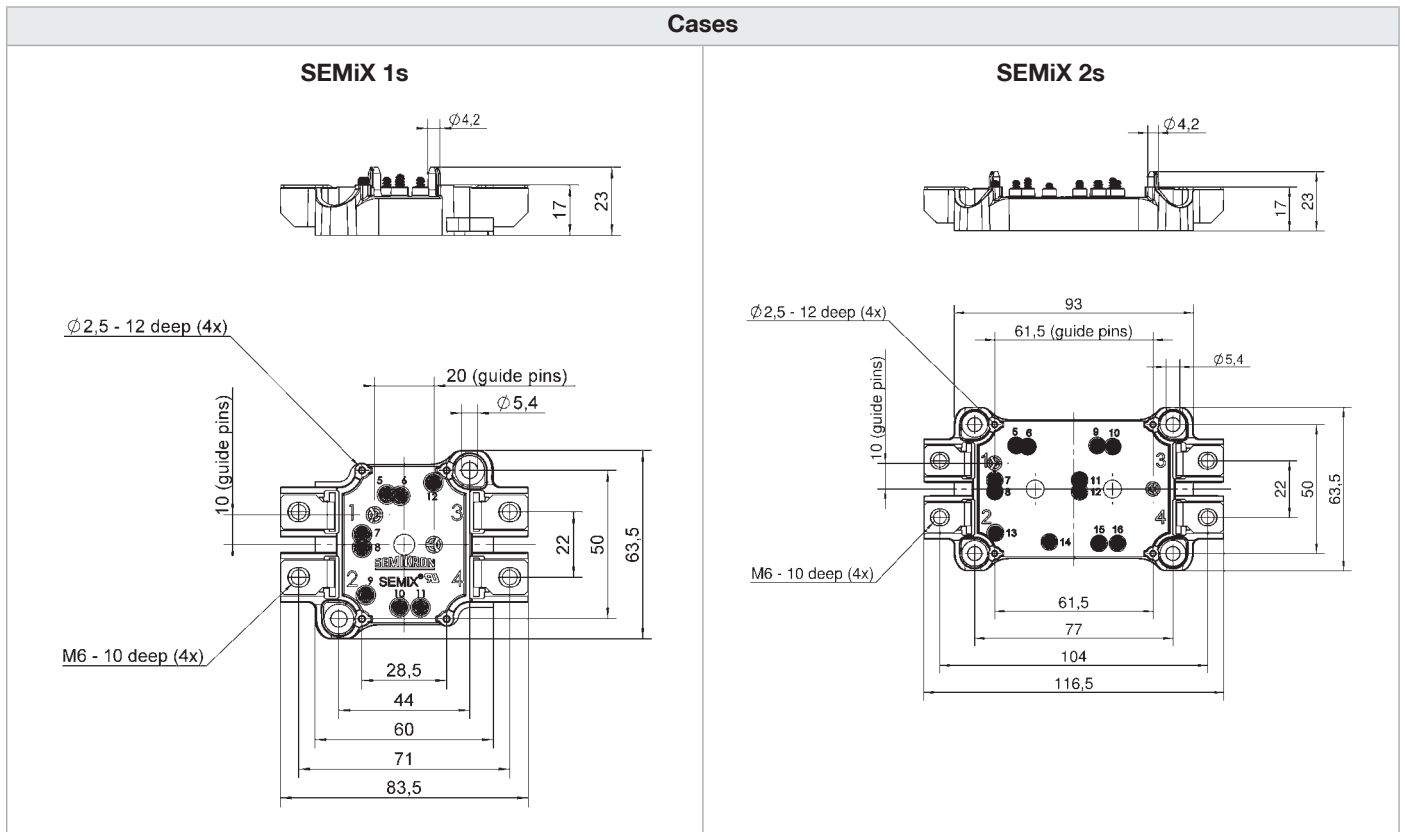
Type	IGBT						Diode				Case		Circuit
	I_C @ $T_C=25^\circ\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_j=25^\circ\text{C}$ typ.	E_{on}	E_{off}	$R_{th(j-c)}$	I_F @ $T_C=25^\circ\text{C}$	V_F @ $T_j=25^\circ\text{C}$ typ.	E_{rr}	$R_{th(j-c)}$	Case	$R_{th(c-s)}$	
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W		K/W	
1200 V - IGBT 4 (Trench)													
SEMiX151GAL12E4HDs	232	150	1.8	18	18	0.19	207	1.7	12	0.31	1s	0.075	
SEMiX302GAL12E4HDs	463	300	1.8	33	44	0.096	387	1.7	25	0.17	2s	0.045	
SEMiX453GAL12E4HDs	683	450	1.8	50	67	0.065	592	1.7	36	0.11	3s	0.04	
SEMiX604GAL12E4HDs	916	600	1.8	38	110	0.049	777	1.7	57	0.086	4s	0.03	
SEMiX151GAR12E4HDs	232	150	1.8	18	18	0.19	207	1.7	12	0.31	1s	0.075	
SEMiX302GAR12E4HDs	463	300	1.8	33	44	0.096	387	1.7	25	0.17	2s	0.045	
SEMiX453GAR12E4HDs	683	450	1.8	50	67	0.065	592	1.7	36	0.11	3s	0.04	
SEMiX604GAR12E4HDs	916	600	1.8	38	110	0.049	777	1.7	57	0.086	4s	0.03	
SEMiX151GB12E4HDs	232	150	1.8	18	18	0.19	207	1.7	12	0.31	1s	0.075	
SEMiX202GB12E4HDs	314	200	1.8	24	28	0.14	249	1.8	16	0.26	2s	0.045	
SEMiX302GB12E4HDs	463	300	1.8	33	44	0.096	387	1.7	25	0.17	2s	0.045	
SEMiX303GB12E4HDs	466	300	1.8	33	41	0.095	362	1.8	23	0.18	3s	0.04	
SEMiX404GB12E4HDs	618	400	1.8	30	60	0.072	471	1.8	34	0.14	4s	0.03	
SEMiX453GB12E4HDs	683	450	1.8	50	67	0.065	592	1.7	36	0.11	3s	0.04	
SEMiX604GB12E4HDs	916	600	1.8	38	110	0.049	777	1.7	57	0.086	4s	0.03	
SEMiX71GD12E4HDs	115	75	1.85	8.5	9	0.38	107	1.7	7	0.58	13	0.04	
SEMiX101GD12E4HDs	160	100	1.8	12	13	0.27	130	1.8	8	0.48	13	0.04	
SEMiX151GD12E4HDs	232	150	1.8	16	19	0.19	207	1.7	16	0.31	13	0.04	
SEMiX223GD12E4HDc	333	225	1.85	24	31	0.135	296	1.7	22	0.22	33c	0.014	
SEMiX303GD12E4HDc	466	300	1.8	33	42	0.095	362	1.8	30	0.18	33c	0.014	
SEMiX453GD12E4HDc	683	450	1.8	57	68	0.065	592	1.7	36	0.11	33c	0.014	
1200 V - IGBT 3 (Trench)													
SEMiX452GAL126HDs	455	300	1.7	35	45	0.083	394	1.6	33	0.15	2s	0.045	
SEMiX703GAL126HDs	642	450	1.7	32	68	0.061	561	1.6	60	0.11	3s	0.04	
SEMiX703GAR126HDs	642	450	1.7	32	68	0.061	561	1.6	60	0.11	3s	0.04	
SEMiX252GB126HDs	242	150	1.7	20	21	0.15	228	1.6	18	0.24	2s	0.045	
SEMiX302GB126HDs	311	200	1.7	30	26	0.12	292	1.6	22.5	0.19	2s	0.045	
SEMiX353GB126HDs	364	225	1.7	26.5	32.5	0.1	329	1.6	29	0.17	3s	0.04	
SEMiX452GB126HDs	455	300	1.7	35	45	0.083	394	1.6	33	0.15	2s	0.045	
SEMiX503GB126HDs	466	300	1.7	28	44	0.08	431	1.6	32.5	0.13	3s	0.04	
SEMiX604GB126HDs	590	400	1.7	36	60	0.065	533	1.6	46	0.11	4s	0.03	
SEMiX703GB126HDs	642	450	1.7	32	68	0.061	561	1.6	60	0.11	3s	0.04	
SEMiX904GB126HDs	821	600	1.7	60	88	0.05	752	1.6	75	0.081	4s	0.03	
SEMiX101GD126HDs	129	75	1.7	10	11	0.27	117	1.6	9	0.46	13	0.04	
SEMiX151GD126HDs	168	100	1.7	12	14	0.21	152	1.6	11.5	0.36	13	0.04	
SEMiX251GD126HDs	242	150	1.7	19	22	0.15	207	1.6	14.5	0.28	13	0.04	
SEMiX353GD126HDc	364	225	1.7	26.5	32.5	0.1	329	1.6	29	0.17	33c	0.014	
SEMiX503GD126HDc	466	300	1.7	28	44	0.08	412	1.6	32.5	0.14	33c	0.014	
SEMiX703GD126HDc	642	450	1.7	32	68	0.061	561	1.6	60	0.11	33c	0.014	

Modules - IGBT - SEMiX

Type	IGBT						Diode				Case		Circuit
	I_C @ $T_C=25^\circ\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_j=25^\circ\text{C}$ typ.	E_{on}	E_{off}	$R_{th(j-c)}$	I_F @ $T_C=25^\circ\text{C}$	V_F @ $T_j=25^\circ\text{C}$ typ.	E_{rr}	$R_{th(j-c)}$	Case	$R_{th(c-s)}$	
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W		K/W	
1700 V - IGBT 3 (Trench)													
SEMiX653GAL176HDs	619	450	2	300	180	0.054	545	1.7	73	0.11	3s	0.04	
SEMiX653GAR176HDs	619	450	2	300	180	0.054	545	1.7	73	0.11	3s	0.04	
SEMiX252GB176HDs	246	150	2	90	55	0.12	288	1.6	32	0.19	2s	0.045	
SEMiX302GB176HDs	308	200	2	130	77	0.1	389	1.5	43	0.15	2s	0.045	
SEMiX353GB176HDs	353	225	2	155	85	0.086	428	1.6	45	0.13	3s	0.04	
SEMiX452GB176HDs	437	300	2	180	110	0.073	389	1.7	46	0.15	2s	0.045	
SEMiX453GB176HDs	444	300	2	215	125	0.071	545	1.5	65	0.11	3s	0.04	
SEMiX604GB176HDs	567	400	2	215	165	0.058	740	1.5	95	0.081	4s	0.03	
SEMiX653GB176HDs	619	450	2	300	180	0.054	545	1.7	73	0.11	3s	0.04	
SEMiX854GB176HDs	779	600	2	300	250	0.045	740	1.7	170	0.081	4s	0.03	
SEMiX353GD176HDc	353	225	2	155	85	0.086	428	1.6	45	0.13	33c	0.014	
SEMiX453GD176HDc	444	300	2	215	125	0.071	545	1.5	65	0.11	33c	0.014	
SEMiX653GD176HDc	619	450	2	300	180	0.054	545	1.7	73	0.11	33c	0.014	

Footnotes

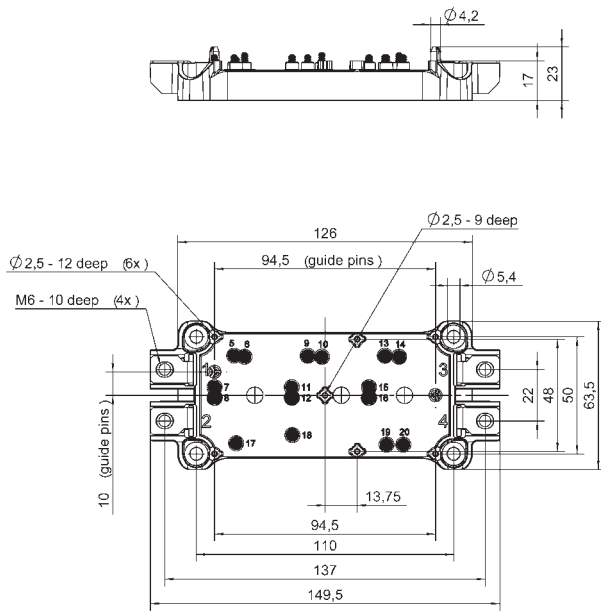
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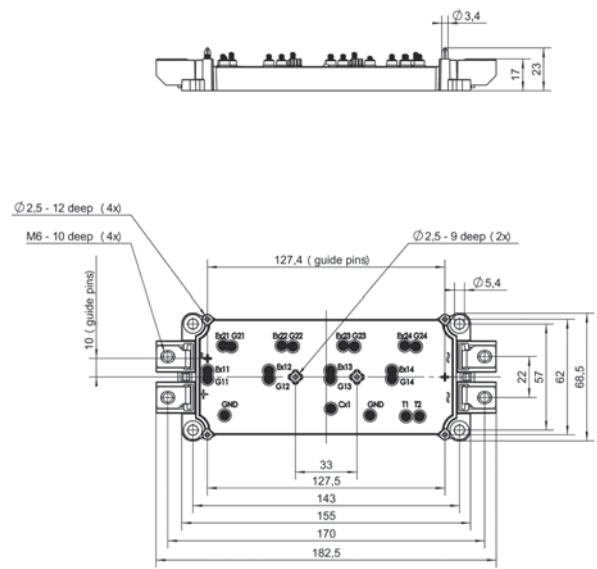
Dimensions in mm

Cases

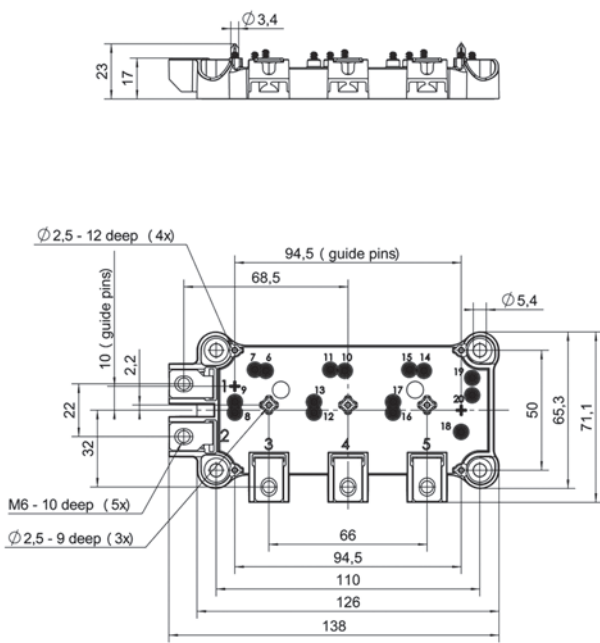
SEMIX 3s



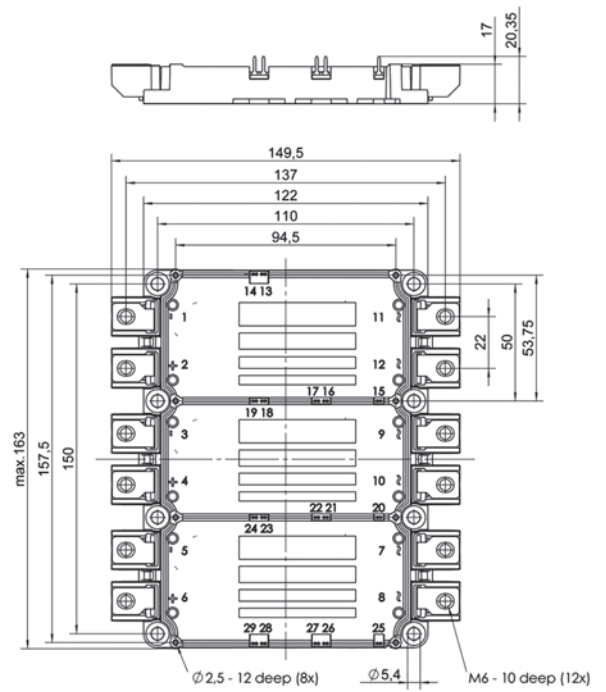
SEMIX 4s



SEMIX 13



SEMIX 33c



Dimensions in mm

Modules - IGBT - SEMITRANS

Type	IGBT						Diode				Case		Circuit
	I_C @ $T_C=25^\circ\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_j=25^\circ\text{C}$ typ.	E_{on}	E_{off}	$R_{th(j-c)}$	I_F @ $T_C=25^\circ\text{C}$	V_F @ $T_j=25^\circ\text{C}$ typ.	E_{rr}	$R_{th(j-c)}$	Case	$R_{th(c-s)}$	
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W		K/W	
600 V - IGBT 3 (Trench)													
SKM145GB066D	195	150	1.45	8.5	5.5	0.3	150	1.38	3.5	0.5	2	0.05	
SKM195GB066D	265	200	1.45	14	8	0.22	200	1.35	5.6	0.4	2	0.05	
SKM300GB066D	390	300	1.45	7.5	11.5	0.15	350	1.38	10.5	0.25	3	0.038	
SKM400GB066D	500	400	1.45	8	16	0.12	450	1.35	14	0.2	3	0.038	
SKM600GB066D	760	600	1.45	7.5	29.5	0.08	700	1.38	25	0.125	3	0.038	
SKM200GARL066T ¹⁾	280	200	1.45	2.24	7.89	0.21	270	1.45	4	0.39	5	0.038	
SKM300GARL066T ¹⁾	400	300	1.45	3.5	10.1	0.15	400	1.45	4	0.26	5	0.038	
SKM400GARL066T ¹⁾	504	400	1.45	4.48	15.78	0.12	421	1.54	8	0.28	5	0.038	
SKM150MLI066TAT	200	150	1.45	1.7	5.1	0.29	200	1.35	2	0.52	5	0.038	
SKM200MLI066TAT ¹⁾	280	200	1.45	2.53	6.82	0.21	270	1.4	4	0.39	5	0.038	
SKM300MLI066TAT ¹⁾	400	300	1.45	3.5	10.1	0.15	324	1.35	4	0.25	5	0.038	
600 V - NPT IGBT (Standard)													
SKM75GAL063D ²⁾	100	75	2.1	3	2.5	0.35	75	1.55	0.53	0.72	2	0.05	
SKM300GAL063D ²⁾	400	300	2.1	14	13	0.09	250	1.65	4	0.25	3	0.038	
SKM75GAR063D ²⁾	100	75	2.1	3	2.5	0.35	75	1.55	0.53	0.72	2	0.05	
SKM300GAR063D	400	300	2.1	14	13	0.09	250	1.65	4	0.25	3	0.038	
SKM50GB063D ²⁾	70	50	2.1	2.5	1.8	0.5	75	1.35	0.48	1	2	0.05	
SKM75GB063D ²⁾	100	75	2.1	3	2.5	0.35	75	1.55	0.53	0.72	2	0.05	
SKM100GB063D ²⁾	130	100	2.1	4	3	0.27	100	1.55	1.5	0.6	2	0.05	
SKM200GB063D ²⁾	260	200	2.1	11	7.5	0.14	200	1.55	2.1	0.3	3	0.038	
SKM300GB063D ²⁾	400	300	2.1	14	13	0.09	250	1.65	4	0.25	3	0.038	
SKM100GD063DL ²⁾	130	100	2.1	4	3	0.27	100	1.55	1.5	0.6	6	0.05	
1200 V - V-IGBT													
SKM150GAL12V ¹⁾	231	150	1.75	13.5	14.2	0.19	189	2.14	8.9	0.31	2	0.05	
SKM400GAL12V ¹⁾	612	400	1.75	39	42	0.072	440	2.20	26	0.14	3	0.038	
SKM400GAR12V ¹⁾	612	400	1.75	39	42	0.072	440	2.20	26	0.14	3	0.038	
SKM300GA12V ¹⁾	420	300	1.85	23	33	0.11	353	2.17	21	0.17	4	0.038	
SKM400GA12V ¹⁾	612	400	1.75	39	42	0.072	440	2.20	26	0.14	4	0.038	
SKM600GA12V ¹⁾	908	600	1.75	76	76	0.049	707	2.14	43	0.086	4	0.038	
SKM50GB12V ¹⁾	77	50	1.85	5	4	0.53	65	2.22	3.6	0.84	2	0.05	
SKM75GB12V ¹⁾	114	75	1.85	6.7	7.1	0.38	97	2.17	4.2	0.58	2	0.05	
SKM100GB12V ¹⁾	159	100	1.75	10.7	8.7	0.27	121	2.20	5.7	0.48	2	0.05	
SKM150GB12V ¹⁾	231	150	1.75	13.5	14.2	0.19	189	2.14	8.9	0.31	2	0.05	
SKM150GB12VG ¹⁾	222	150	1.85	10	16.5	0.2	187	2.17	11	0.31	3	0.038	
SKM200GB12V ¹⁾	311	200	1.75	14	22	0.14	229	2.20	13	0.26	3	0.038	
SKM300GB12V ¹⁾	420	300	1.85	23	33	0.11	353	2.17	21	0.17	3	0.038	
SKM400GB12V ¹⁾	612	400	1.75	39	42	0.072	440	2.20	26	0.14	3	0.038	

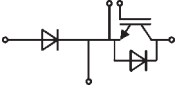
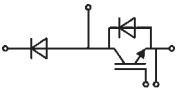

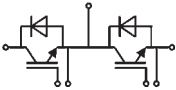
Modules - IGBT - SEMITRANS

Type	IGBT						Diode				Case		Circuit
	I_C @ $T_C=25^\circ\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_J=25^\circ\text{C}$ typ.	E_{on}	E_{off}	$R_{th(j-c)}$	I_F @ $T_C=25^\circ\text{C}$	V_F @ $T_J=25^\circ\text{C}$ typ.	E_{rr}	$R_{th(j-c)}$	Case	$R_{th(c-s)}$	
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W		K/W	
1200 V - IGBT 4 (Trench)													
SKM200GAL12E4HD	313	200	1.8	23	27	0.14	249	1.77	17	0.26	3	0.038	
SKM300GAL12E4HD	422	300	1.85	30	39	0.11	387	1.72	30	0.17	3	0.038	
SKM400GAL12E4HD	616	400	1.8	36	56	0.072	471	1.77	40	0.14	3	0.038	
SKM200GAR12E4HD	313	200	1.8	21	27	0.14	249	1.77	13	0.26	3	0.038	
SKM300GAR12E4HD	422	300	1.85	27	39	0.11	387	1.72	23	0.17	3	0.038	
SKM400GAR12E4HD	616	400	1.8	36	56	0.072	471	1.77	40	0.14	3	0.038	
SKM300GA12E4HD	422	300	1.85	29	35	0.11	387	1.72	29	0.17	4	0.038	
SKM400GA12E4HD	616	400	1.8	31	59	0.072	471	1.77	48	0.14	4	0.038	
SKM600GA12E4HD	913	600	1.8	81	84	0.049	777	1.72	49	0.086	4	0.038	
SKM900GA12E4HD ¹⁾	1305	900	1.83	100	137	0.035	956	1.84	85	0.07	4	0.038	
SKM200GB12E4HD	313	200	1.8	23	27	0.14	249	1.77	17	0.26	3	0.038	
SKM300GB12E4HD	422	300	1.85	30	39	0.11	387	1.72	30	0.17	3	0.038	
SKM400GB12E4HD	616	400	1.8	36	56	0.072	471	1.77	40	0.14	3	0.038	
SKM450GB12E4HD ¹⁾	699	450	1.82	39	61	0.062	471	1.84	43	0.14	3	0.038	
1200 V - IGBT 4 Fast (Trench)													
SKM50GAL12T4 ¹⁾	81	50	1.85	5.5	4.5	0.53	65	2.22	3.6	0.84	2	0.05	
SKM100GAL12T4 ¹⁾	160	100	1.8	15	10.2	0.27	121	2.20	5.9	0.48	2	0.05	
SKM150GAL12T4	232	150	1.8	19.2	15.8	0.19	189	2.14	13	0.31	2	0.05	
SKM200GAL12T4	313	200	1.8	21	20	0.14	229	2.20	13	0.26	3	0.038	
SKM300GAL12T4	422	300	1.85	27	29	0.11	353	2.17	23	0.17	3	0.038	
SKM400GAL12T4	616	400	1.8	33	42	0.072	440	2.20	30.5	0.14	3	0.038	
SKM150GAR12T4	232	150	1.8	19.2	15.8	0.19	189	2.14	13	0.31	2	0.05	
SKM400GAR12T4	616	400	1.8	33	42	0.072	440	2.20	30.5	0.14	3	0.038	
SKM300GA12T4	422	300	1.85	23.4	26	0.11	353	2.17	22.2	0.17	4	0.038	
SKM400GA12T4	616	400	1.8	28	44	0.072	440	2.20	37	0.14	4	0.038	
SKM600GA12T4	913	600	1.8	74	63	0.049	707	2.14	38	0.086	4	0.038	
SKM50GB12T4	81	50	1.85	5.5	4.5	0.53	65	2.22	3.8	0.84	2	0.05	
SKM75GB12T4	115	75	1.85	11	6.9	0.38	97	2.17	4.7	0.58	2	0.05	
SKM100GB12T4	160	100	1.8	15	10.2	0.27	121	2.20	5.9	0.48	2	0.05	
SKM100GB12T4G	154	100	1.85	16.1	8.6	0.29	118	2.22	6	0.49	3	0.038	
SKM150GB12T4	232	150	1.8	19.2	15.8	0.19	189	2.14	13	0.31	2	0.05	
SKM150GB12T4G	223	150	1.85	18.7	14.1	0.2	183	2.17	9	0.32	3	0.038	
SKM200GB12T4	313	200	1.8	21	20	0.14	229	2.20	13	0.26	3	0.038	
SKM300GB12T4	422	300	1.85	27	29	0.11	353	2.17	23	0.17	3	0.038	
SKM400GB12T4	616	400	1.8	33	42	0.072	440	2.20	30.5	0.14	3	0.038	
SKM150GM12T4G ¹⁾	229	150	1.85	19.2	15.8	0.19	187	2.17	13	0.31	3	0.038	
SKM200GM12T4 ¹⁾	313	200	1.8	21	20	0.14	229	2.20	13	0.26	3	0.038	
SKM300GM12T4 ¹⁾	422	300	1.85	27	29	0.11	353	2.17	23	0.17	3	0.038	
SKM400GM12T4 ¹⁾	616	400	1.8	33	42	0.072	440	2.20	30.5	0.14	3	0.038	
SKM300GBD12T4 ¹⁾	422	300	1.85	27	29	0.11	56	2.41	30.5	0.94	3	0.038	

Modules - IGBT - SEMITRANS

Type	IGBT						Diode				Case		Circuit
	I_C @ $T_C=25^\circ\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_J=25^\circ\text{C}$ typ.	E_{on}	E_{off}	$R_{th(j-c)}$	I_F @ $T_C=25^\circ\text{C}$	V_F @ $T_J=25^\circ\text{C}$ typ.	E_{rr}	$R_{th(j-c)}$	Case	$R_{th(c-s)}$	
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W		K/W	
1200 V - IGBT 3 (Trench)													
SKM195GAL126D	220	150	1.7	16	24.5	0.16	170	2.45	5.8	0.32	2	0.05	
SKM200GAL126D	260	150	1.7	18	24	0.13	200	1.64	18	0.3	3	0.038	
SKM400GAL126D	470	300	1.7	29	48	0.08	400	1.64	27	0.18	3	0.038	
SKM600GAL126D	660	400	1.7	39	64	0.055	490	1.67	41	0.125	3	0.038	
SKM600GA126D	660	400	1.7	39	64	0.055	490	1.67	41	0.125	4	0.038	
SKM800GA126D	960	600	1.7	65	95	0.042	680	1.69	59	0.09	4	0.038	
SKM195GB126D	220	150	1.7	16	24.5	0.16	170	2.45	5.8	0.32	2	0.05	
SKM200GB126D	260	150	1.7	18	24	0.13	200	1.64	18	0.3	3	0.038	
SKM300GB126D	310	200	1.7	21	33	0.12	250	1.67	18	0.25	3	0.038	
SKM400GB126D	470	300	1.7	29	48	0.08	400	1.64	27	0.18	3	0.038	
SKM600GB126D	660	400	1.7	39	64	0.055	490	1.67	41	0.125	3	0.038	
1200 V - NPT IGBT (Ultrafast)													
SKM200GAL125D	200	150	3.3	14	8	0.09	200	2.06	8	0.25	3	0.038	
SKM400GAL125D	400	300	3.3	17	18	0.05	390	2.06	16	0.125	3	0.038	
SKM200GAR125D	200	150	3.3	14	8	0.09	200	2.06	8	0.25	3	0.038	
SKM400GAR125D	400	300	3.3	17	18	0.05	390	2.06	16	0.125	3	0.038	
SKM600GA125D	580	400	3.3	30	22	0.041	500	2.00	24	0.09	4	0.038	
SKM800GA125D	760	600	3.2	88	48	0.03	720	2.3	28	0.07	4	0.038	
SKM100GB125DN	100	75	3.3	9	3.5	0.18	95	2.06	4	0.5	2N	0.05	
SKM200GB125D	200	150	3.3	14	8	0.09	200	2.06	8	0.25	3	0.038	
SKM300GB125D	300	200	3.3	16	11	0.075	260	2.00	13	0.18	3	0.038	
SKM400GB125D	400	300	3.3	17	18	0.05	390	2.06	16	0.125	3	0.038	
SKM25GD125D ¹⁾	39	25	3.2	3.9	1.6	0.56	47	2.13	1.1	1	6	0.05	
SKM50GD125D ¹⁾	73	50	3.2	8	3.2	0.32	77	2.00	2.1	0.6	6	0.05	
SKM25GAH125D ¹⁾	39	25	3.2	3.9	1.6	0.56	47	2.13	1.1	1	6	0.05	
1700 V - IGBT 3 (Trench)													
SKM145GAL176D	160	100	2	60	38	0.19	140	1.6	27.5	0.36	2	0.05	
SKM200GAL176D	260	150	2	93	58	0.12	210	1.55	31	0.25	3	0.038	
SKM400GAL176D	432	300	2	170	118	0.075	440	1.55	78	0.125	3	0.038	
SKM400GAR176D	432	300	2	170	118	0.075	440	1.55	78	0.125	3	0.038	
SKM600GA176D	660	400	2	255	155	0.044	600	1.6	102	0.09	4	0.038	
SKM800GA176D	830	600	2	335	245	0.04	630	1.6	155	0.07	4	0.038	
SKM75GB176D	80	50	2	25	18	0.38	80	1.50	14.5	0.55	2	0.05	
SKM100GB176D	125	75	2	44	28.5	0.24	100	1.6	21.4	0.45	2	0.05	
SKM145GB176D	160	100	2	60	38	0.19	140	1.6	27.5	0.36	2	0.05	
SKM200GB176D	260	150	2	93	58	0.12	210	1.55	31	0.25	3	0.038	
SKM400GB176D	432	300	2	170	118	0.075	440	1.55	78	0.125	3	0.038	

Modules - IGBT - SEMITRANS

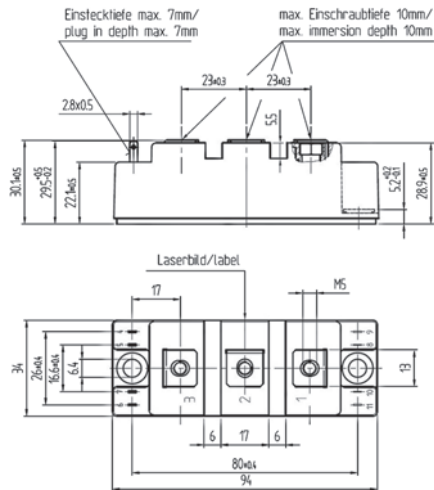
Type	IGBT						Diode				Case		Circuit
	I_C @ $T_C = 25^\circ\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_j = 25^\circ\text{C}$ typ.	E_{on}	E_{off}	$R_{th(j-c)}$	I_F @ $T_C = 25^\circ\text{C}$	V_F @ $T_j = 25^\circ\text{C}$ typ.	E_{rr}	$R_{th(j-c)}$	Case	$R_{th(c-s)}$	
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W		K/W	
1700 V - NPT IGBT (Standard)													
SKM200GAR173D ²⁾	220	150	3.4	95	45	0.1	150	2.2	21	0.32	3	0.038	
SKM200GAL173D ²⁾	220	150	3.4	95	45	0.1	150	2.2	21	0.32	3	0.038	
SKM400GA173D ²⁾	440	300	3	180	10	0.05	300	2.2	46	0.17	4	0.038	
SKM75GB173D ²⁾	75	50	3.4	18	13	0.25	60	2.2	10.5	0.75	2	0.05	
SKM100GB173D ²⁾	110	75	3.4	35	21	0.2	80	2.2	11.5	0.63	2	0.05	
SKM150GB173D ²⁾	150	100	3.4	60	32	0.125	125	2.2	14	0.4	3	0.038	
SKM200GB173D ²⁾	220	150	3.4	95	45	0.1	150	2.2	21	0.32	3	0.038	

Footnotes

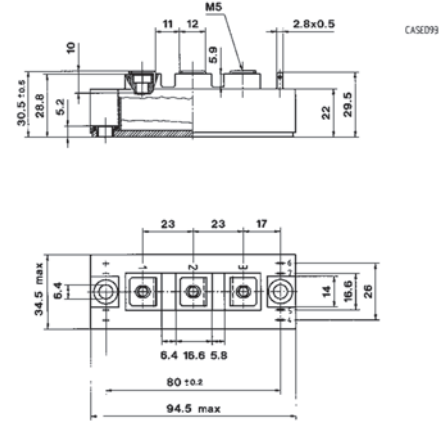
- 1) New
- 2) Not for New Design

Cases

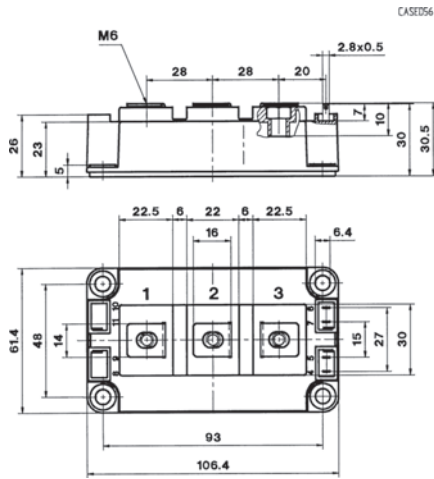
SEMISTRANS 2



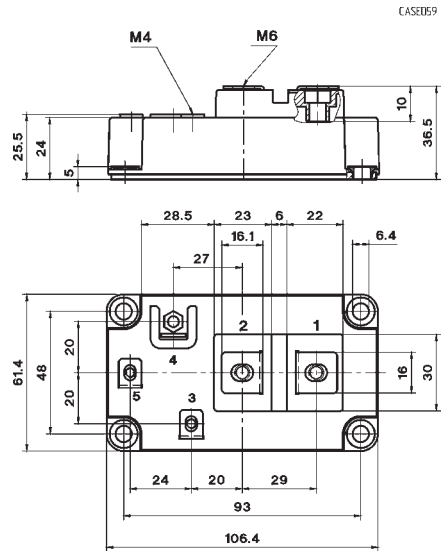
SEMISTRANS 2N



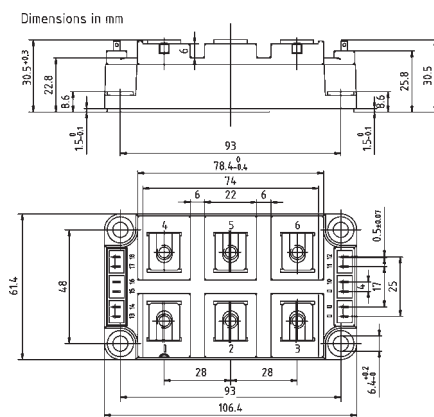
SEMISTRANS 3



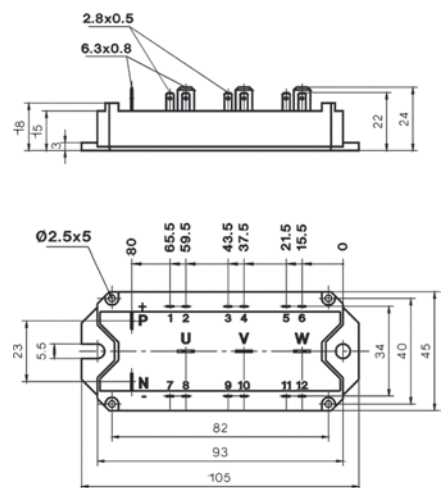
SEMISTRANS 4



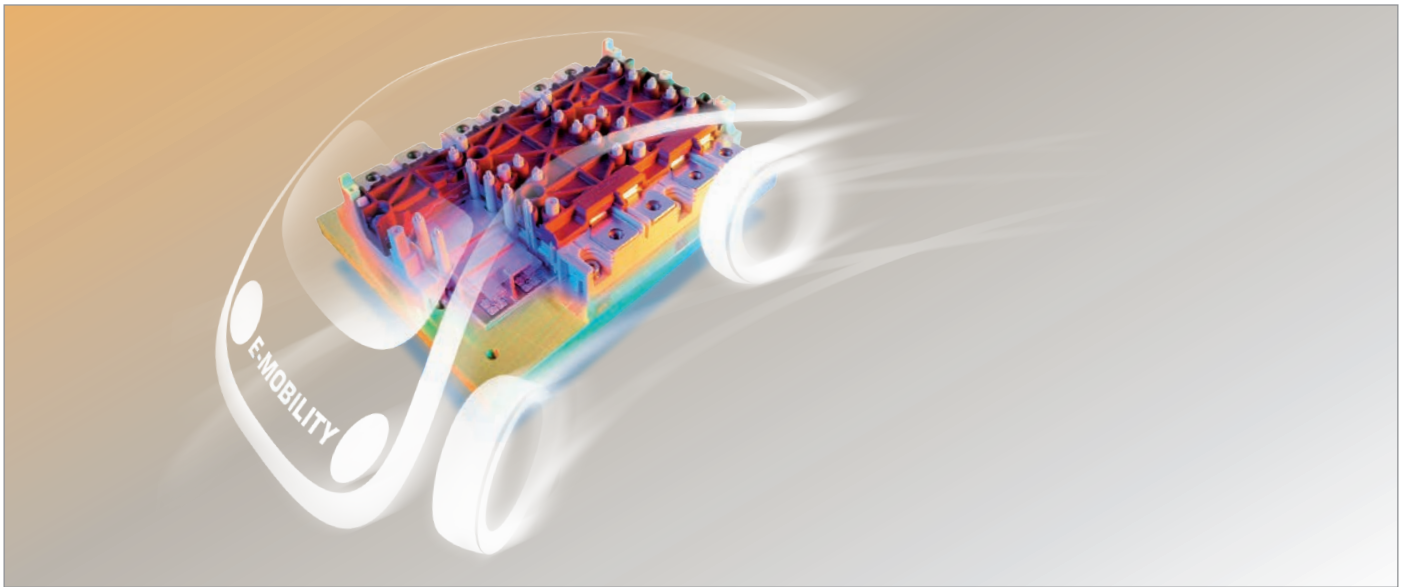
SEMISTRANS 5



SEMISTRANS 6



Dimensions in mm



100% solder-free ensures durability

Applications

SKiM 63/93 sintered modules with no base plate offer a number of possibilities for boosting the reliability of inverters. The SKiM 63/93 is used in many different applications, such as electric powertrains in electric vehicles, hybrid cars and utility vehicles, heavy-duty construction machinery, or even to provide leading-edge performance in race cars.

Product range

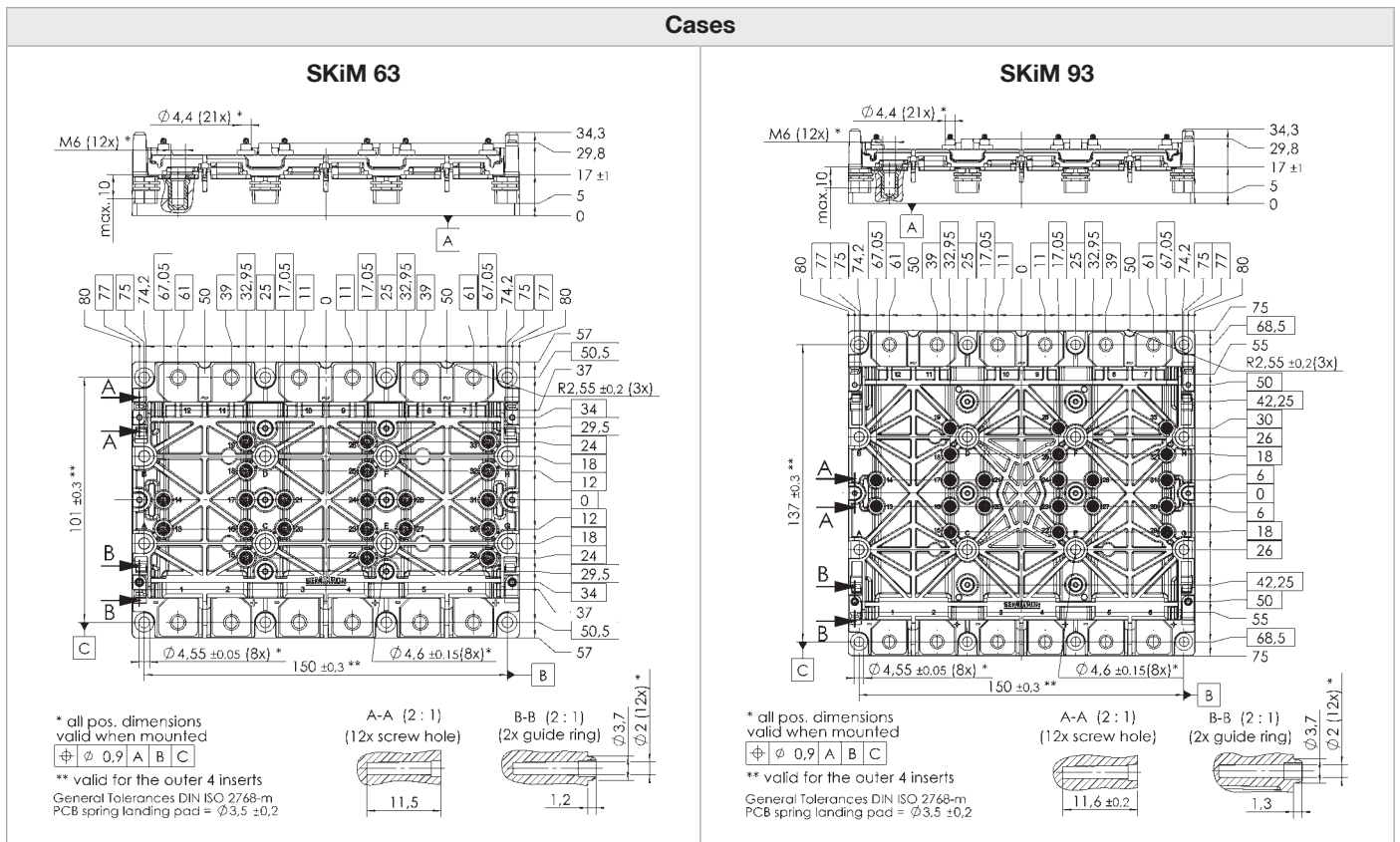
The SKiM 63/93 modules combine 3-phase inverter topology with temperature control for all 3 phases at 600 V, 1200 V and 1700 V voltage. Power ranges from 20 kW - 180 kW, nominal currents range from 300 A - 900 A. Driver solutions for all voltage classes are available as well as an optimised water cooler for fast and customer-friendly evaluation. In addition, paralleling boards for a simple and powerful half-bridge configuration are also available.

Benefits

SKiM solderfree technology completely eliminates solder connections that can be detrimental to service life. The reliability of the inverter, even under substantial active and passive temperature swings, can be increased by several factors. This is proven by best-in-class results in power cycle and temperature cycle tests. Thanks to the baseplate-free design, the thickness of the thermal paste layer could be reduced by a factor of 4 as compared to conventional modules. Hand in hand with the optimised thermal layout, operating temperatures are reduced significantly. Temperatures are largely homogenous throughout the 3 phases of the inverter. All SKiM modules come with pre-applied thermal paste. No soldering is required for SKiM driver board and heat sink mounting, making the assembly easy and cost-efficient.

Modules - IGBT - SKiM 63/93

Type	IGBT						Diode				Case	Circuit
	I_C @ $T_S=25^\circ\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_J=25^\circ\text{C}$ typ.	E_{on}	E_{off}	$R_{th(j-s)}$	I_F @ $T_S=25^\circ\text{C}$	V_F @ $T_J=25^\circ\text{C}$ typ.	E_{rr}	$R_{th(j-s)}$		
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W		
600 V - IGBT 3 (Trench)												
SKiM406GD066HD	468	400	1.45	8	25	0.135	360	1.5	12	0.243	63	
SKiM606GD066HD	641	600	1.45	16	53	0.105	453	1.6	21	0.201	63	
SKiM909GD066HD	899	900	1.45	36	88	0.078	712	1.5	29	0.135	93	
1200 V - IGBT 4 (Trench)												
SKiM609GAL12E4	748	600	1.85	136	83	0.068	1397	1.7	39	0.048	93	
SKiM609GAR12E4	748	600	1.85	136	83	0.068	1397	1.7	39	0.048	93	
SKiM306GD12E4	410	300	1.85	19	39	0.116	302	2.1	21	0.218	63	
SKiM459GD12E4	554	450	1.85	22	57	0.092	438	2.1	40	0.155	93	
1700 V - IGBT 4 (Trench)												
SKiM429GD17E4HD	595	420	1.9	245	180	0.079	413	1.7	99	0.169	93	



Dimensions in mm

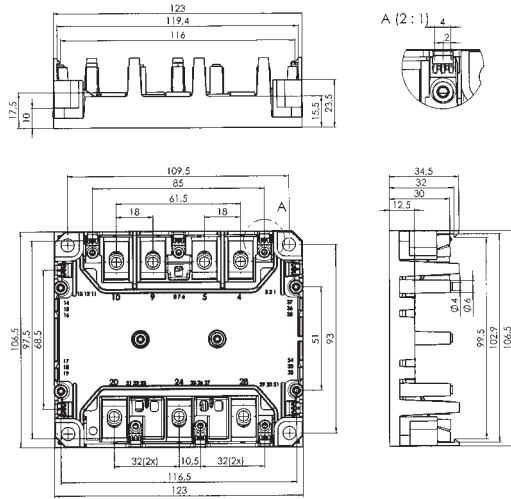
Modules - IGBT - SKiM 4/5

Type	IGBT						Diode				Case	Circuit	
	I_C @ $T_S=25^\circ\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_j=25^\circ\text{C}$ typ.	E_{on}	E_{off}	$R_{th(j-s)}$	I_F @ $T_S=25^\circ\text{C}$	V_F @ $T_j=25^\circ\text{C}$ typ.	E_{rr}	$R_{th(j-s)}$			
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W			
650 V - IGBT 3 (Trench)													
SKiM201MLI07E4	190	200	1.45	-	-	-	-	-	-	-	4		
SKiM301MLI07E4	256	300	1.45	-	-	-	-	-	-	4			
SKiM401MLI07E4	317	400	1.45	3.32	-	-	-	-	1.8	4			
SKiM601MLI07E4	438	600	1.45	5.49	-	-	-	-	2.4	4			
1200 V - IGBT 3 (Trench)													
SKiM200GD126D	-	200	1.65	15	25	-	152	2.4	-	0.35	4		
SKiM300GD126D	265	300	1.7	28	47	0.2	260	1.9	-	0.285	4		
SKiM300GD126DL	265	300	1.65	28	47	0.2	260	1.9	-	0.285	4		
SKiM400GD126DLM	330	300	1.65	29	46	0.134	300	1.9	-	0.19	4		
SKiM400GD126DM	330	300	1.7	29	46	0.134	300	1.9	-	0.19	4		
SKiM450GD126D	390	450	1.7	42	70	0.13	345	1.9	-	0.19	5		
SKiM450GD126DL	390	450	1.65	42	70	0.13	345	1.9	-	0.19	5		
SKiM600GD126DLM	480	450	1.65	42	70	0.09	450	1.9	-	0.125	5		
SKiM601GD126DM	480	450	1.7	42	70	0.09	450	1.9	-	0.125	5		
1200 V - IGBT 4 (Trench)													
SKiM304GD12T4D	312	300	1.8	-	-	0.19	221	2.3	-	0.25	4		
SKiM455GD12T4D1	400	450	1.8	34	40	0.14	295	2.3	28	0.19	5		
SKiM455GD12T4DM1	460	450	1.8	34	40	0.11	390	2.3	28	0.12	5		
SKiM201MLI12E4	225	200	1.8	23.7	-	-	180	2.2	-	-	4		
SKiM301MLI12E4	312	300	1.8	23.7	-	-	253	2.1	-	-	4		
SKiM301TMLI12E4B	311	300	1.8	23.7	-	0.19	249	2.20	-	0.29	4		
SKiM301TMLI12E4C	311	300	1.8	23.7	-	0.19	249	2.20	-	0.29	4		
SKiM401TMLI12E4B	388	400	1.8	8.83	-	0.16	311	2.20	2.26	0.24	4		
SKiM601TMLI12E4B	542	600	1.8	-	-	0.12	438	2.14	3.45	0.18	4		
1700 V - IGBT 3 (Trench)													
SKiM120GD176D	110	125	2	72	46	0.4	105	1.6	22	0.56	4		
SKiM220GD176DH4	220	250	2	145	100	0.21	220	1.7	65	0.26	4		
SKiM270GD176D	260	300	2	170	120	0.175	215	1.7	-	0.29	5		

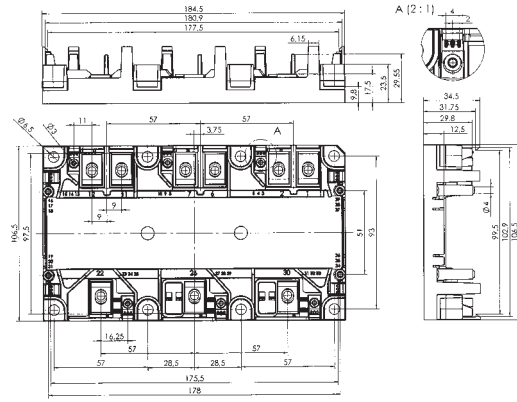
Modules - IGBT - SKiM 4/5

Cases

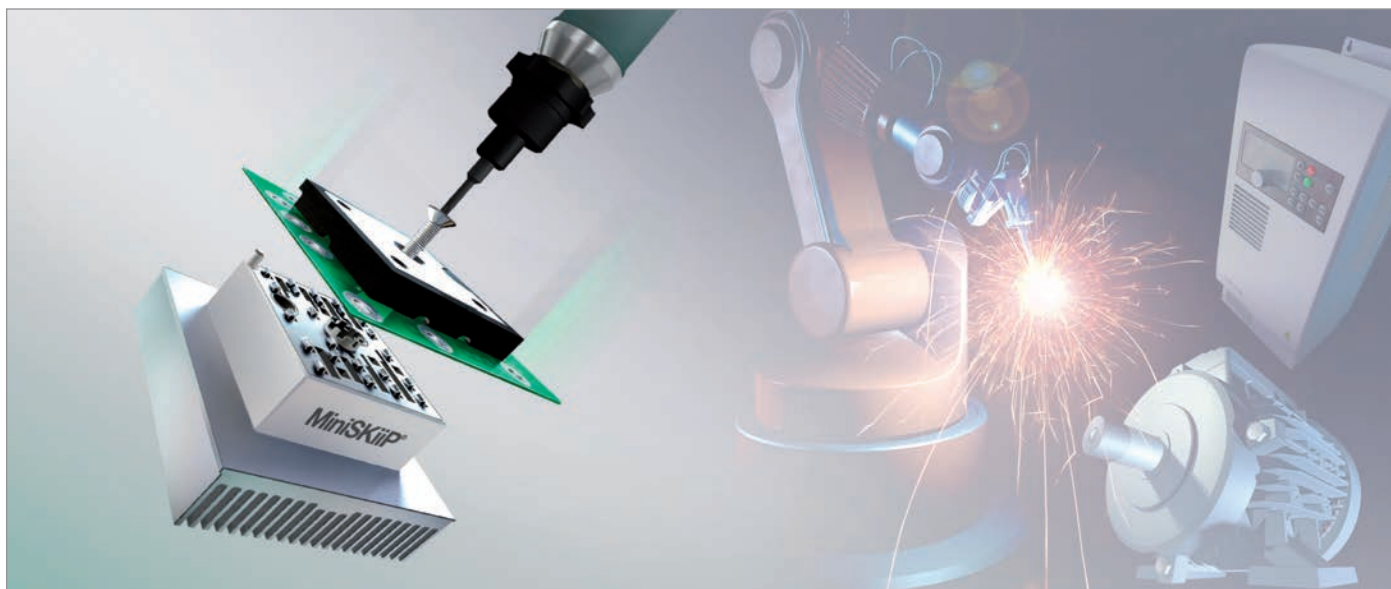
SKiM 4



SKiM 5



Dimensions in mm



Fast, cost efficient and reliable one screw mounting

Applications

Thanks to the use of spring contact technology, MiniSKiiP modules enable fast single-screw or double-screw assembly, facilitating quick and reliable inverter manufacture. With more than 15 years of field experience and more than 21 million modules in the field, this module platform has proven successful in all standard applications. Key applications include all kinds of frequency inverters, such as standard drives, stand-alone drives, servo drives, system drives, solar inverters, UPS systems and welding machines. Thanks to the reliability of spring contacts, applications such as agricultural vehicles or pitch motors of windmills benefit from the MiniSKiiP technology.

Product range

MiniSKiiP modules are designed for 600 V and 1200 V chip with 4-200 A nominal chip currents, and feature Trench IGBT technology in combination with the SEMIKRON CAL diode. In the 1200 V range, the latest Trench IGBT4 technology is used in combination with the CAL 4 diode. These chips are designed for a junction temperature of up to 175°C. In addition to the CIB configuration and 6-pack modules, non-controlled rectifiers with brake chopper, as well as half-controlled rectifiers with brake chopper, are also available. Modules for 3-level inverters with output powers of 30-80 kVA and an IGBT blocking voltage of 650 V, as well as SiC devices, are also available.

Benefits

An important mechanical feature in this module is the easy-assembly and service-friendly spring-contact for load and gate terminals. Compared to conventionally soldered modules, where expensive automatic soldering equipment is required for time-consuming soldering processes, no special tools are needed to assemble MiniSKiiP modules - instead, a single-screw connection is used. The printed circuit board (PCB), power module and heat sink are firmly joined via the pressure lid.

This connection technology features a number of additional advantages: the customer's PCB can be more flexible in design, as the power circuit board does not need to include holes for solder pins. The springs provide a flexible connection between the PCB and the power circuitry which is far superior to a soldered joint, particularly under thermal or mechanical load conditions which can affect lifetime. Thanks to the good contact force provided by the springs, an air-tight, reliable electrical connection can be sustained.

Modules - IGBT - MiniSKiiP

Type	IGBT						Diode				Rectifier		Circuit	
	I_C @ $T_S=25^\circ\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_j=25^\circ\text{C}$ typ.	E_{on}	E_{off}	$R_{th(j-s)}$	I_F @ $T_S=25^\circ\text{C}$	V_F @ $T_j=25^\circ\text{C}$ typ.	E_{rr}	$R_{th(j-s)}$	I_{FSM} @ $T_S=25^\circ\text{C}$	$R_{th(j-s)}$		
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W	A	K/W		
600 V - IGBT 3 (Trench)														
SKiiP 16GH066V1	65	50	1.45	1.7	1.7	0.95	56	1.50	1.3	1.6	-	-	II 1	
SKiiP 27GH066V1	88	75	1.45	2.7	3	0.75	77	1.50	1.8	1.2	-	-	II 2	
SKiiP 28GH066V1	112	100	1.45	3.4	3.5	0.6	112	1.30	3.3	0.8	-	-	II 2	
SKiiP 01NEC066V3	12	6	1.45	0.3	0.2	2.4	12	1.30	0.2	3	220	1.5	II 0	
SKiiP 02NEC066V3	20	10	1.45	0.5	0.3	2	20	1.30	0.5	2.5	220	1.5	II 0	
SKiiP 03NEC066V3	27	15	1.45	0.6	0.5	1.8	28	1.40	0.5	2.5	220	1.5	II 0	
SKiiP 12NAB066V1	20	10	1.45	0.5	0.3	2	20	1.30	0.5	2.5	220	1.5	II 1	
SKiiP 13NAB066V1	27	15	1.45	0.6	0.5	1.8	28	1.40	0.5	2.5	220	1.5	II 1	
SKiiP 14NAB066V1	33	20	1.45	0.75	0.7	1.6	31	1.60	0.55	2.5	220	1.5	II 1	
SKiiP 25NAB066V1	43	30	1.45	0.9	1.2	1.35	39	1.50	1.1	2.1	370	1.5	II 2	
SKiiP 26NAB066V1	65	50	1.45	1.6	1.6	0.95	56	1.50	1.3	1.6	370	1.5	II 2	
SKiiP 25NEB066V1	43	30	1.45	0.9	1.2	1.35	39	1.50	1.1	2.1	370	1.5	II 2	
600 V - NPT IGBT (Ultrafast)														
SKiiP 11NAB065V1 ²⁾	12	6	2	0.3	0.2	1.9	12	1.30	0.2	2.5	220	1.5	II 1	
SKiiP 12NAB065V1 ²⁾	20	10	2	0.3	0.3	1.5	20	1.40	0.2	2.5	220	1.5	II 1	
SKiiP 13NAB065V1 ²⁾	24	15	2	0.6	0.3	1.4	26	1.40	0.4	2.2	220	1.5	II 1	
SKiiP 14NAB065V1 ²⁾	29	20	2	0.7	0.4	1.25	26	1.60	0.4	2.2	370	1.25	II 1	
650 V - IGBT 3 (Trench)														
SKiiP 26MLI07E3V1 ¹⁾	-	75	1.45	-	-	-	-	1.5	-	-	-	-	II 2	
SKiiP 27MLI07E3V1 ¹⁾	-	100	1.45	-	-	-	-	1.4	-	-	-	-	II 2	
SKiiP 28MLI07E3V1 ¹⁾	-	150	1.45	-	-	-	-	1.4	-	-	-	-	II 2	
SKiiP 39MLI07E3V1 ¹⁾	-	200	1.45	-	-	-	-	1.4	-	-	-	-	II 3	
1200 V - IGBT 3 (Trench)														
SKiiP 11AC126V1 ²⁾	16	8	1.7	0.9	1	1.5	14	1.90	0.9	2.5	-	-	II 1	
SKiiP 12AC126V1 ²⁾	28	15	1.7	1.7	1.9	1.15	26	1.60	1.2	1.95	-	-	II 1	
SKiiP 13AC126V1 ²⁾	41	25	1.7	4.1	3.1	0.9	30	1.80	2.2	1.7	-	-	II 1	
SKiiP 23AC126V1 ²⁾	41	25	1.7	3.7	3.1	0.9	30	1.80	2.6	1.7	-	-	II 2	
SKiiP 24AC126V1 ²⁾	52	35	1.7	4.2	4.4	0.75	38	1.80	3.5	1.5	-	-	II 2	
SKiiP 25AC126V1 ²⁾	73	50	1.7	5.8	6.5	0.55	62	1.60	5.1	1	-	-	II 2	
SKiiP 26AC126V1 ²⁾	88	70	1.7	9	7.7	0.5	91	1.50	7.5	0.7	-	-	II 2	
SKiiP 37AC126V2 ²⁾	97	75	1.7	9.6	8.7	0.45	90	1.60	9.6	0.7	-	-	II 3	
SKiiP 38AC126V2 ²⁾	118	105	1.7	13.1	13	0.4	118	1.60	11.2	0.55	-	-	II 3	
SKiiP 39AC126V2 ²⁾	157	140	1.7	19.9	17.2	0.3	167	1.50	16.2	0.4	-	-	II 3	
SKiiP 11NAB126V1 ²⁾	16	8	1.7	0.8	1	1.5	14	1.90	0.9	2.5	220	1.5	II 1	
SKiiP 12NAB126V1 ²⁾	28	15	1.7	2	1.9	1.15	26	1.60	1.3	1.95	220	1.5	II 1	
SKiiP 23NAB126V1 ²⁾	41	25	1.7	3.5	3	0.9	30	1.80	2.5	1.7	370	1.25	II 2	
SKiiP 23NAB126V10 ²⁾	41	25	1.7	3.5	3	0.9	30	1.80	2.5	1.7	635	0.9	II 2	
SKiiP 24NAB126V1 ²⁾	52	35	1.7	4.6	4	0.75	38	1.80	3.3	1.5	370	1.25	II 2	
SKiiP 24NAB126V10 ²⁾	52	35	1.7	4.6	4	0.75	38	1.80	3.3	1.5	635	0.9	II 2	
SKiiP 35NAB126V1 ²⁾	73	50	1.7	6.5	6.1	0.55	62	1.60	4.7	1	700	0.9	II 3	
SKiiP 36NAB126V1 ²⁾	88	70	1.7	9	7.7	0.5	91	1.50	7.5	0.7	700	0.9	II 3	

Modules - IGBT - MiniSKiiP

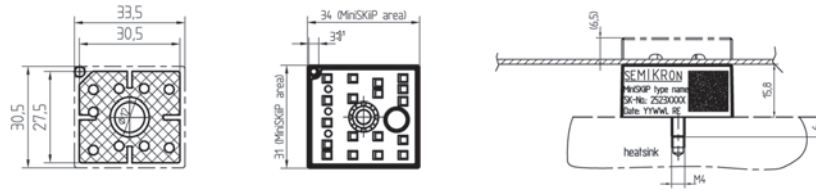
Type	IGBT						Diode				Rectifier		Circuit	
	I_C @ $T_S=25^\circ\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_j=25^\circ\text{C}$ typ.	E_{on}	E_{off}	$R_{th(j-s)}$	I_F @ $T_S=25^\circ\text{C}$	V_F @ $T_j=25^\circ\text{C}$ typ.	E_{rr}	$R_{th(j-s)}$	I_{FSM} @ $T_S=25^\circ\text{C}$	$R_{th(j-s)}$		
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W	A	K/W		
1200 V - IGBT 4 (Trench)														
SKiiP 26GH12T4V11	90	70	1.85	9.5	7.1	0.55	83	2.1	5.6	0.75	-	-	II 2	
SKiiP 11AC12T4V1	12	8	1.85	0.87	0.75	1.84	15	2.3	0.53	2.53	-	-	II 1	
SKiiP 12AC12T4V1	18	15	1.85	1.65	1.5	1.3	23	2.4	0.79	1.92	-	-	II 1	
SKiiP 13AC12T4V1	41	25	1.85	3.7	2.4	1	32	2.4	1.64	1.52	-	-	II 1	
SKiiP 23AC12T4V1	41	25	1.85	3.7	2.4	1	32	2.4	1.64	1.52	-	-	II 2	
SKiiP 24AC12T4V1	52	35	1.85	3.7	3	0.85	44	2.3	2.3	1.2	-	-	II 2	
SKiiP 25AC12T4V1	69	50	1.85	6	4.5	0.71	60	2.2	3.2	0.95	-	-	II 2	
SKiiP 26AC12T4V1	90	70	1.85	9.5	7.1	0.55	83	2.2	5.6	0.75	-	-	II 2	
SKiiP 37AC12T4V1	90	75	1.85	11.5	6.8	0.58	83	2.2	5.5	0.75	-	-	II 3	
SKiiP 38AC12T4V1	115	100	1.8	13.7	9.7	0.48	100	2.2	6.5	0.66	-	-	II 3	
SKiiP 39AC12T4V1	167	150	1.85	22.5	14	0.33	136	2.1	11.4	0.52	-	-	II 3	
SKiiP 02NAC12T4V1	6	4	1.85	0.66	0.37	2.49	7.5	1.8	0.34	2.53	220	1.5	II 0	
SKiiP 03NAC12T4V1	7.5	8	1.85	0.9	0.7	1.84	9	2.3	0.5	2.53	220	1.5	II 0	
SKiiP 10NAB12T4V1	6	4	1.85	0.66	0.37	2.49	7.5	1.8	0.34	2.53	220	1.5	II 1	
SKiiP 11NAB12T4V1	12	8	1.85	0.87	0.74	1.84	15	2.3	0.57	2.53	220	1.5	II 1	
SKiiP 12NAB12T4V1	18	15	1.85	1.4	1.3	1.3	23	2.40	1.1	1.92	220	1.5	II 1	
SKiiP 23NAB12T4V1	37	25	1.85	2.65	2.3	1.2	32	2.40	1.6	1.52	370	1.25	II 2	
SKiiP 24NAB12T4V1	48	35	1.85	4.3	3.25	1	44	2.3	2.4	1.2	370	1.25	II 2	
SKiiP 34NAB12T4V1	52	35	1.85	4.3	3.3	0.85	44	2.3	2.4	1.2	370	1.25	II 3	
SKiiP 35NAB12T4V1	69	50	1.85	6	4.7	0.71	60	2.25	3.4	0.95	700	0.9	II 3	
SKiiP 37NAB12T4V1	90	75	1.85	9.7	6.8	0.58	83	2.2	4.9	0.75	700	0.9	II 3	
SKiiP 38NAB12T4V1	115	100	1.8	11.2	10	0.48	99	2.2	6.5	0.66	1000	0.7	II 3	
SKiiP 11ACC12T4V10 ¹⁾	12	8	1.85	0.87	0.74	1.84	15	2.3	0.57	2.53	-	-	II 1	
SKiiP 12ACC12T4V10 ¹⁾	18	15	1.85	1.73	1.42	1.3	23	2.4	1.1	1.92	-	-	II 1	
SKiiP 23ACC12T4V10 ¹⁾	41	25	1.85	2.8	2.3	1	32	2.4	1.7	1.52	-	-	II 2	
SKiiP 24ACC12T4V10 ¹⁾	52	35	1.85	4.2	3.1	0.85	44	2.3	2.2	1.2	-	-	II 2	

Footnotes

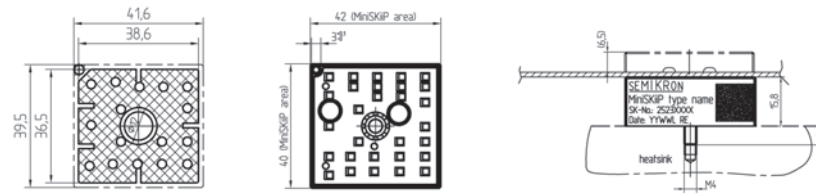
- 1) New
- 2) Not for New Design

Cases

MiniSKiiP II 0

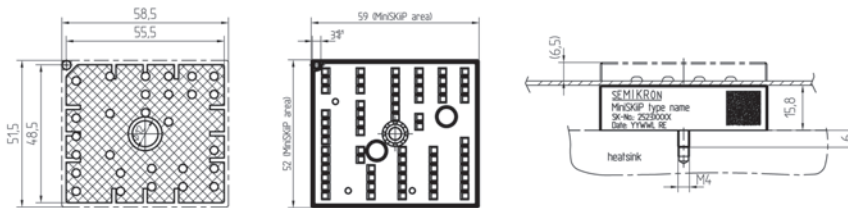


MiniSKiiP II 1



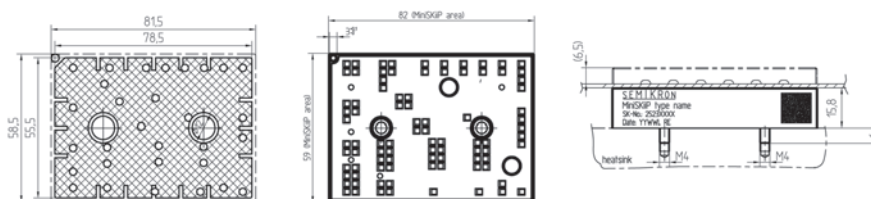
pin configuration depends on circuit details in data sheet

MiniSKiiP II 2



pin configuration depends on circuit details in data sheet

MiniSKiiP II 3



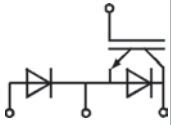
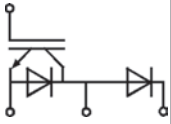
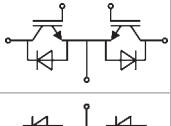
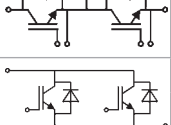
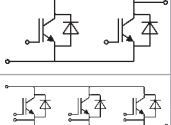
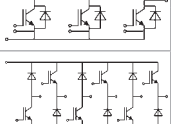
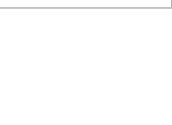
pin configuration depends on circuit details in data sheet

Dimensions in mm

Modules - IGBT - SEMITOP

Type	IGBT						Diode				Rectifier		Case	Circuit
	I_C @ $T_S=25^\circ\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_J=25^\circ\text{C}$ typ.	E_{on}	E_{off}	$R_{th(j-s)}$	I_F @ $T_S=25^\circ\text{C}$	V_F @ $T_J=25^\circ\text{C}$ typ.	E_{rr}	$R_{th(j-s)}$	I_{FSM} @ $T_S=25^\circ\text{C}$	$R_{th(j-s)}$		
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W	A	K/W		
600 V - IGBT 3 (Trench)														
SK 75 GB 066 T	77	75	1.45	3.1	2.8	0.94	62	1.35	0.85	1.55	-	-	3	
SK 100 GB 066 T	96	100	1.45	7	6	0.78	108	1.35	1.7	0.91	-	-	3	
SK 150 GB 066 T	124	150	1.45	6.25	5.7	0.55	135	1.35	1.7	0.73	-	-	3	
SK 30 GBB 066 T	40	30	1.45	0.97	1.77	1.65	36	1.45	0.26	2.1	-	-	3	
SK 50 GBB 066 T	60	50	1.45	2.2	1.73	1.11	56	1.50	0.72	1.7	-	-	3	
SK 75 GBB 066 T	77	75	1.45	3.1	2.8	0.94	77	1.35	0.85	1.55	-	-	3	
SK 20 MLI 066	30	20	1.45	0.4	1.07	1.95	30	1.60	0.2	2.46	-	-	3	
SK 30 MLI 066	40	30	1.45	0.97	1.77	1.65	37	1.50	0.26	2.3	-	-	3	
SK 50 MLI 066	60	50	1.45	1.46	2.02	1.11	56	1.50	1.07	1.7	-	-	3	
SK 75 MLI 066 T	83	75	1.45	1.7	2.8	0.75	92	1.50	1.1	1.2	-	-	4	
SK 100 MLI 066 T	105	100	1.45	2.5	4.2	0.65	110	1.35	1.9	0.9	-	-	4	
SK 150 MLI 066 T	151	150	1.45	2.7	5.9	0.55	115	1.50	2.6	0.72	-	-	4	
SK 75 GD 066 T	83	75	1.45	3.1	2.8	0.75	92	1.35	0.85	1.2	-	-	4	
SK 100 GD 066 T	105	100	1.45	7	6	0.65	99	1.30	1.7	0.8	-	-	4	
SK 150 GD 066 T	151	150	1.45	6.25	5.7	0.55	198	1.30	1.7	0.54	-	-	4	
SK 200 GD 066 T	174	200	1.45	13.9	12	0.45	99	1.30	3.4	0.8	-	-	4	
SK 20 GD 066 ET	30	20	1.45	0.34	0.63	1.95	31	1.45	0.2	2.46	-	-	3	
SK 30 GD 066 ET	40	30	1.45	0.97	1.77	1.65	36	1.45	0.26	2.1	-	-	3	
SK 50 GD 066 ET	60	50	1.45	2.2	1.73	1.11	56	1.50	0.72	1.7	-	-	3	
SK 20 DGD L 066 ET	30	20	1.45	0.3	0.6	1.95	27	1.40	0.2	2.46	220	2.15	3	
SK 30 DGD L 066 ET	40	30	1.45	0.55	1.15	1.65	36	1.50	0.53	2.3	370	1.7	3	
SK 50 DGD L 066 T	69	50	1.45	2.2	1.74	0.95	54	1.35	0.73	1.6	370	1.5	4	
SK 75 DGD L 066 T	81	75	1.45	3.1	2.8	0.75	64	1.35	0.9	1.2	700	0.9	4	
SK 100 DGD L 066 T	106	100	1.45	4.4	3.5	0.65	99	1.10	1.45	0.8	700	0.9	4	

Modules - IGBT - SEMITOP

Type	IGBT						Diode				Rectifier		Case	Circuit
	I_C @ $T_S=25^\circ\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_J=25^\circ\text{C}$ typ.	E_{on}	E_{off}	$R_{th(j-s)}$	I_F @ $T_S=25^\circ\text{C}$	V_F @ $T_J=25^\circ\text{C}$ typ.	E_{rr}	$R_{th(j-s)}$	I_{FSM} @ $T_S=25^\circ\text{C}$	$R_{th(j-s)}$		
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W	A	K/W		
600 V - NPT IGBT (Standard)														
SK 45 GAR 063 ²⁾	45	50	2.1	1.4	1.2	1	57	1.45	0.25	1.2	-	-	2	
SK 45 GAL 063 ²⁾	45	50	2.1	1.4	1.2	1	57	1.45	0.25	1.2	-	-	2	
SK 80 GM 063 ²⁾	81	100	2	3	2.3	0.6	105	1.30	0.2	1.2	-	-	2	
SK 45 GB 063 ²⁾	45	50	2.1	1.4	1.2	1	57	1.45	0.25	1.2	-	-	2	
SK 80 GB 063 ²⁾	81	100	2.1	4	3	0.6	79	1.40	1.2	0.9	-	-	3	
SK 15 GH 063 ²⁾	20	15	2	0.71	0.4	1.9	20	1.45	0.45	1.2	-	-	2	
SK 25 GH 063 ²⁾	30	30	2.1	1.1	0.8	1.4	36	1.45	0.25	1.7	-	-	2	
SK 45 GH 063 ²⁾	45	50	2.1	1.4	1.2	1	57	1.30	0.9	1.2	-	-	3	
SK 13 GD 063 ²⁾	18	10	2.1	0.6	0.4	2	22	1.45	0.1	2.3	-	-	3	
SK 25 GD 063 ²⁾	30	30	2.1	1.3	0.9	1.4	36	1.45	0.25	1.7	-	-	3	
SK 45 GD 063 ²⁾	45	50	2.1	1.4	1.2	1	36	1.45	0.25	1.7	-	-	3	
SK 25 GAD 063 T ²⁾	30	30	2.1	1.3	0.9	1.4	36	1.45	0.25	1.7	-	-	3	

Modules - IGBT - SEMITOP

Type	IGBT						Diode				Rectifier		Case	Circuit
	I_C @ $T_S=25^\circ\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_J=25^\circ\text{C}$ typ.	E_{on}	E_{off}	$R_{th(j-s)}$	I_F @ $T_S=25^\circ\text{C}$	V_F @ $T_J=25^\circ\text{C}$ typ.	E_{rr}	$R_{th(j-s)}$	I_{FSM} @ $T_S=25^\circ\text{C}$	$R_{th(j-s)}$		
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W	A	K/W		
600 V - NPT IGBT (Ultrafast)														
SK 50 GAR 065	54	60	2	1.1	0.7	0.85	57	1.30	0.2	1.2	-	-	2	
SK 50 GAL 065	54	60	2	1.1	0.7	0.85	57	1.30	0.2	1.2	-	-	2	
SK 55 GARL 065 E	54	60	1.7	1.1	0.76	0.85	36	1.45	0.9	1.7	-	-	3	
SK 75 GARL 065 E	80	90	1.7	2.71	2.75	0.6	57	1.30	0.2	1.2	-	-	3	
SK 50 GB 065	54	60	2	1.1	0.7	0.85	64	1.45	0.55	1.1	-	-	2	
SK 50 GARL 065 F	54	60	1.7	1.03	0.8	0.85	82	1.70	-	2.3	-	-	2	
SK 50 GARL 065 USA	54	60	1.7	1.07	0.76	0.85	64	1.40	-	2.3	-	-	2	
SK 50 GH 065 F	54	60	2	1.07	1.76	0.85	82	1.10	0.42	1.1	-	-	3	
SK 8 BGD 065 E ²⁾	12	6	2	0.22	0.12	2.6	13	1.35	-	2.7	220	2.15	2	
SK 9 DGD 065 ET	12	6	2	0.22	0.12	2.6	20	1.35	0.31	2.7	220	2.15	3	
SK 20 DGD 065 ET	26	20	2	0.66	0.4	1.7	25	1.60	-	1.7	370	1.7	3	
SK 25 DGD 065 ET ²⁾	30	20	1.8	0.8	0.55	1.4	36	1.45	-	1.7	370	1.7	3	
SK 35 GD 065 ET	45	50	2	1.3	0.6	1	36	1.90	0.9	1.7	-	-	3	
SK 10 BGD 065 ET	17	6	2	0.18	0.13	2	22	1.30	0.18	2.3	220	2.7	3	
SK 9 BGD 065 ET	12	6	2	0.22	0.12	2.6	20	1.35	0.31	2.7	220	2.15	3	
SK 10 DGD 065 ET	17	6	2	0.18	0.13	2	22	1.30	0.18	2.3	220	2.7	3	
SK 8 DGD 065 ET ²⁾	12	6	2	0.22	0.12	2.6	13	1.35	-	2.7	-	2.8	3	
SK 15 DGD 065 ET ²⁾	19	10	2	0.3	0.22	1.9	22	1.40	0.24	2.3	220	2.7	3	
SK 20 DGD 065 ET	24	20	2	0.69	0.39	1.7	25	1.60	-	1.7	220	2	3	

Modules - IGBT - SEMITOP

Type	IGBT						Diode				Rectifier		Case	Circuit
	I_C @ $T_S=25^\circ\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_J=25^\circ\text{C}$ typ.	E_{on}	E_{off}	$R_{th(j-s)}$	I_F @ $T_S=25^\circ\text{C}$	V_F @ $T_J=25^\circ\text{C}$ typ.	E_{rr}	$R_{th(j-s)}$	I_{FSM} @ $T_S=25^\circ\text{C}$	$R_{th(j-s)}$		
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W	A	K/W		
1200 V - IGBT 3 (Trench)														
SK 8 GD 126 ²⁾	15	8	1.7	0.78	0.96	2	13	1.90	20.6	2.8	-	-	2	
SK 50 GD 126 T	68	50	1.7	4.6	6.3	0.6	62	1.35	3.6	1	-	-	4	
SK 75 GD 126 T	88	75	1.7	11.3	10	0.5	91	1.46	6	0.7	-	-	4	
SK 100 GD 126 T	114	100	1.7	9.8	11.7	0.4	118	1.50	7.3	0.55	-	-	4	
SK 10 GD 126 ET	15	8	1.7	1	1	2	25	1.90	1.4	2.1	-	-	3	
SK 15 GD 126 ET	22	15	1.7	2	1.8	1.6	25	1.60	1.4	2.1	-	-	3	
SK 25 GD 126 ET	32	25	1.7	3.3	3.1	1.2	28	1.80	2.1	1.9	-	-	3	
SK 35 GD 126 ET	40	35	1.7	4.6	4.3	1.05	34	1.80	2.9	1.7	-	-	3	
SK 10 DGD L 126 ET	15	8	1.7	1	1	2	25	1.90	1.4	2.1	220	2.7	3	
SK 15 DGD L 126 ET	22	15	1.7	2	1.8	1.6	25	1.60	1.1	2.1	220	2	3	
SK 25 DGD L 126 T	41	25	1.7	2.8	3.1	0.9	30	1.50	2	1.7	370	1.5	4	
SK 35 DGD L 126 T	52	35	1.7	3.7	4.8	0.75	38	1.50	3	1.5	370	1.25	4	
SK 50 DGD L 126 T	68	50	1.7	4.6	6.3	0.6	62	1.35	3.6	1	700	0.9	4	
1200 V - IGBT 4 (Trench)														
SK 25 GB 12T4	37	25	1.85	2.27	2.7	1.31	30	2.40	1.28	1.91	-	-	2	
SK 35 GB 12T4	44	35	1.85	3.27	3.3	1.21	40	2.30	1.46	1.55	225	-	2	
SK 50 GB 12T4 T	71	50	1.85	8.3	5	0.9	50	2.20	2.15	1.24	-	-	3	
SK 75 GB 12T4 T	80	75	1.85	13.6	8.2	0.74	70	2.10	3.39	0.97	-	-	3	
SK 100 GB 12T4 T	100	100	1.85	16.6	10	0.6	85	2.25	5.2	0.87	-	-	3	
SK 50 GH 12T4 T	75	50	1.8	8.3	5	0.65	56	2.20	2.15	1.05	-	-	4	
SK 100 GH 12T4 T	126	100	1.8	16.6	10	0.43	102	2.20	5.2	0.62	-	-	4	
SK 25 GH 12T4 ¹⁾	-	25	1.85	2.27	2.7	1.11	26	2.41	1.28	2.15	-	-	3	
SK 50 GD 12T4 T	75	50	1.85	8.3	5	0.65	60	2.20	2.15	0.97	-	-	4	
SK 75 GD 12T4 T	102	75	1.85	13.6	8.2	0.51	83	2.20	3.38	0.75	-	-	4	
SK 100 GD 12T4 T	126	100	1.85	16.6	10	0.43	102	2.25	5.2	0.62	-	-	4	
SK 10 GD 12T4 ET	17	8	1.85	0.41	0.76	2.2	15	2.38	0.41	2.7	-	-	3	
SK 15 GD 12T4 ET	27	15	1.85	0.83	1.52	1.65	21	2.38	0.82	2.34	-	-	3	
SK 25 GD 12T4 ET	37	25	1.85	2.27	2.7	1.31	30	2.40	1.28	1.91	-	-	3	
SK 35 GD 12T4 ET	44	35	1.85	3.27	3.3	1.21	40	2.30	1.46	1.55	-	-	3	
SK 10 DGD L 12T4 ET	17	8	1.85	0.41	0.75	2.2	15	2.38	0.41	2.7	220	2	3	
SK 15 DGD L 12T4 ET	27	15	1.85	0.82	1.52	1.65	21	2.38	0.82	2.34	220	2	3	
SK 25 DGD L 12T4 T	45	25	1.85	2.27	2.7	0.96	30	2.40	-	1.7	370	1.25	4	
SK 35 DGD L 12T4 T	58	35	1.85	3.27	3.3	0.8	46	2.30	1.46	1.37	370	1.25	4	
SK 50 DGD L 12T4 T	75	50	1.85	8.3	5	0.65	60	2.22	2.15	0.97	700	0.9	4	

Modules - IGBT - SEMITOP

Type	IGBT						Diode				Rectifier		Case	Circuit
	I_C @ $T_S=25^\circ C$	I_{Cnom}	$V_{CE(sat)}$ @ $T_J=25^\circ C$ typ.	E_{on}	E_{off}	$R_{th(j-s)}$	I_F @ $T_S=25^\circ C$	V_F @ $T_J=25^\circ C$ typ.	E_{rr}	$R_{th(j-s)}$	I_{FSM} @ $T_S=25^\circ C$	$R_{th(j-s)}$		
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W	A	K/W		
1200 V - NPT IGBT (Ultrafast)														
SK 60 GAR 125	51	50	3.2	8.36	3.32	0.6	43	2.00	2	1.16	-	-	2	
SK 60 GAL 125	51	50	3.2	8.36	3.32	0.6	43	2.00	2	1.16	-	-	2	
SK 60 GB 125	51	50	3.2	8.36	3.32	0.6	57	-	2	0.9	-	-	3	
SK 80 GB 125 T	85	75	3.2	9.9	5	0.32	90	2.00	1	0.65	-	-	3	

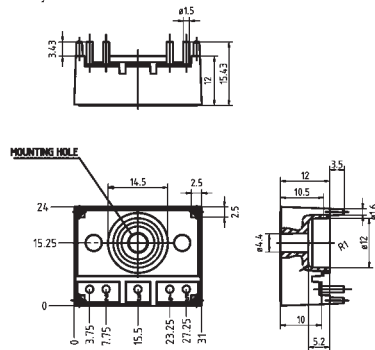
Footnotes

- 1) New
- 2) Not for New Design

Cases

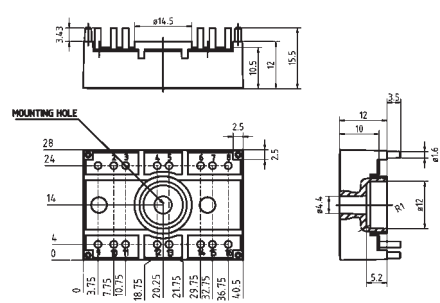
SEMITOP 1

dimensions in mm
tolerance system: ISO 2768-m



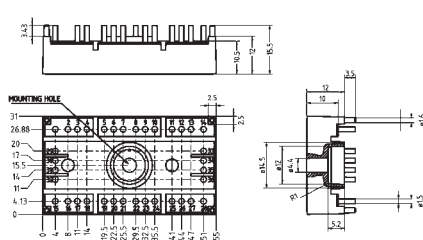
SEMITOP 2

dimensions in mm
tolerance system: ISO 2768-m



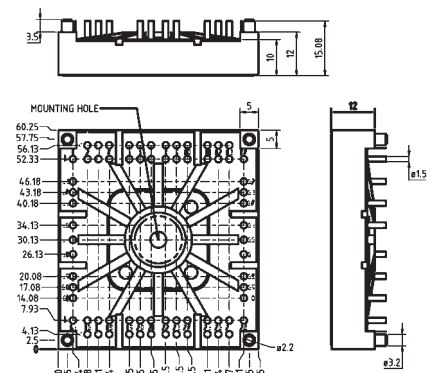
SEMITOP 3

dimensions in mm
tolerance system: ISO 2768-m



SEMITOP 4

dimensions in mm
tolerance system: ISO 2768-m



Dimensions in mm

IPM Intelligent Power Module

MiniSKiiP® IPM

CIB
6-pack



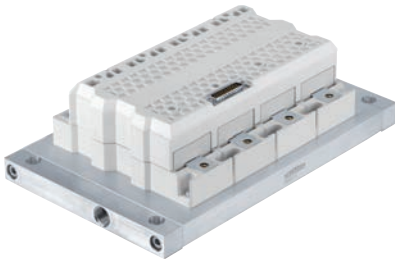
600V
up to
1200V

I_{Cnom} in A

0 50 100 600 1200 1800 2400 3600

SKiiP® 4

half bridge



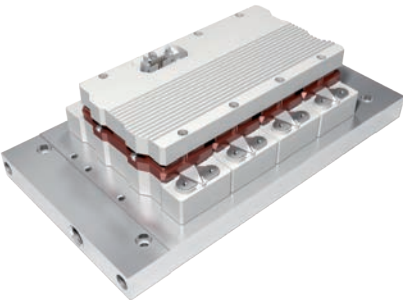
1200V
up to
1700V

I_{Cnom} in A

0 50 100 600 1200 1800 2400 3600

SKiiP® 3

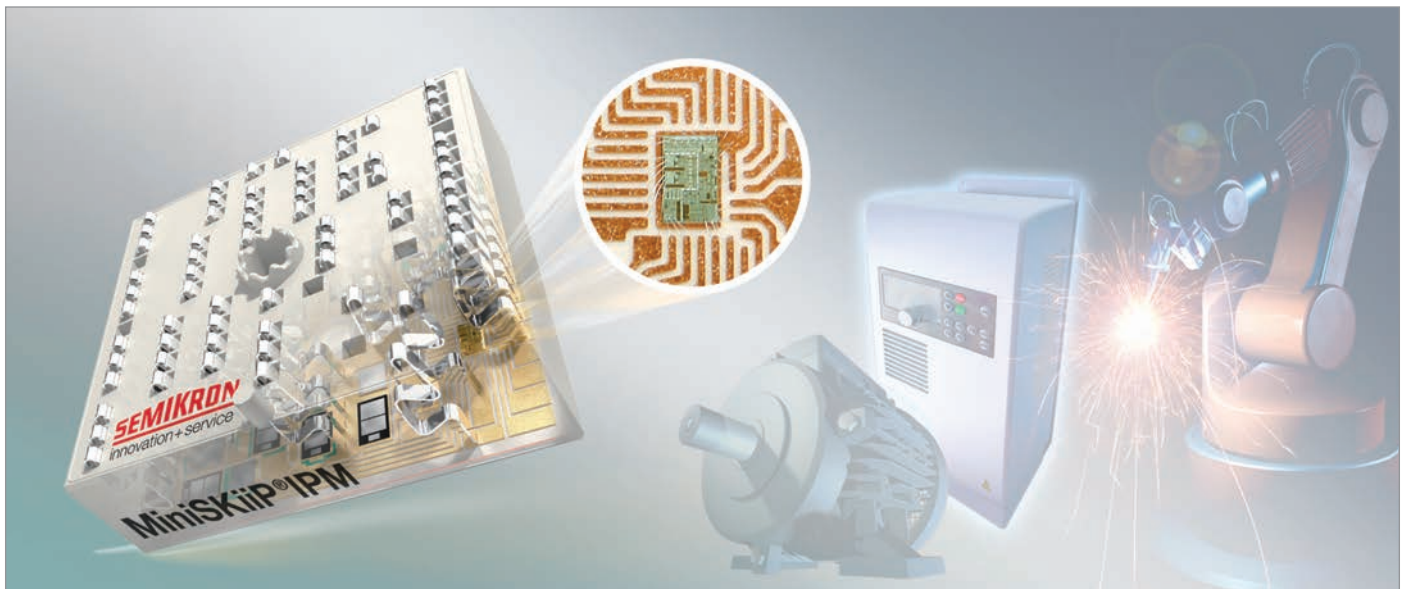
6-pack
half bridge



1200V
up to
1700V

I_{Cnom} in A

0 50 100 600 1200 1800 2400 3600



Compact 3-phase inverter design through high power density

Applications

MiniSKiiP IPM is SEMIKRON's new intelligent power module family for medium power applications. Each IPM incorporates a latch-up free HVIC SOI gate driver with the advanced level shifter concept. The gate driver features a 3.3 V/ 5 V/ 15 V compatible input signal interface and provides short-circuit current detection using an external shunt resistor, integrated under-voltage lockout for all channels and interlock logic with dead time setting for cross-conduction protection. A built-in temperature sensor with NTC characteristics allows for the permanent monitoring of the intelligent power module temperature by using the external μC .

Product range

MiniSKiiP IPM is suitable for industrial and consumer drives up to 15 kW, as well as for process control and solar applications. Using state-of-the-art Trench-Field-Stop IGBTs, the IPMs are available in 600 V as CIB and 1200 V as a 6-pack. The modules are RoHS compliant.

Benefits

The IPM combines a base plate-free package with the proven pressure contact technology for quick and easy solder-free assembly. All power, control and auxiliary contacts are connected directly to the printed circuit board via springs, resulting in more reliable electrical connections under more severe vibration and shock conditions. The simple one-step mounting of module, printed circuit board and heat sink with a single standard screw reduces assembly steps and costs.

Modules - IPM - MiniSKiiP

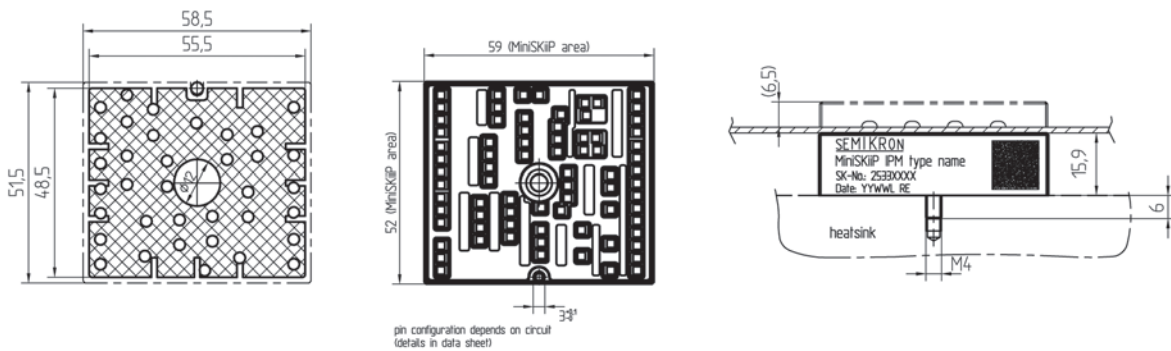
Type	IGBT						Diode				Rectifier		Case	Circuit
	I_C @ $T_S=25^\circ\text{C}$ A	I_{Cnom} A	$V_{CE(sat)}$ @ $T_j=25^\circ\text{C}$ typ. V	E_{on} mJ	E_{off} mJ	$R_{th(j-s)}$ K/W	I_F @ $T_S=25^\circ\text{C}$ A	V_F @ $T_j=$ V	E_{rr} mJ	$R_{th(j-s)}$ K/W	I_{FSM} @ $T_S=25^\circ\text{C}$ A	$R_{th(j-s)}$ K/W		
600 V - IGBT 3 (Trench)														
SKiiP 25NAB1066V3 ¹⁾	41	30	1.5	1.1	1	1.4	37	1.6	0.7	1.8	370	1.7	IPM 2	
SKiiP 26NAB1066V3 ¹⁾	59	50	1.45	2.4	2.1	1.1	51	1.5	1	1.6	370	1.7	IPM 2	
1200 V - IGBT 4 (Trench)														
SKiiP 25AC112T4V2 ¹⁾	62	50	1.85	6.6	5.7	0.84	59	2.25	3	0.99	-	-	IPM 2	

Footnotes

¹⁾ New

Cases

MiniSKiiP IPM 2



Dimensions in mm



Sintered chips – for high operating temperatures

Applications

The success story of the SKiiP family has progressed hand in hand with the advancement of the wind power market. The 4th generation SKiiP modules are a further improvement of the powerful SKiiP series. The mainstay of SKiiP4 modules is the wind power sector, with approximately 57 GW out of the 122 GW of wind power installed worldwide (at the end of 2009) featuring SEMIKRON solutions, in many cases SKiiP technology. Besides wind power applications, SKiiP modules can also be found in elevators, solar power and railway applications - in fact, in any area where powerful, safe and reliable IGBT IPMs are a must.

Product range

SKiiP4 is available for 1200 V and 1700 V. In both of these voltage classes, SKiiP4 modules come in the topologies 3GB 1800 A, 4GB 2400 A and - new to the SKiiP family - 6GB 3600 A. The wide range of accessories is now available for both SKiiP3 and SKiiP4. Among them the fiberoptic boards, the boards for paralleling of SKiiP systems and the adapter board for connection SKiiP4 to SKiiP3 controller.

Benefits

SKiiP4 is the most powerful IPM on the market. SKiiP4 modules enable the production of converter units with outputs of up to 2.1 MW. The power semiconductors used in SKiiP4 modules can be operated at a junction temperature of up to 175°C. To make sure these components can be reliably used at these temperatures, the power circuitry is 100% solder-free. Instead, sinter technology is used to create a sintered silver layer instead of the solder layer which could limit the service life of power modules. Reliability during active and passive thermal cycling is greatly improved. A further benefit is the better load cycling capability as compared to solder-based modules. The integrated gate driver in the SKiiP4 sets new standards in terms of reliability and functionality. The digital driver guarantees safe isolation between the primary and secondary side, both for switching signals and all measurement parameters, such as temperature and DC link voltage. This means the user no longer has to introduce complex and costly circuit components to provide safe isolation. For the first time, the SKiiP drive features a CANopen diagnosis channel for the integration of additional functions.

Modules - IPM - SKiiP 3 / 4

Type	I_C @ $T_S=25^\circ\text{C}$	I_{nom}	IGBT		Diode			Case	Case Options F=F-Option U=U-Option S=SKiFace Adapter	Circuit
			$V_{CE(sat)}$ @ $T_J=25^\circ\text{C}$ typ.	$E_{on} + E_{off}$	I_F @ $T_S=25^\circ\text{C}$	V_F @ $T_J=25^\circ\text{C}$ typ.	E_{rr}			
	A	A	V	mJ	A	V	mJ			
1200 V - IGBT 3 (Trench) - SKiiP 3										
SKiiP 603 GD123-3DUL V3	627	600	1.7	195	508	1.50	28	S33	-	
SKiiP 603 GD123-3DUW V3	627	600	1.7	195	508	1.50	28	S33	-	
SKiiP 613 GD123-3DUL V3	577	600	1.7	195	466	1.50	28	S33	-	
SKiiP 613 GD123-3DUW V3	577	600	1.7	195	466	1.50	28	S33	-	
SKiiP 1213 GB123-2DL V3	1145	1200	1.7	390	925	1.50	56	S23	F,U	
SKiiP 1213 GB123-2DW V3	1145	1200	1.7	390	925	1.50	56	S23	F,U	
SKiiP 1813 GB123-3DL V3	1695	1800	1.7	585	1411	1.50	84	S33	F,U	
SKiiP 1813 GB123-3DW V3	1695	1800	1.7	585	1411	1.50	84	S33	F,U	
SKiiP 2413 GB123-4DL V3	2280	2400	1.7	780	1807	1.50	112	S43	F,U	
SKiiP 2413 GB123-4DW V3	2280	2400	1.7	780	1807	1.50	112	S43	F,U	
1200 V - IGBT 4 (Trench) - SKiiP 4										
SKiiP 1814 GB12E4-3DUL	2345	1800	2.01	1260	1776	2.33	150	S34	F,S	
SKiiP 1814 GB12E4-3DUW	2345	1800	2.01	1260	1776	2.33	150	S34	F,S	
SKiiP 2414 GB12E4-4DUL	3109	2400	2.01	1680	2369	2.33	200	S44	F,S	
SKiiP 2414 GB12E4-4DUW	3109	2400	2.01	1680	2369	2.33	200	S44	F,S	
SKiiP 3614 GB12E4-6DUL	4664	3600	2.01	2520	3558	2.33	300	S64	F,S	
SKiiP 3614 GB12E4-6DUW	4664	3600	2.01	2520	3558	2.33	300	S64	F,S	
1700 V - IGBT 3 (Trench) - SKiiP 3										
SKiiP 513 GD172-3DUL V3	540	500	1.9	288	438	2.00	43	S33	-	
SKiiP 513 GD172-3DUW V3	540	500	1.9	288	438	2.00	43	S33	-	
SKiiP 603 GD172-3DUL V3	587	570	1.9	288	476	2.00	43	S33	-	
SKiiP 603 GD172-3DUW V3	570	570	1.9	288	476	2.00	43	S33	-	
SKiiP 1013 GB172-2DL V3	1072	1000	1.9	575	879	2.00	86	S23	F,U	
SKiiP 1013 GB172-2DW V3	1072	1000	1.9	575	879	2.00	86	S23	F,U	
SKiiP 1203 GB172-2DL V3	1159	1200	1.9	575	961	2.00	86	S23	F,U	
SKiiP 1203 GB172-2DW V3	1159	1200	1.9	575	961	2.00	86	S23	F,U	
SKiiP 1513 GB172-3DL V3	1589	1500	1.9	863	1336	2.00	128	S33	F,U	
SKiiP 1513 GB172-3DW V3	1589	1500	1.9	863	1336	2.00	128	S33	F,U	
SKiiP 1803 GB172-3DL V3	1744	1800	1.9	863	1454	2.00	128	S33	F,U	
SKiiP 1803 GB172-3DW V3	1744	1800	1.9	863	1454	2.00	128	S33	F,U	
SKiiP 2013 GB172-4DL V3	2102	2000	1.9	1150	1758	2.00	171	S43	F,U	
SKiiP 2013 GB172-4DW V3	2102	2000	1.9	1150	1758	2.00	171	S43	F,U	
SKiiP 2403 GB172-4DL V3	2282	2400	1.9	1150	1921	2.00	171	S43	F,U	
SKiiP 2403 GB172-4DW V3	2282	2400	1.9	1150	1921	2.00	171	S43	F,U	

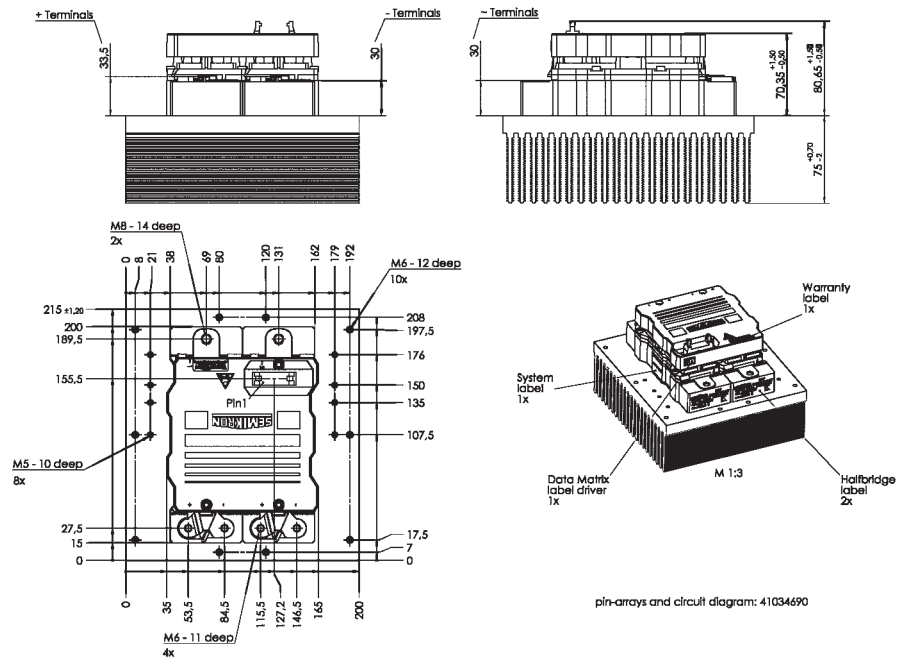
Modules - IPM - SKiiP 3 / 4

Type	I_C @ $T_S=25^\circ\text{C}$	I_{nom}	IGBT		Diode			Case	Case Options F=F-Option U=U-Option S=SKiFace Adapter	Circuit
			$V_{CE(sat)}$ @ $T_J=25^\circ\text{C}$ typ.	$E_{on} + E_{off}$	I_F @ $T_S=25^\circ\text{C}$	V_F @ $T_J=25^\circ\text{C}$ typ.	E_{rr}			
	A	A	V	mJ	A	V	mJ			
1700 V - IGBT 4 (Trench) - SKiiP 4										
SKiiP 1814 GB17E4-3DUL	2547	1800	2.12	2130	1771	2.02	498	S34	F,S	
SKiiP 1814 GB17E4-3DUW	2547	1800	2.12	2130	1771	2.02	498	S34	F,S	
SKiiP 2414 GB17E4-4DUL	3385	2400	2.12	2840	2362	2.02	664	S44	F,S	
SKiiP 2414 GB17E4-4DUW	3385	2400	2.12	2840	2362	2.02	664	S44	F,S	
SKiiP 3614 GB17E4-6DUL	5078	3600	2.12	6840	3547	2.02	996	S64	F,S	
SKiiP 3614 GB17E4-6DUW	5078	3600	2.12	6840	3547	2.02	996	S64	F,S	

Type	Description
F-Option SKiiP4	
SKiiP4 F-Option	Fiber optic control board for SKiiP4
SKiiP3 Parallel Board	
SKiiP3 Parallel Board 4-fold	Board for paralleling of 4 SKiiP3, F-Option usage possible
SKiiP3 Parallel Board 3-fold	Board for paralleling of 3 SKiiP3, F-Option usage possible
SKiiP3 Parallel Board 2-fold	Board for paralleling of 2 SKiiP3, F-Option usage possible
SKiiP4 Parallel Board	
SKiiP4 Parallel Board 4-fold without F-Option	Board for paralleling of 4 SKiiP4, F-Option usage not possible
SKiiP4 Parallel Board 4-fold F-Option	Board for paralleling of 4 SKiiP4, F-Option usage possible
SKiiP4 Parallel Board 3-fold without F-Option	Board for paralleling of 3 SKiiP4, F-Option usage not possible
SKiiP4 Parallel Board 3-fold F-Option	Board for paralleling of 3 SKiiP4, F-Option usage possible
SKiiP4 Parallel Board 2-fold without F-Option	Board for paralleling of 2 SKiiP4, F-Option usage not possible
SKiiP4 Parallel Board 2-fold F-Option	Board for paralleling of 2 SKiiP4, F-Option usage possible
SKiFace Adapter Board	
SKiiP4 SKiFace Adapter UZK	Adapter board to connect SKiiP4 to SKiiP3 controller with DC-Link voltage measurement function
SKiiP4 SKiFace Adapter Temp	Adapter board to connect SKiiP4 to SKiiP3 controller with temperatur measurement function

Cases SKiiP 3

Case S 23 mounted on P3016 heat sink



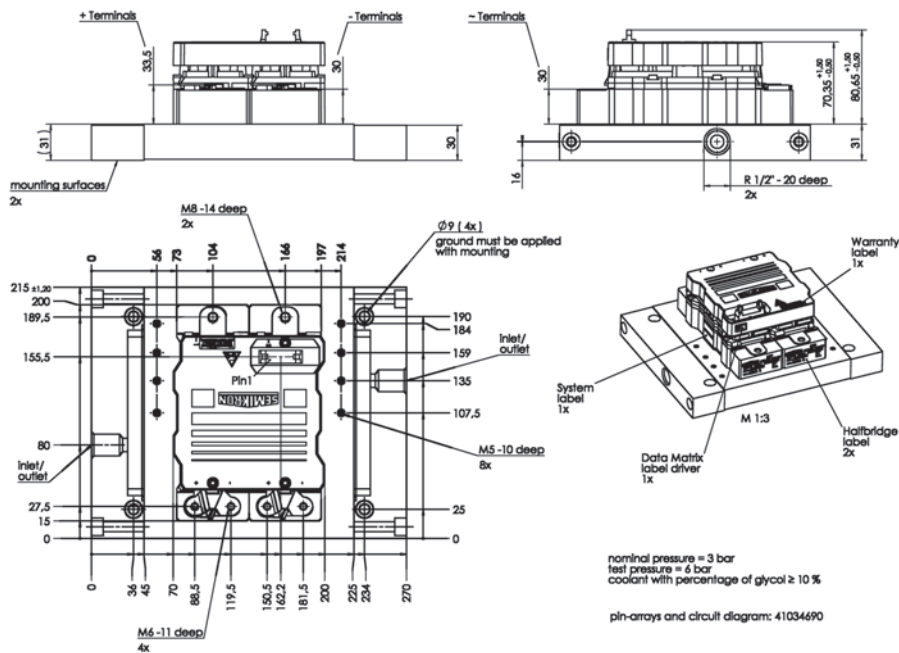
weight without heat sink:

1,7 kg

P3016:

4,4 kg

Case S 23 mounted on liquid cooled heat sink NWK 40



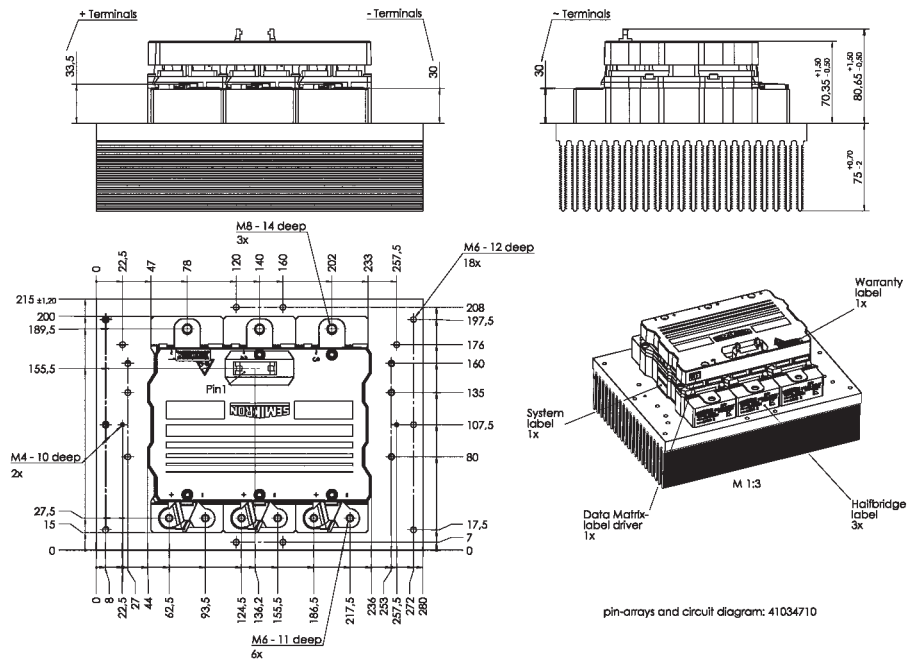
NWK 40:

2,8 kg

Dimensions in mm

Cases SKiiP 3

Case S 33 mounted on P3016 heat sink



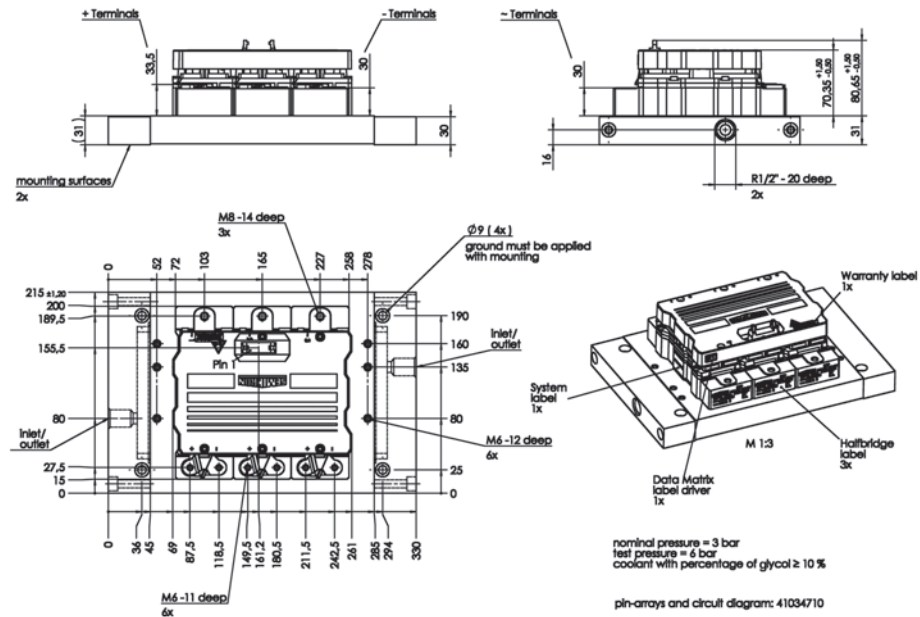
weight without heat sink:

2,4 kg

P3016:

6,2 kg

Case S 33 mounted on liquid cooled heat sink NWK 40



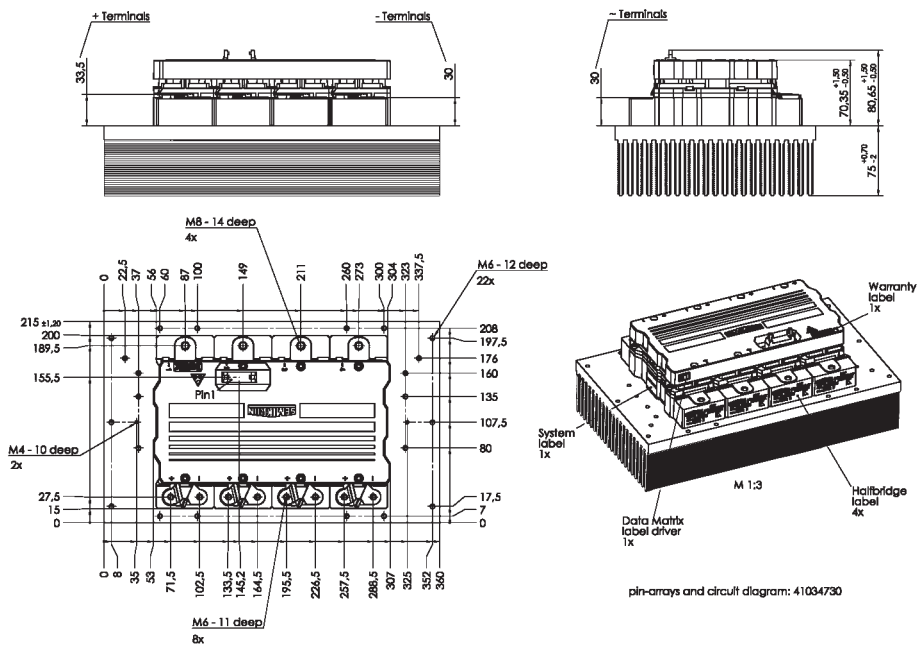
NWK 40:

5,2 kg

Dimensions in mm

Cases SKiiP 3

Case S 43 mounted on P3016 heat sink



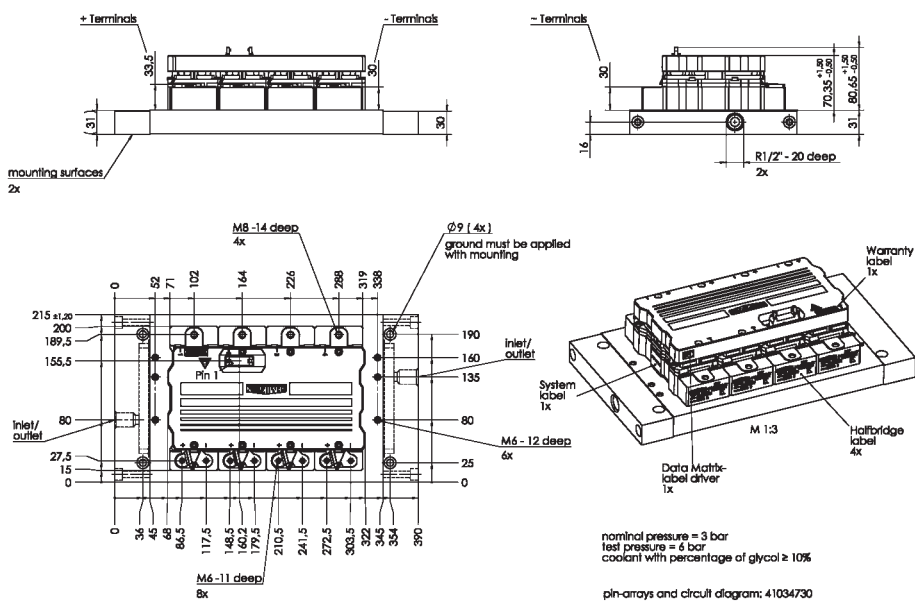
weight without heat sink:

3,1 kg

P3016:

8,0 kg

Case S 43 mounted on liquid cooled heat sink NWK 40



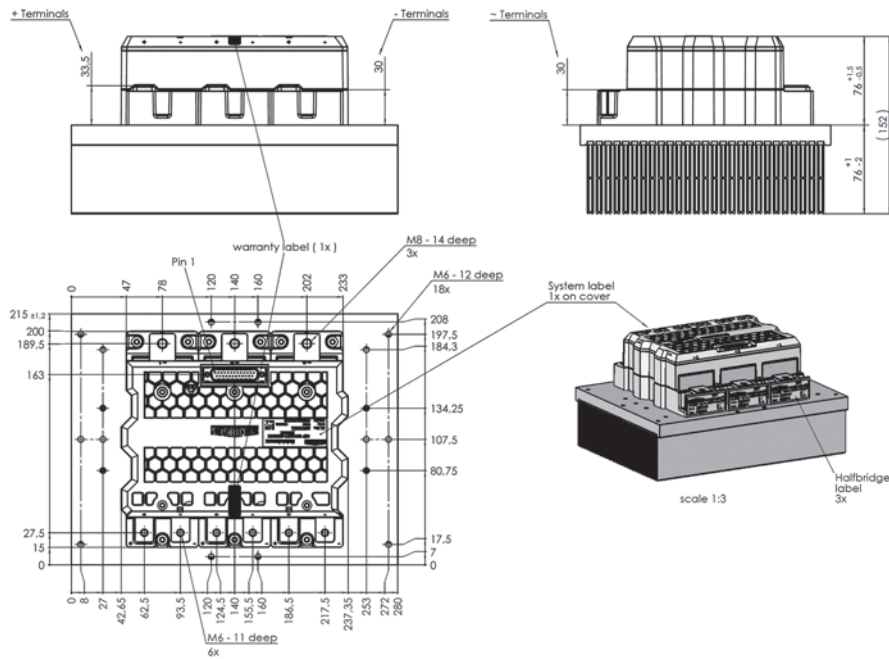
NWK 40:

6,2 kg

Dimensions in mm

Cases SKiiP 4

Case S 34 mounted on P4016 heat sink



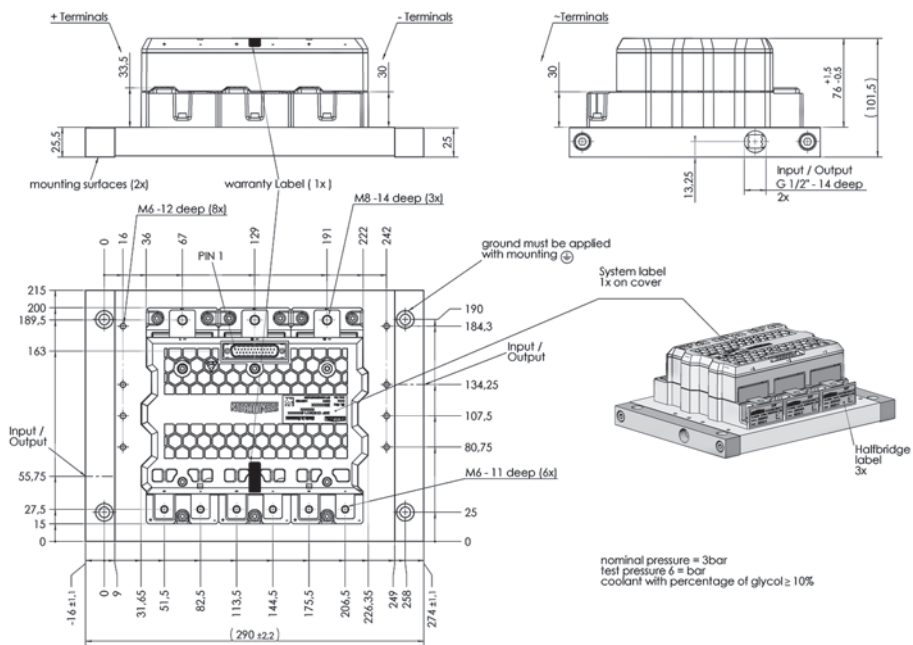
weight without heat sink:

2,48 kg

P4016:

5,9 kg

Case S 34 mounted on liquid cooled heat sink NHC



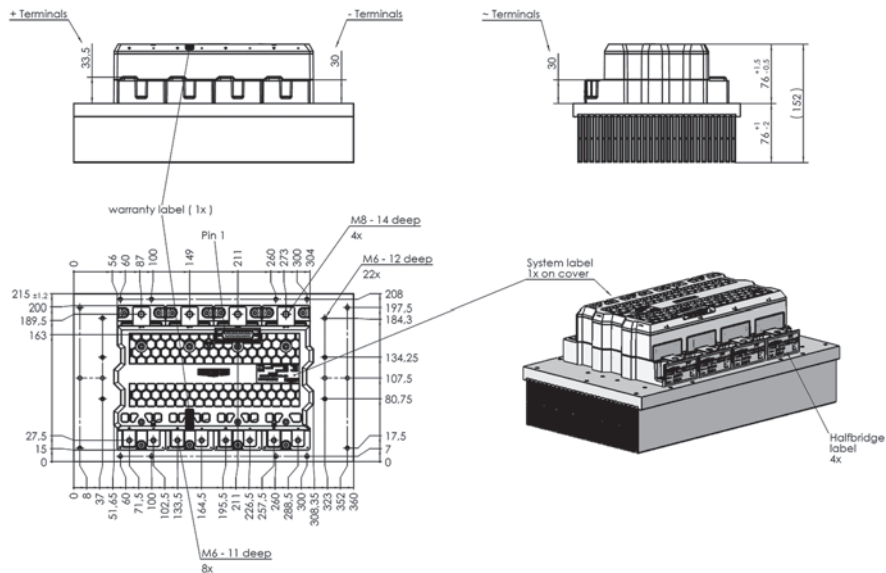
NHC:

3,49 kg

Dimensions in mm

Cases SKiiP 4

Case S 44 mounted on P4016 heat sink



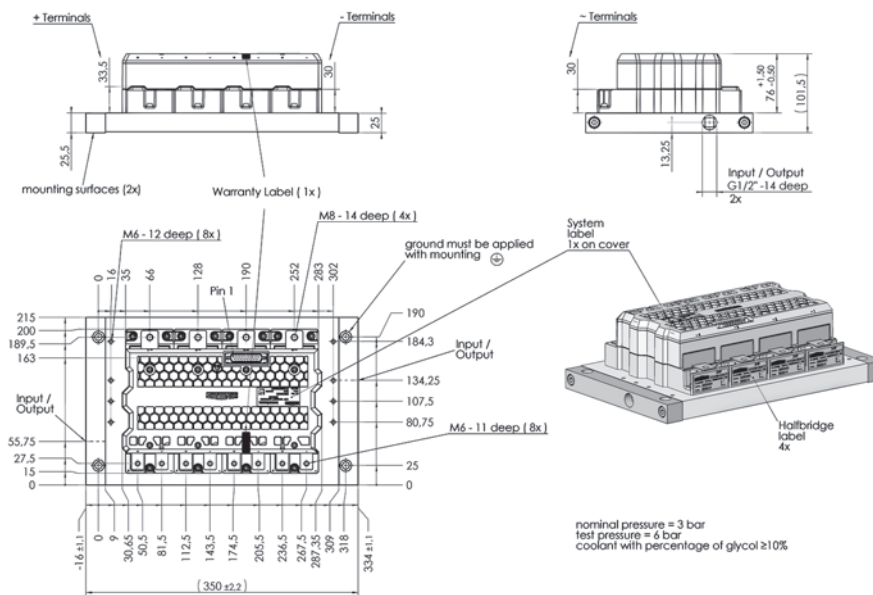
weight without heat sink:

3,22 kg

P4016:

7,55 kg

Case S 44 mounted on liquid cooled heat sink NHC



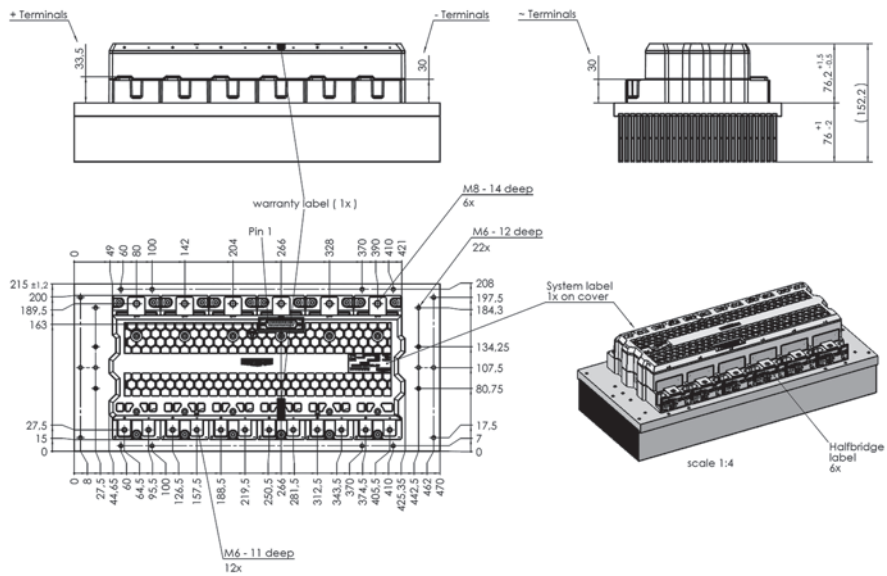
NHC:

4,25 kg

Dimensions in mm

Cases SKiiP 4

Case S 64 mounted on P4016 heat sink



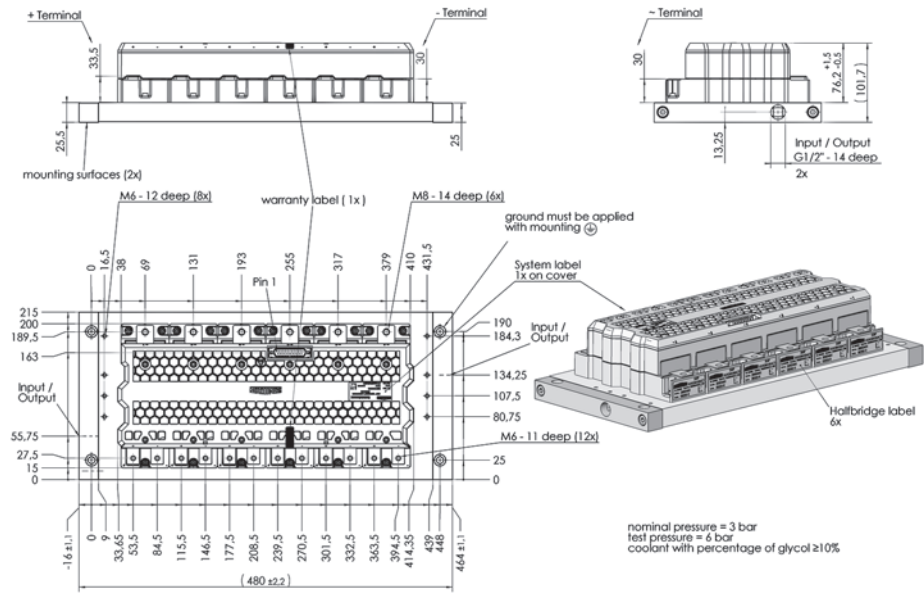
weight without heat sink:

4,84 kg

P4016:

9,9 kg

Case S 64 mounted on liquid cooled heat sink NHC



NHC:

5,77 kg

Dimensions in mm

MOSFET Modules

SEMITRANS®

single switch



100V
up to
200V

I_D @ 25°C in A

0

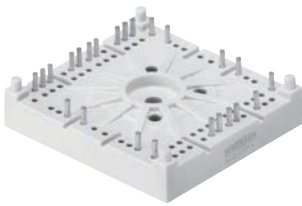
100

200

300

SEMITOP®

6-pack
H-bridge
half bridge



55V
up to
600V

I_D @ 25°C in A

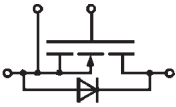
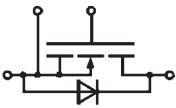
0

100

200

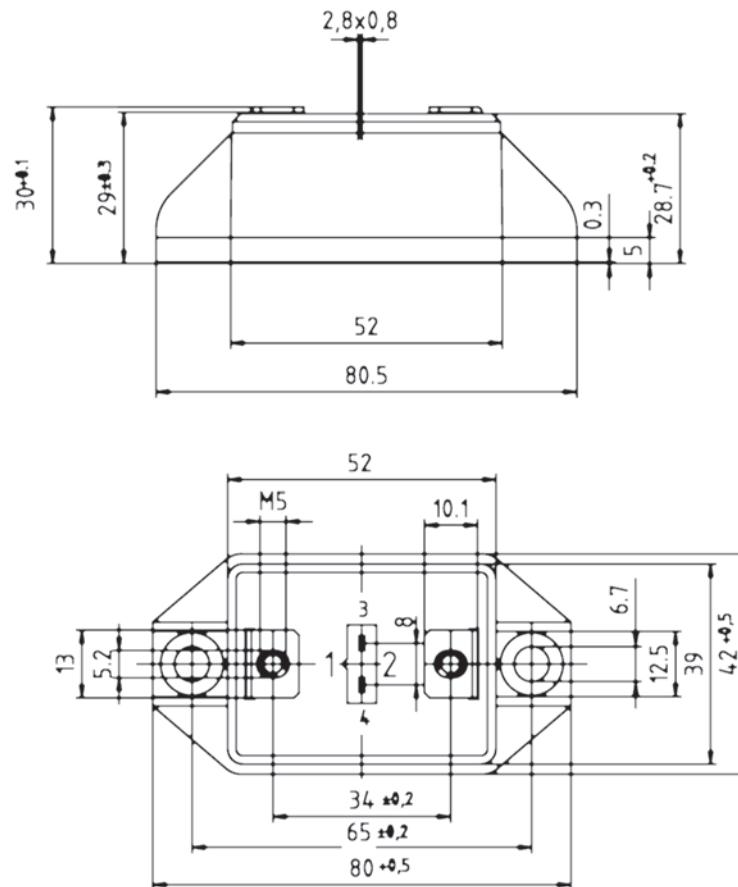
300

Modules - MOSFET - SEMITRANS

Type	V_{DS} V	I_D @ $T_c = 25^\circ\text{C}$ A	$R_{DS(on)}$ @ $T_j = 25^\circ\text{C typ.}$ $m\Omega$	$R_{th(j-c)}$ K/W	Case	Circuit
100 V						
SKM 111 AR	100	200	7	0.18	M1	
200 V						
SKM 180 A020	200	180	9	0.18	M1	

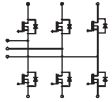
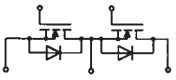
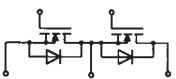
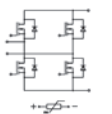
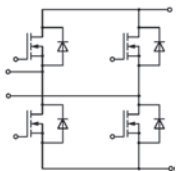
Cases

SEMITRANS M1



Dimensions in mm

Modules - MOSFET - SEMITOP

Type	V_{DS} V	I_D @ $T_c = 25^\circ\text{C}$ A	$R_{DS(on)}$ @ $T_j = 25^\circ\text{C}$ typ. $m\Omega$	$R_{th(j-s)}$ K/W	Case	Circuit
55 V						
SK 80 MBBB 055	55	117	2.2	1.1	3	
75 V						
SK 300 MB 075	75	290	-	0.45	3	
100 V						
SK 260 MB 10	100	230	-	0.45	3	
SK 85 MH 10 T	100	80	-	1.1	2	
600 V						
SK 60 MH 60 ¹⁾	600	60	33	0.54	4	

For detailed case drawings please see page 26

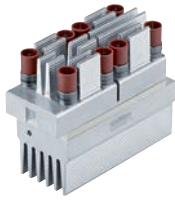
Footnotes

¹⁾ New

Thyristor / Diode Modules

SEMiSTART®

W1C



I_{overload} in A

0 500 1000 1500 2000 2500 3000



SEMiPACK® 3 / 4 / 5 / 6

single switch
half bridge



800V
up to
2200V

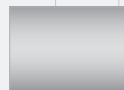


SEMiPACK® 2 / 3

single switch
half bridge



200V
up to
2200V



SEMiPACK® 0 / 1

single switch
half bridge



400V
up to
2200V



$I_{\text{TAV / FAV}}$ in A

0 20 40 60 80 100 200 300 400 500 600 700 800 900 1000 1100 1200

SEMiX® 1 / 2

half bridge



1600V



$I_{\text{TAV / FAV}}$ in A

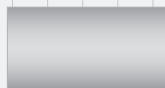
0 20 40 60 80 100 200 300 400 500 600 700 800 900 1000 1100 1200

SEMiTOP® 1 / 2 / 3

W1C, WT, W3C
single switch



800V
up to
1600V



$I_{\text{TAV / FAV}}$ in A

0 20 40 60 80 100 200 300 400 500 600 700 800 900 1000 1100 1200

SEMiPONT® 5

W3C



1200V
up to
1600V



I_{RMS} in A

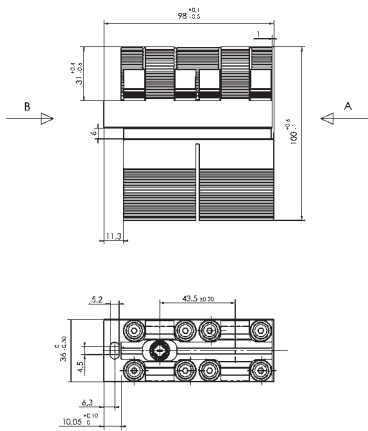
0 20 40 60 80 100 200 300 400 500 600 700 800 900 1000 1100 1200

Modules - Thyristors - SEMiSTART

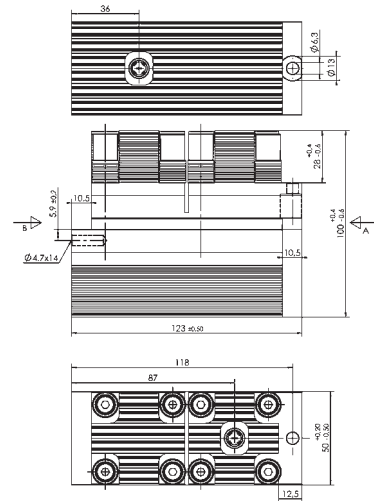
Type	V_{RRM} V_{DRM}	$I_{overload}$ $W1C$ (for 20s)	T_C	I_{TSM} @ $T_j = 125^\circ C$	$V_{T(TO)}$ @ $T_j = 125^\circ C$	r_T @ $T_j = 125^\circ C$	$R_{th(j-s)}$ cont. per chip	T_j (for 20s)	Case	Circuit
	V	A	$^\circ C$	A	V	m Ω	K/W	$^\circ C$		
SKKQ 560	1400-1800	560	150	5200	0.9	0.9	0.106	150	1	
SKKQ 800	1400-1800	800	150	5200	0.9	0.8	0.106	150	2	
SKKQ 1200	1400-1800	1225	150	8000	0.9	0.5	0.066	150	2	
SKKQ 1201	1400-1800	1225	150	8000	0.9	0.5	0.066	150	2a	
SKKQ 1500	1400-1800	1500	150	15000	0.85	0.3	0.037	150	2	
SKKQ 1501	1400-1800	1500	150	15000	0.85	0.3	0.037	150	2a	
SKKQ 2001	1400-1800	1950	150	15000	0.85	0.3	0.051	150	3a	
SKKQ 3000	1400-1800	3080	150	25500	0.95	0.18	0.026	150	3	
SKKQ 3001	1400-1800	3080	150	25500	0.95	0.18	0.026	150	3a	

Cases

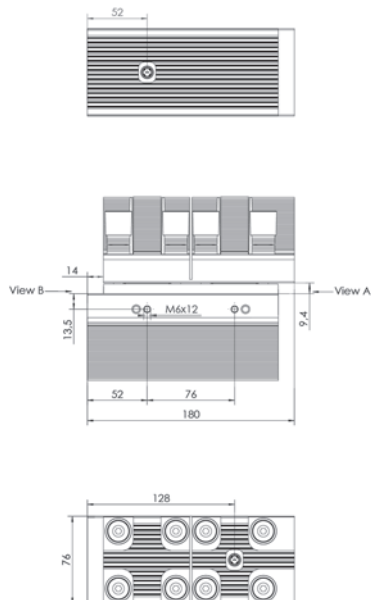
SEMiSTART 1



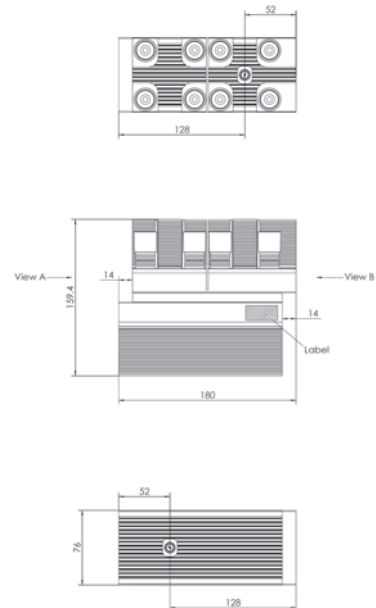
SEMiSTART 2 / 2a



SEMiSTART 3



SEMiSTART 3a




Dimensions in mm

Modules - Thyristor / Diode - SEMIPACK

Type	V_{RRM} V_{DRM}	I_{TAV} I_{FAV} @ T_C	T_C	I_{TSM} I_{FSM} @ T_{jmax}	$V_{T(TO)}$ @ T_{jmax}	r_T @ T_{jmax}	$R_{th(j-c)}$ cont. per chip	$R_{th(c-s)}$ per chip	T_j	Case	Circuit
	V	A	°C	A	V	mΩ	K/W	K/W	°C		
SKET 330	800-2200	295	85	8000	1.2	0.55	0.09	0.02	-40 ... +130	4	
SKET 400	800-1800	392	85	12000	0.92	0.3	0.09	0.02	-40 ... +130	4	
SKKE 15	600-1600	14	85	280	0.85	15	2	0.2	-40 ... +125	0	
SKKE 162	800-1800	195	85	5000	0.85	1.2	0.18	0.1	-40 ... +135	2	
SKKE 380	1200-1600	380	100	10000	0.8	0.35	0.11	0.04	-40 ... +150	3	
SKKE 600	1200-2200	600	100	18000	0.75	0.25	0.07	0.02	-40 ... +150	4	
SKKE 1200	1800-2200	1180	85	40000	0.72	0.19	0.0385	0.01	-40 ... +160	6	
SKET 740	1800-2200	699	85	31000	0.88	0.28	0.0405	0.01	-40 ... +125	6	
SKET 800	1400-1800	808	85	32000	0.83	0.25	0.0405	0.01	-40 ... +130	6	
SKKL 92	800-1800	95	85	1750	0.9	2	0.28	0.2	-40 ... +125	1	
SKMT 92	800-1800	95	85	1750	0.9	2	0.28	0.2	-40 ... +125	1	
SKKD 15	600-1600	14	85	280	0.85	15	2	0.2	-40 ... +125	0	
SKKD 26	1200-1600	31	85	480	0.85	6	1	0.2	-40 ... +125	1	
SKKD 46	400-1800	47	85	600	0.85	5	0.6	0.2	-40 ... +125	1	
SKKD 81	400-1800	82	85	1750	0.85	1.8	0.4	0.2	-40 ... +125	1	
SKKD 100	400-1800	100	85	2000	0.85	1.3	0.35	0.2	-40 ... +125	1	
SKKD 101/16 ¹⁾	1600	134	85	2000	0.87	2.45	0.19	0.22	-40 ... +130	1	
SKKD 162	800-2200	195	85	5000	0.85	1.2	0.18	0.1	-40 ... +135	2	
SKKD 212	1200-1800	212	85	5500	0.75	1.05	0.18	0.1	-40 ... +135	2	
SKKD 260	800-2200	260	85	10000	0.9	0.37	0.14	0.04	-40 ... +130	3	
SKKD 380	800-2200	380	100	10000	0.8	0.35	0.11	0.04	-40 ... +150	3	
SKKD 701	1200-2200	701	100	22500	0.7	0.28	0.069	0.02	-40 ... +160	5	
SKKD 82/22 H4 ⁵⁾	2200	-	-	-	-	-	-	-	-	1	
SKKH 15	600-1600	13.5	85	280	1.1	20	1.6	0.2	-40 ... +125	0	
SKKH 27	800-1800	25	85	480	0.9	12	0.9	0.2	-40 ... +125	1	
SKKH 42	800-1800	40	85	850	1	4.5	0.65	0.2	-40 ... +125	1	
SKKH 58/16 E ¹⁾	1600	55	85	1200	1	4.8	0.47	0.22	-40 ... +130	1	
SKKH 57	800-1800	50	85	1250	0.9	3.5	0.57	0.2	-40 ... +125	1	
SKKH 72	800-1800	70	85	1450	0.9	3.5	0.35	0.2	-40 ... +125	1	
SKKH 92	800-1800	95	85	1750	0.9	2	0.28	0.2	-40 ... +125	1	
SKKH 106	800-1800	106	85	1900	0.9	2	0.28	0.2	-40 ... +130	1	
SKKH 107/16 E ¹⁾	1600	119	85	1900	0.9	3.35	0.19	0.22	-40 ... +130	1	
SKKH 122	800-1800	129	85	3200	0.85	2	0.2	0.13	-40 ... +125	2	
SKKH 132 H4	2000-2200	128	85	3800	1.1	2	0.17	0.1	-40 ... +125	2	
SKKH 132	800-1800	137	85	4000	1	1.6	0.18	0.1	-40 ... +125	2	
SKKH 162 H4	2000-2200	143	85	4800	0.95	2	0.16	0.1	-40 ... +125	2	
SKKH 162	800-1800	156	85	5000	0.85	1.5	0.17	0.1	-40 ... +125	2	
SKKH 172	1600	175	85	5000	0.83	1.3	0.155	0.1	-40 ... +125	2	
SKKH 280 H4	2000-2200	252	85	7500	0.9	0.75	0.11	0.04	-40 ... +125	3	
SKKH 250	1200-1800	250	85	8000	0.925	0.45	0.14	0.04	-40 ... +130	3	
SKKH 273	1200-1800	273	85	8000	0.9	0.92	0.104	0.08	-40 ... +130	3	
SKKH 330	800-1800	305	85	8000	0.8	0.6	0.11	0.04	-40 ... +130	3	
SKKH 323	1200-1600	320	85	8200	0.81	0.85	0.091	0.08	-40 ... +130	3	
SKKH 460	1600	460	85	15500	0.88	0.45	0.072	0.02	-40 ... +130	5	
SKKH 460 H4	2200	460	85	15500	0.88	0.45	0.072	0.02	-40 ... +130	5	
SKKH 570	1600-1800	570	85	15500	0.78	0.32	0.069	0.02	-40 ... +135	5	
SKKH 73/22 H4	2200	-	-	-	-	-	-	-	-	1	

Modules - Thyristor / Diode - SEMIPACK

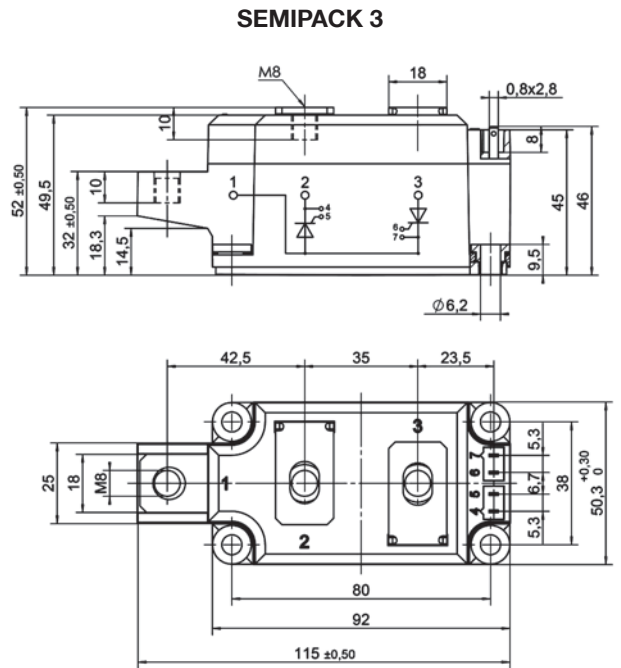
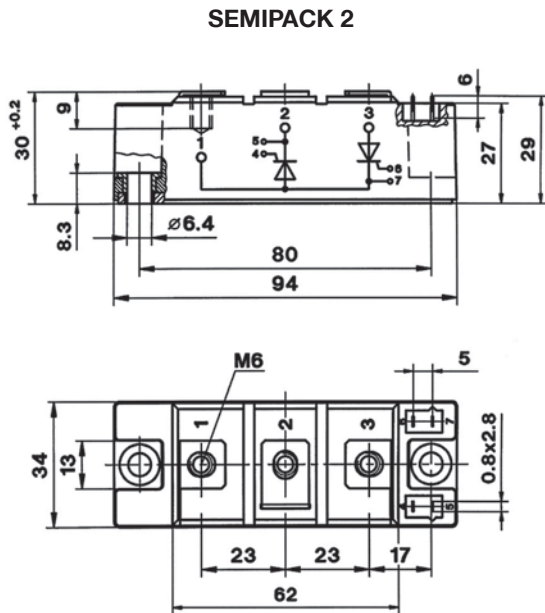
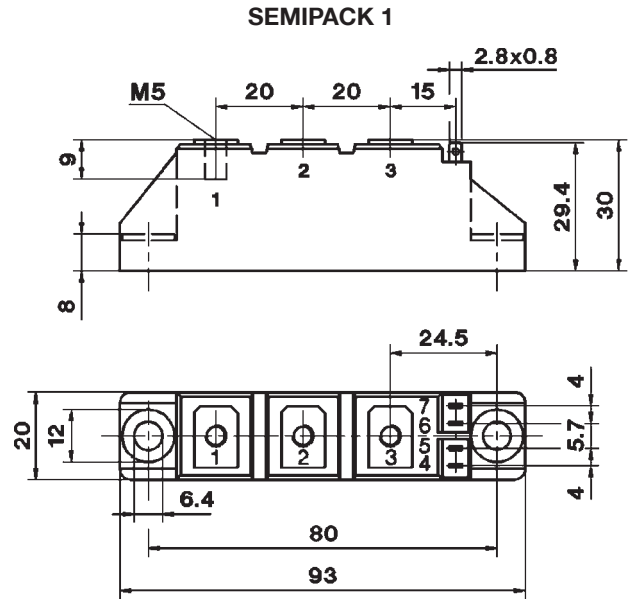
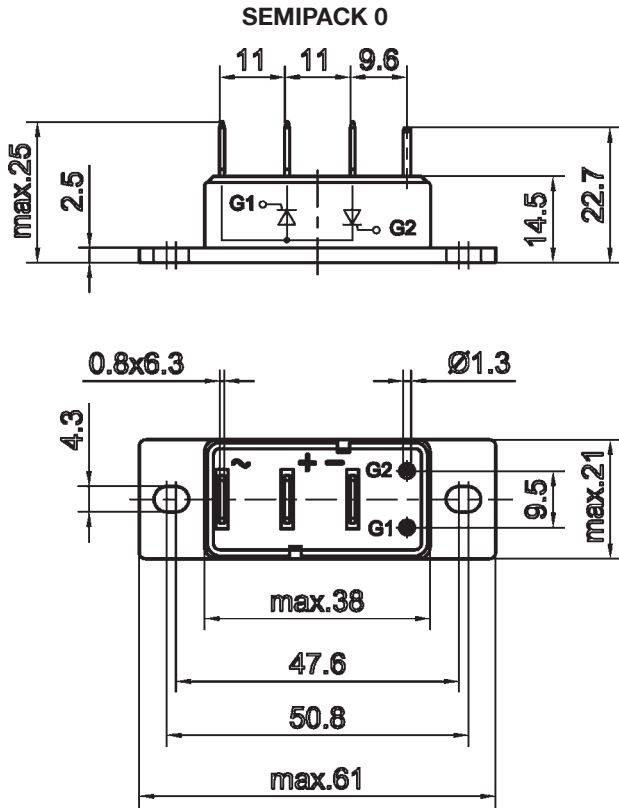
Type	V_{RRM} V_{DRM}	I_{TAV} I_{FAV} @ T_C	T_C	I_{TSM} I_{FSM} @ T_{jmax}	$V_{I(TO)}$ @ T_{jmax}	r_T @ T_{jmax}	$R_{th(j-c)}$ cont. per chip	$R_{th(c-s)}$ per chip	T_j	Case	Circuit
	V	A	°C	A	V	mΩ	K/W	K/W	°C		
SKKT 15	600-1600	13.5	85	280	1.1	20	1.6	0.2	-40 ... +125	0	
SKKT 20	800-1600	18	85	280	1	16	1.2	0.2	-40 ... +125	1	
SKKT 20B	800-1600	18	85	280	1	16	1.2	0.2	-40 ... +125	1	
SKKT 27	800-1600	25	85	480	0.9	12	0.9	0.2	-40 ... +125	1	
SKKT 27B	800-1600	25	85	480	0.9	12	0.9	0.2	-40 ... +125	1	
SKKT 42	800-1800	40	85	850	1	4.5	0.65	0.2	-40 ... +125	1	
SKKT 42B	800-1800	40	85	850	1	4.5	0.65	0.2	-40 ... +125	1	
SKKT 58/16 E ¹⁾	1600	55	85	1200	1	4.8	0.47	0.22	-40 ... +130	1	
SKKT 58B16 E ¹⁾	1600	55	85	1200	1	4.8	0.47	0.22	-40 ... +130	1	
SKKT 57	800-1800	50	85	1250	0.9	3.5	0.57	0.2	-40 ... +125	1	
SKKT 57 H4	2000-2200	50	85	1250	0.9	3.5	0.57	0.2	-40 ... +125	1	
SKKT 57B	800-1800	50	85	1250	0.9	3.5	0.57	0.2	-40 ... +125	1	
SKKT 72	800-1800	70	85	1450	0.9	3.5	0.35	0.2	-40 ... +125	1	
SKKT 72 H4	2000-2200	70	85	1450	0.9	3.5	0.35	0.2	-40 ... +125	1	
SKKT 72B	800-1800	70	85	1450	0.9	3.5	0.35	0.2	-40 ... +125	1	
SKKT 92	800-1800	95	85	1750	0.9	2	0.28	0.2	-40 ... +125	1	
SKKT 92B	800-1800	95	85	1750	0.9	2	0.28	0.2	-40 ... +125	1	
SKKT 106	800-1800	106	85	1900	0.9	2	0.28	0.2	-40 ... +130	1	
SKKT 106B	800-1800	106	85	1900	0.9	2	0.28	0.2	-40 ... +130	1	
SKKT 107/16 E ¹⁾	1600	119	85	1900	0.9	3.35	0.19	0.22	-40 ... +130	1	
SKKT 107B16 E ¹⁾	1600	119	85	1900	0.9	3.35	0.19	0.22	-40 ... +130	1	
SKKT 122	800-1800	129	85	3200	0.85	2	0.2	0.13	-40 ... +125	2	
SKKT 132 H4	2000-2200	128	85	3800	1.1	2	0.17	0.1	-40 ... +125	2	
SKKT 132	800-1800	137	85	4000	1	1.6	0.18	0.1	-40 ... +125	2	
SKKT 162 H4	2000-2200	143	85	4800	0.95	2	0.16	0.1	-40 ... +125	2	
SKKT 162	800-1800	156	85	5000	0.85	1.5	0.17	0.1	-40 ... +125	2	
SKKT 172	1400-1800	175	85	5000	0.83	1.3	0.155	0.1	-40 ... +125	2	
SKKT 280 H4	2000-2200	252	85	7500	0.9	0.75	0.11	0.04	-40 ... +125	3	
SKKT 250	800-1800	250	85	8000	0.925	0.45	0.14	0.04	-40 ... +130	3	
SKKT 273	1200-1800	273	85	8000	0.9	0.92	0.104	0.08	-40 ... +130	3	
SKKT 330	800-1800	305	85	8000	0.8	0.6	0.11	0.04	-40 ... +130	3	
SKKT 323	1200-1600	320	85	8200	0.81	0.85	0.091	0.08	-40 ... +130	3	
SKKT 460	1600	460	85	15500	0.88	0.45	0.072	0.02	-40 ... +130	5	
SKKT 460 H4	2200	460	85	15500	0.88	0.45	0.072	0.02	-40 ... +130	5	
SKKT 570	1200-1800	570	85	15500	0.78	0.32	0.069	0.02	-40 ... +135	5	

Footnotes

- ¹⁾ New
⁵⁾ UNDER DEVELOPMENT

Modules - Thyristor / Diode - SEMIPACK

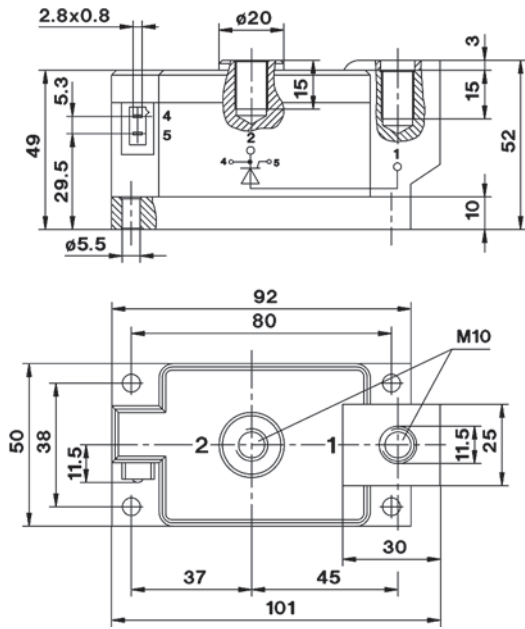
Cases



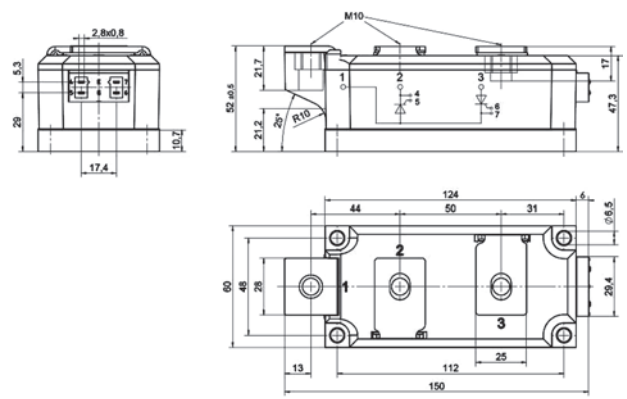
Dimensions in mm

Cases

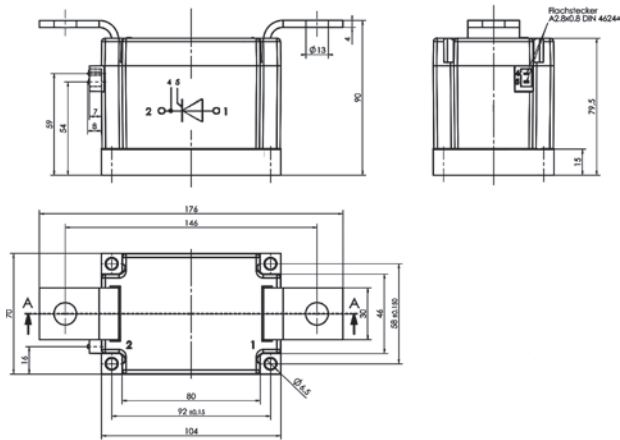
SEMIPACK 4



SEMIPACK 5



SEMIPACK 6



Dimensions in mm

Modules - Thyristor / Diode - SEMIPACK Fast

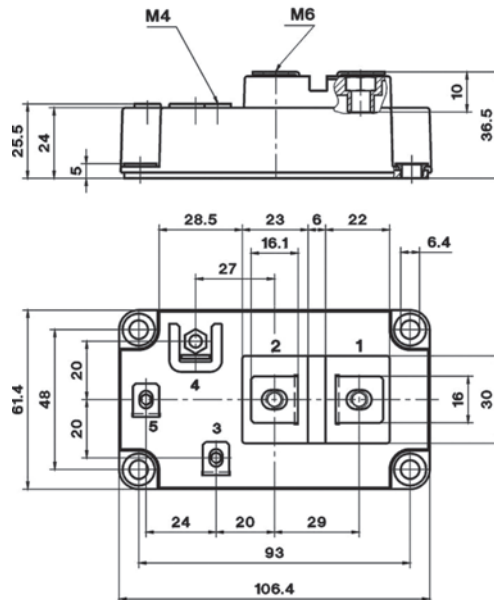
Type	V_{RRM} V_{DRM}	I_{TAV} I_{FAV} @ T_C	T_C	I_{FSM} @ T_{jmax}	$V_{I(TO)}$ @ T_{jmax}	r_T @ T_{jmax}	$R_{th(j-c)}$ per chip	$R_{th(c-s)}$ per chip	T_j	Case	Circuit
	V	A	°C	A	V	mΩ	K/W	K/W	°C		
SKKE 120F	1700	120	82	1800	1.5	4.5	0.2	0.05	-40 ... +150	2	
SKKE 290F	600	290	109	6000	0.9	1.2	0.08	0.05	-40 ... +150	2	
SKKE 301F	1200	300	43	3600	1.2	2.75	0.11	0.05	-40 ... +150	2	
SKKE 310F	1200	310	84	5500	1.2	1.9	0.08	0.05	-40 ... +150	2	
SKKE 330F ⁵⁾	1700	330	70	5200	1.5	1.9	0.079	0.038	-40 ... +150	4	
SKKE 600F ⁵⁾	1200	600	85	5800	1.2	1.9	0.062	0.038	-40 ... +150	4	
SKKD 60F	1700	60	83	900	1.5	9	0.4	0.1	-40 ... +150	2	
SKKD 75F12	1200	75	55	900	1.2	11	0.4	0.1	-40 ... +150	2	
SKKD 150F	1200	150	54	1800	1.2	5.5	0.2	0.1	-40 ... +150	2	
SKKD 170F	1200	170	85	2300	1.2	3.5	0.14	0.1	-40 ... +150	2	
SKKD 205F	600	205	87	3000	0.9	2	0.16	0.1	-40 ... +150	2	
SKKD 116F ⁶⁾	-	-	-	-	-	-	-	-	-	1	
SKMD 150F12	1200	150	54	1800	1.2	5.5	0.2	0.1	-40 ... +150	2	
SKMD 202E	200-300	202	87	2800	0.8	1.5	0.2	0.1	-40 ... +150	2	
SKND 150F	1200	150	54	1800	1.2	5.5	0.2	0.1	-40 ... +150	2	
SKND 202E	200-300	202	87	2800	0.8	1.5	0.2	0.1	-40 ... +150	2	
SKND 205F	600	205	87	3000	0.9	2	0.16	0.1	-40 ... +150	2	

Footnotes

- ⁵⁾ SEMIPACK Fast in SEMITRANS 4 case
- ⁶⁾ UNDER DEVELOPMENT






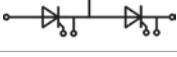
Cases

SEMIPACK Fast in SEMITRANS 4



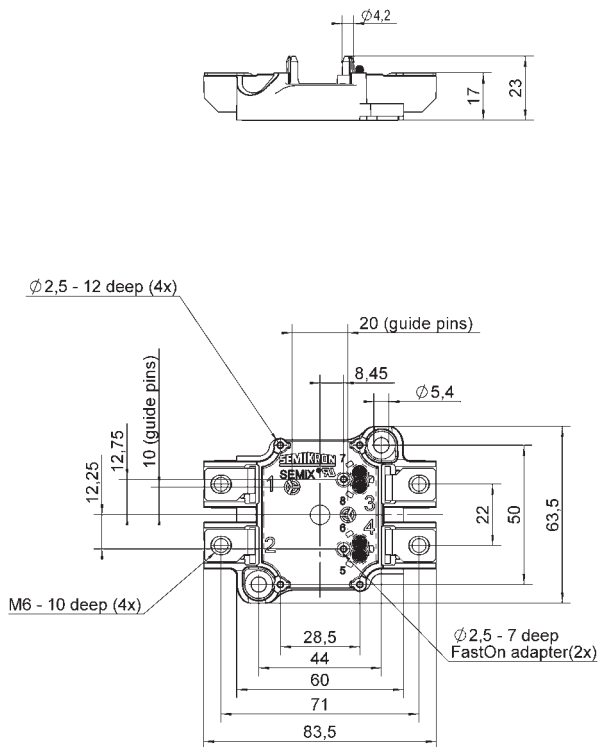
Dimensions in mm

Modules - Thyristor / Diode - SEMiX

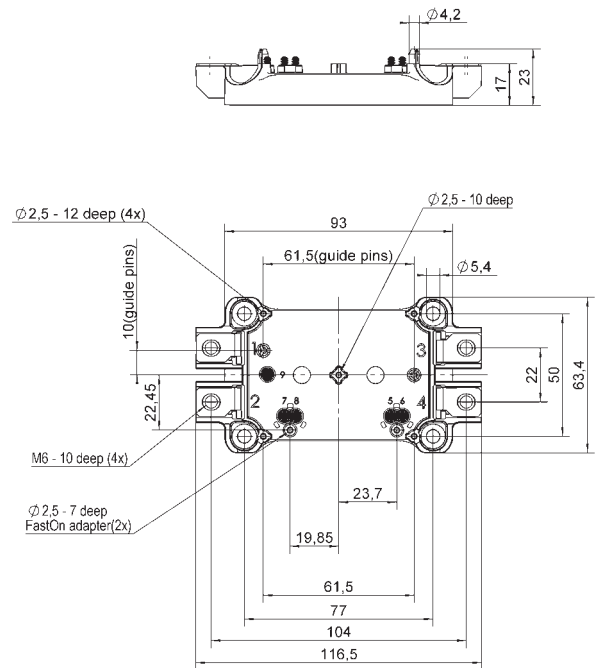
Type	V_{RRM} V_{DRM}	I_{TAV} I_{FAV} @ T_C	T_C	I_{TSM} I_{FSM} @ T_{jmax}	$V_{I(TO)}$ @ T_{jmax}	r_T @ T_{jmax}	$R_{th(j-c)}$ per chip	$R_{th(c-s)}$ per module	T_j	Case	Circuit
	V	A	°C	A	V	mΩ	K/W	K/W	°C		
SEMiX191KD16s	1600	190	85	5000	0.85	0.95	0.18	0.075	-40 ... +130	1s	
SEMiX302KD16s	1600	300	85	7500	0.85	1.1	0.091	0.045	-40 ... +130	2s	
SEMiX171KH16s	1600	170	85	4800	0.85	1.5	0.18	0.075	-40 ... +130	1s	
SEMiX302KH16s	1600	300	85	8000	0.85	1.1	0.091	0.045	-40 ... +130	2s	
SEMiX141KT16s	1600	140	85	3000	0.85	2.1	0.21	0.075	-40 ... +130	1s	
SEMiX302KT16s	1600	300	85	8000	0.85	1.7	0.091	0.045	-40 ... +130	2s	

Cases

SEMiX 1s



SEMiX 2s



Dimensions in mm

Modules - Thyristor / Diode - SEMITOP

Type	V_{RRM} V_{DRM}	I_{TAV} I_{FAV} @ T_C	T_C	I_{TSM} I_{FSM} @ T_{jmax}	$V_{T(TO)}$ @ T_{jmax}	r_T @ T_{jmax}	$R_{th(j-s)}$ cont. per chip	T_j	Case	Circuit
	V	A	°C	A	V	mΩ	K/W	°C		
SK 25 KQ	800-1600	29	85	280	1.1	20	1.7	-40 ... +125	1	
SK 45 KQ	800-1600	47	85	380	1	10	1.2	-40 ... +125	1	
SK 70 KQ	800-1600	72	85	900	1	6	0.8	-40 ... +125	1	
SK 100 KQ	800-1600	101	85	1350	0.9	4.5	0.6	-40 ... +125	2	
SK 120 KQ	800-1600	134	85	1800	0.9	3.5	0.45	-40 ... +125	2	
SK 35 TAA	800-1600	35	80	380	0.85	9.1	1.2	-40 ... +130	2	
SK 55 TAA	800-1600	55	80	900	0.85	5.7	0.8	-40 ... +130	2	
SK 75 TAA	800-1600	75	80	1500	0.9	4.5	0.6	-40 ... +130	2	
SK 100 TAA	800-1600	100	80	2000	0.9	3.5	0.45	-40 ... +130	2	
SK 75 TAE 12	1200	75	80	1250	0.85	4.4	0.6	-40 ... +130	2	
SK 25 WT	800-1600	29	85	280	1.1	20	1.7	-40 ... +125	2	
SK 45 WT	800-1600	47	85	380	1	10	1.2	-40 ... +125	2	
SK 70 WT	800-1600	72	85	900	1	6	0.8	-40 ... +125	3	
SK 100 WT	800-1600	101	85	1350	0.9	4.5	0.6	-40 ... +125	3	
SK 35 BZ	800-1600	35	80	270	0.85	14	1.7	-40 ... +125	2	
SK 45 STA	800-1600	47	75	380	1	10	1.2	-40 ... +125	3	
SK 25 UT	800-1600	29	85	280	1.1	20	1.7	-40 ... +125	3	
SK 45 UT	800-1600	47	85	380	1	10	1.2	-40 ... +125	2	
SK 30 DTA	800-1600	25	80	900	1	6	1.7	-40 ... +150	3	
SK 60 DTA	800-1600	61	80	1350	0.9	0.6	0.6	-40 ... +125	3	
SK 80 DTA	800-1600	65	80	1800	0.9	3.5	1	-40 ... +150	3	

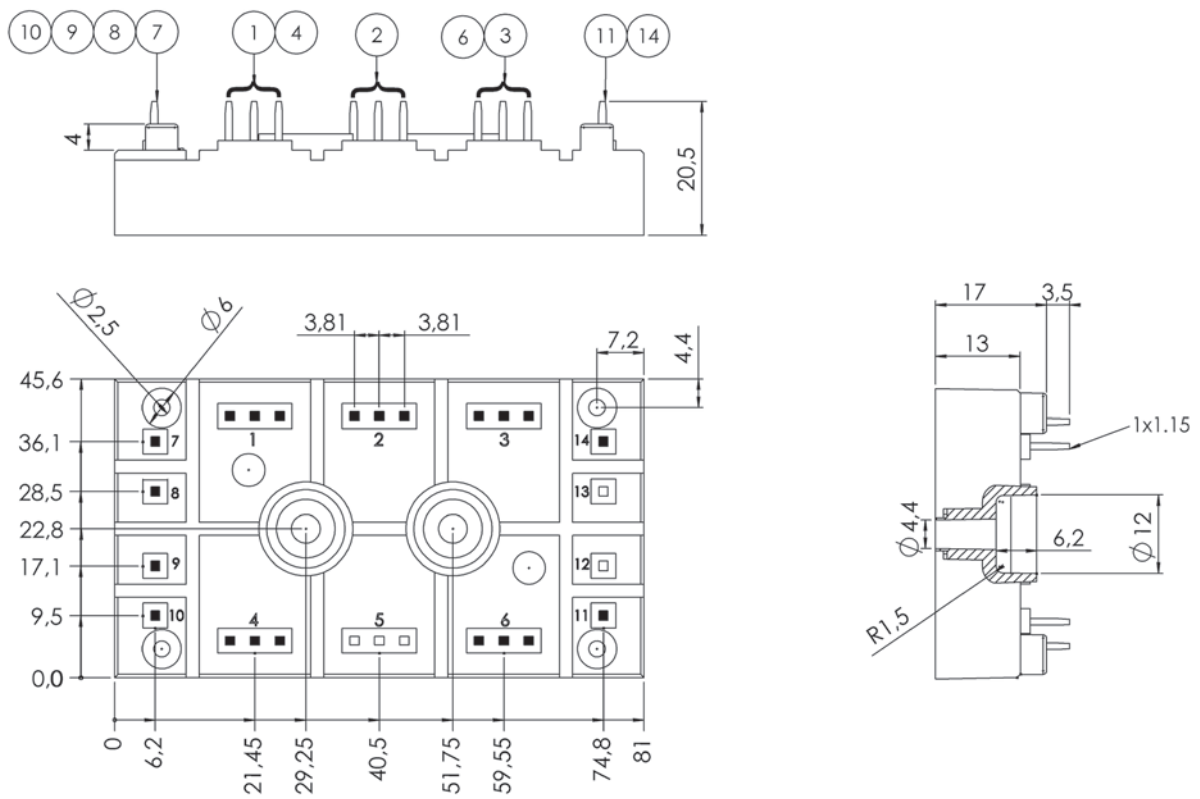
For detailed case drawings please see page 26

Modules - Thyristor / Diode - SEMIPONT

Type	V_{RRM} V_{DRM}	I_{RMS} @ T_C	T_C	I_{TSM} @ T_{jmax}	I_{FSM} @ T_{jmax}	$V_{T(TO)}$ @ T_{jmax}	r_T @ T_{jmax}	$R_{th(j-s)}$ cont. per chip	T_j	Case	Circuit
	V	A	°C	A	A	V	mΩ	K/W	°C		
SKUT 85 T	1200-1600	85	85	1050	1.1	6	0.85	-40 ... +125	5		
SKUT 115 T	1200-1600	105	85	1250	0.9	5	0.63	-40 ... +125	5		
SKUT 85	1200-1600	85	85	1050	1.1	6	0.85	-40 ... +125	5		
SKUT 115	1200-1600	105	85	1250	0.9	5	0.63	-40 ... +125	5		

Cases

SEMIPONT 5

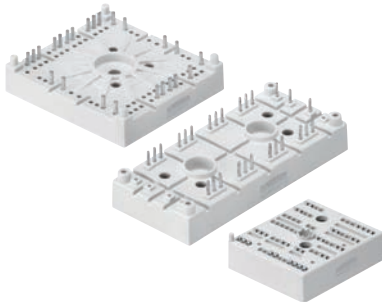


Dimensions in mm

Bridge Rectifier

SEMITOP® / SEMIPONT® / MiniSKiiP®

rectifier with
brake chopper



600V
up to
1600V

I_D / I_C in A

0 10 20 30 40 50 75 100 200 300 400 500



SEMITOP® / SEMIPONT® / SEMiX®

three phase



400V
up to
1800V

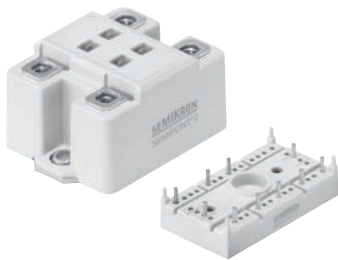
I_D in A

0 10 20 30 40 50 75 100 200 300 400 500



SEMIPONT® / SEMITOP®

single phase



400V
up to
1800V

I_D in A

0 10 20 30 40 50 75 100 200 300 400 500



Modules - Bridge - SEMiX

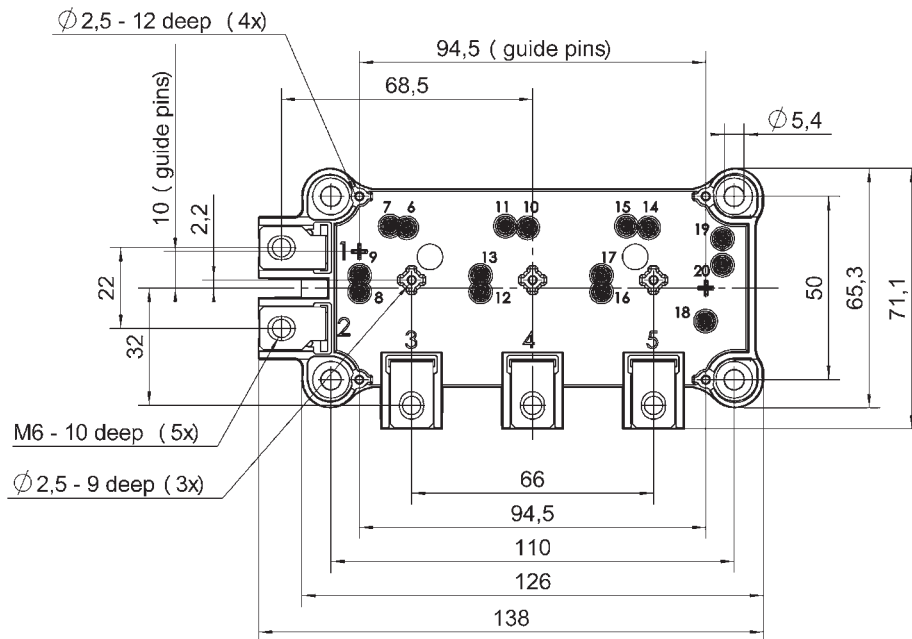
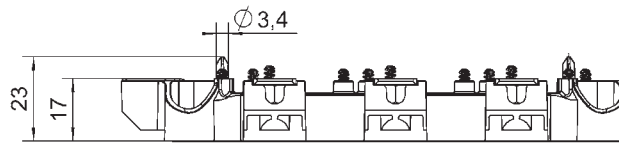
Type	V_{RRM} V_{DRM}	I_D @ T_C	T_C	I_{TSM} @ T_{jmax}	I_{FSM} @ T_{jmax}	$V_{I(TO)}$ @ T_{jmax}	r_T @ T_{jmax}	$R_{th(j-c)}$ per chip	$R_{th(c-s)}$ per module	T_j	Case	Circuit
	V	A	°C	A	A	V	mΩ	K/W	K/W	°C		
SEMIX251D12Fs	1200	250	85	1330	1.2	7	0.26	0.04	0.04	-40 ... +150	13	
SEMIX291D16s ¹⁾	1600	290	85	1380	0.83	4.6	0.45	0.04	-40 ... +150	13		
SEMIX341D16s	1600	340	85	2000	0.9	2.7	0.22	0.04	-40 ... +130	13		
SEMIX501D17Fs ¹⁾	1700	489	85	2140	1.1	2.7	0.165	0.04	-40 ... +150	13		
SEMIX241DH16s	1600	240	85	1900	0.85	4	0.32	0.04	-40 ... +130	13		

Footnotes

¹⁾ New

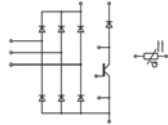
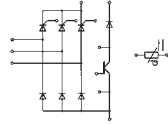
Cases

SEMIX 13



Dimensions in mm

Modules - Bridge - MiniSKiiP

Type	IGBT						Diode				Rectifier		Case	Circuit
	I_C @ $T_S=25^\circ\text{C}$	I_{Cnom}	$V_{CE(sat)}$ @ $T_J=25^\circ\text{C}$ typ.	E_{on}	E_{off}	$R_{th(j-s)}$	I_F @ $T_S=25^\circ\text{C}$	V_F @ $T_J=25^\circ\text{C}$ typ.	E_{rr}	$R_{th(j-s)}$	I_{FSM} @ $T_S=25^\circ\text{C}$	$R_{th(j-s)}$		
	A	A	V	mJ	mJ	K/W	A	V	mJ	K/W	A	K/W		
1200 V - IGBT 3 (Trench)														
SKiiP 28ANB16V1	118	105	1.7	13.1	13	0.4	118	1.60	11.2	0.55	1000	0.7	II 2	
SKiiP 39ANB16V1	157	140	1.7	19.9	17.2	0.3	167	1.50	16.2	0.4	1600	0.5	II 3	
SKiiP 28AHB16V1	118	105	1.7	14.4	13.3	0.4	118	1.60	10.8	0.55	1000	0.7	II 2	
SKiiP 39AHB16V1	157	140	1.7	19.9	17.3	0.3	167	1.50	16.2	0.4	1250	0.5	II 3	

For detailed case drawings please see page 21

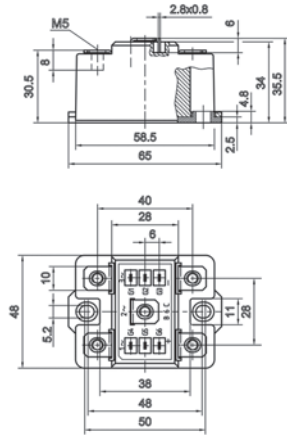
Modules - Bridge - SEMIPONT

Type	V_{RRM} V_{DRM}	I_D @ T_C	T_C	I_{TSM} @ T_{jmax}	I_{FSM} @ T_{jmax}	$V_{T(TO)}$ @ T_{jmax}	r_T @ T_{jmax}	$R_{th(j-c)}$ cont. per chip	T_j	Case	Circuit
	V	A	°C	A	A	V	mΩ	K/W	°C		
1 and 3 phase											
SKB 52	400-1800	50	99	425	0.85	8	1.5	1.5	-40 ... +150	3	
SKB 60	400-1600	60	88	850	0.85	5	1	1	-40 ... +125	2	
SKB 72	400-1800	70	101	640	0.85	5	1.1	1.1	-40 ... +150	3	
SKBT 40	800-1400	46	92	400	1	16	1	1	-40 ... +125	2	
SKCH 40	400-1600	40	92	400	1	16	1	1	-40 ... +125	2	
SKDT 60	400-1400	60	86	400	1	16	1	1	-40 ... +125	2	
SKDT 115	1200-1600	110	80	950	1.1	6	0.84	0.84	-40 ... +125	5	
SKDT 145	1200-1600	140	80	1250	0.9	5	0.6	0.6	-40 ... +125	5	
SKD 60	400-1600	60	102	850	0.85	5	1	1	-40 ... +125	2	
SKD 62	400-1800	60	110	425	0.85	8	1.5	1.5	-40 ... +150	3	
SKD 82	400-1800	80	110	640	0.85	5	1.1	1.1	-40 ... +150	3	
SKD 100	400-1600	100	93	1000	0.85	5	0.85	0.85	-40 ... +125	2	
SKD 110	800-1800	110	100	1000	0.85	4	0.9	0.9	-40 ... +150	4	
SKD 115	1200-1800	110	85	1150	0.8	7	1	1	-40 ... +150	5	
SKD 145	1200-1800	140	85	1700	0.8	4	0.8	0.8	-40 ... +150	5	
SKD 160	800-1800	205	100	1500	0.85	3	0.65	0.65	-40 ... +150	4	
SKD 210	900-1800	207	99	1600	0.85	3	0.5	0.5	-40 ... +150	4	
SKDH 100	800-1400	100	84	850	1	4.5	0.85	0.85	-40 ... +125	2	
SKDH 115	1200-1600	110	80	950	1.1	6	0.84	0.84	-40 ... +125	5	
SKDH 145	1200-1600	110	80	1250	0.9	5	0.63	0.63	-40 ... +125	5	
3 phase with brake chopper											
SKD 116/...-L105	1200-1600	110	85	1050	0.8	7	1	1	-40 ... +125	6	
SKD 116/...-L140	1200-1600	110	85	1050	0.8	7	1	1	-40 ... +125	6	
SKD 146/...-L105	1200-1600	140	85	1250	0.8	4	0.8	0.8	-40 ... +125	6	
SKD146/...-L140T4	1200-1600	140	85	1250	0.8	4	0.8	0.8	-40 ... +125	6	
SKDH116/...L105	1200-1600	110	85	1050	0.8	7	1	1	-40 ... +125	6	
SKDH116/...L140	1200-1600	110	85	1050	0.8	7	1	1	-40 ... +125	6	
SKDH146/...-L105	1200-1600	110	85	1250	0.8	4	0.8	0.8	-40 ... +125	6	
SKDH146/...-L140	1200-1600	110	85	1250	0.8	4	0.8	0.8	-40 ... +125	6	
SKDH 146/08-L200	800	140	80	1250	0.85	3	0.6	0.6	-40 ... +125	6	

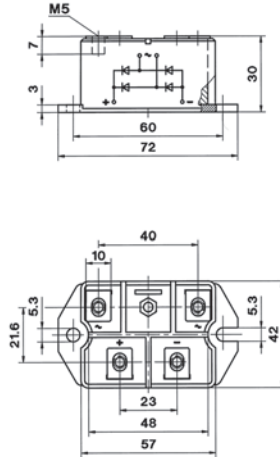
Modules - Bridge - SEMIPONT

Cases

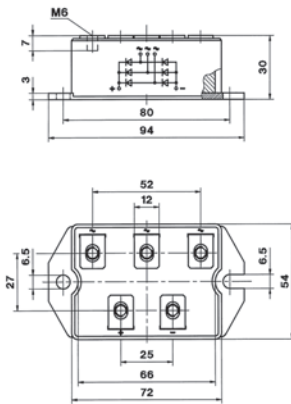
SEMIPONT 2



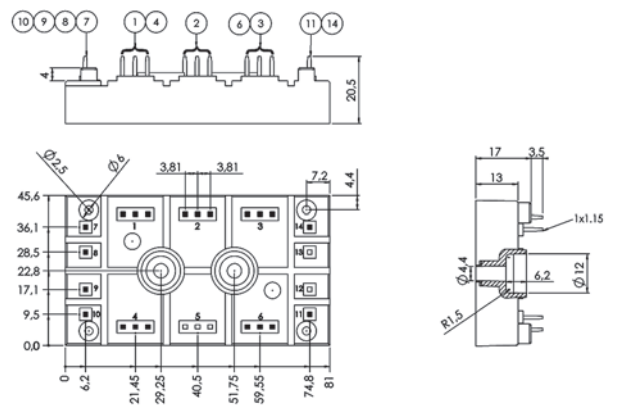
SEMIPONT 3



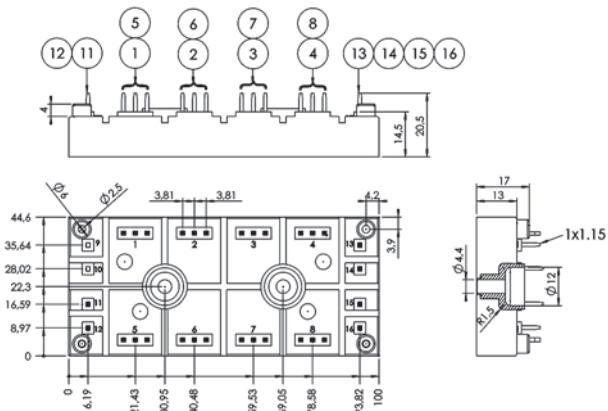
SEMIPONT 4



SEMIPONT 5



SEMIPONT 6



Dimensions in mm

Modules - Bridge - SEMITOP

Type	V_{RRM} V_{DRM}	I_D @ T_S	T_S	I_{TSM} @ T_{jmax}	I_{FSM} @ T_{jmax}	$V_{T(TO)}$ @ T_{jmax}	r_T @ T_{jmax}	$R_{th(j-s)}$ per chip	T_j	Case	Circuit
	V	A	°C	A	A	V	mΩ	K/W	°C		
1 and 3 phase											
SK 50 B 06 UF	600	46	80	400	0.8	11	0.45	-40 ... +150	2		
SK 50 B	800-1600	51	80	270	0.8	13	1.7	-40 ... +150	2		
SK 55 B 06 F	600	54	80	440	0.9	16	1.2	-40 ... +150	2		
SK 55 B 12 F	1200	57	80	550	1.2	22	0.9	-40 ... +150	2		
SK 70 B	800-1600	68	80	560	0.8	11	1.2	-40 ... +150	2		
SK 100 B	800-1600	100	80	890	0.83	3.9	1	-40 ... +150	2		
SK 40 DT	800-1600	42	80	280	1.1	20	1.7	-40 ... +125	3		
SK 70 DT	800-1600	68	80	380	1	10	1.2	-40 ... +125	3		
SK 55 D	800-1600	55	80	200	0.8	13	2.15	-40 ... +150	2		
SK 70 D	800-1600	70	80	270	0.8	13	1.7	-40 ... +150	2		
SK 80 D 12F	1200	80	80	550	1.2	22	0.9	-40 ... +150	3		
SK 95 D	800-1600	95	80	560	0.8	11	1.2	-40 ... +150	2		
SK 40 DH	800-1600	42	80	270	1.1	20	1.7	-40 ... +150	3		
SK 70 DH	800-1600	68	80	270	1	10	1.2	-40 ... +125	3		
SK 55 DGL 126	1200	55	80	370	0.8	13	2	-40 ... +150	3		
SK 95 DGL 126	1600	96	80	700	0.8	11	1.2	-40 ... +150	3		
SK 170 DHL 126	1200	170	70	1000	0.8	7	0.51	-40 ... +150	4		
SK 200 DHL 066	600	210	70	1250	0.8	4	0.52	-40 ... +150	4		

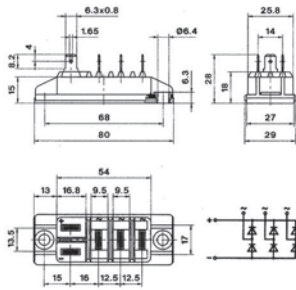
For detailed case drawings please see page 26

Modules - Bridge - Power Bridge

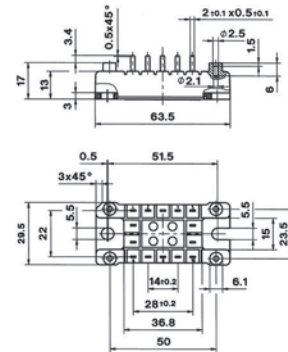
Type	V_{RRM} V_{DRM}	I_D @ T_C	T_C	I_{FSM} @ T_{jmax}	$V_{T(TO)}$ @ T_{jmax}	r_T @ T_{jmax}	$R_{th(j-s)}$ cont. per chip	T_j	Case	Circuit
	V	A	°C	A	V	mΩ	K/W	°C		
3 phase										
SKD 33	400-1800	33	110	240	0.8	18	2.5	-40 ... +150	G55	
SKD 51	400-1800	50	127	700	0.8	8.5	1.1	-40 ... +150	G51	
SKD 53	400-1800	53	100	270	0.8	13	1.9	-40 ... +150	G55	
SKD 83	400-1800	83	95	560	0.8	7.5	1.4	-40 ... +150	G55	

Cases

G 51



G 55

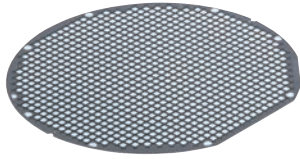


Dimensions in mm

Discretes

Chips SEMICELL

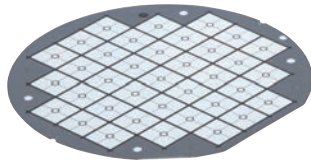
Freewheeling Diode CAL / Rectifier



600V
up to
1700V



Thyristor



1600V



$I_{T/F}$ in A

0 10 20 30 40 50 100 200 400 600 800 1000 2000 3000 4000 5000 6000

Capsule

Diode



200V
up to
600V



I_{FAV} in A

0 10 20 30 40 50 100 200 400 600 800 1000 2000 3000 4000 5000 6000

Thyristor



1200V
up to
1800V



I_{TAV} in A

0 10 20 30 40 50 100 200 400 600 800 1000 2000 3000 4000 5000 6000

Discretos - Chips - SEMICELL

Type	V_{RRM}	I_F @ $T_j = 150^\circ\text{C}$	I_{FSM} @ $T_j = 150^\circ\text{C}$ 10ms	V_F @ $T_j = 25^\circ\text{C}$	$I_F @ V_F$ $T_j = 25^\circ\text{C}$	Q_{rr} @ $T_j = 125^\circ\text{C}$
	V	A	A	V	A	μC
600 V - Freewheeling Diodes CAL I3 Fast						
SKCD 06 C 060 I3	600	15	-	1.35	10	0.7
SKCD 09 C 060 I3	600	20	100	1.35	15	1.2
SKCD 18 C 060 I3	600	30	200	1.35	25	2.5
SKCD 31 C 060 I3	600	50	440	1.35	50	3.3
SKCD 47 C 060 I3	600	80	720	1.35	85	5.5
SKCD 61 C 060 I3	600	100	1000	1.35	110	7
SKCD 81 C 060 I3	600	150	1260	1.35	155	8.5
SKCD 121 C 060 I3	600	210	2100	1.35	245	10.7

Type	V_{RRM}	I_F @ $T_j = 175^\circ\text{C}$	I_{FSM} @ $T_j = 150^\circ\text{C}$ 10ms	V_F @ $T_j = 25^\circ\text{C}$	$I_F @ V_F$ $T_j = 25^\circ\text{C}$	Q_{rr} @ $T_j = 150^\circ\text{C}$
	V	A	A	V	A	μC
600 V - Freewheeling Diodes CAL High Density						
SKCD 04 C 060 I HD	600	10	65	1.35	7	0.89
SKCD 06 C 060 I HD	600	20	95	1.35	12	0.93
SKCD 09 C 060 I HD	600	30	160	1.35	19	1.6
SKCD 16 C 060 I HD	600	50	320	1.35	37	5.64
SKCD 24 C 060 I HD	600	75	395	1.35	60	7.8
SKCD 42 C 060 I HD	600	100	810	1.35	110	14
SKCD 61 C 060 I HD	600	150	1080	1.35	160	22
SKCD 81 C 060 I HD	600	200	1310	1.35	230	32

Type	V_{RRM}	I_F @ $T_j = 175^\circ\text{C}$	I_{FSM} @ $T_j = 150^\circ\text{C}$ 10ms	V_F @ $T_j = 25^\circ\text{C}$	$I_F @ V_F$ $T_j = 25^\circ\text{C}$	E_{off} @ $T_j = 150^\circ\text{C}$
	V	A	A	V	A	mJ
650 V - Freewheeling Diodes CAL I4 Fast						
SKCD 24 C 065 I4F	650	50	460	1.30	39	1.1
SKCD 42 C 065 I4F	650	100	680	1.30	73	2.2
SKCD 61 C 065 I4F	650	150	1100	1.30	109	3.8
SKCD 81 C 065 I4F	650	200	1290	1.30	148	5.8

Discretes - Chips - SEMICELL

Type	V_{RRM}	I_F @ $T_j = 150^\circ\text{C}$	I_{FSM} @ $T_j = 150^\circ\text{C}$ 10ms	V_F @ $T_j = 25^\circ\text{C}$	$I_F @ V_F$ $T_j = 25^\circ\text{C}$	Q_{rr} @ $T_j = 125^\circ\text{C}$
	V	A	A	V	A	μC
1200 V - Freewheeling Diodes CAL I3 Fast						
SKCD 11 C 120 I3	1200	15	130	2.00	10	1.6
SKCD 18 C 120 I3	1200	25	200	2.00	15	3
SKCD 23 C 120 I3R	1200	30	270	2.00	25	3.8
SKCD 31 C 120 I3	1200	40	370	2.00	35	5.3
SKCD 47 C 120 I3	1200	55	600	2.00	55	7.5
SKCD 61 C 120 I3	1200	75	800	2.00	70	11
SKCD 81 C 120 I3	1200	100	1100	2.00	100	16.5
SKCD 121 C 120 I3	1200	150	1600	2.00	155	24

Type	V_{RRM}	I_F @ $T_j = 150^\circ\text{C}$	I_{FSM} @ $T_j = 150^\circ\text{C}$ 10ms	V_F @ $T_j = 25^\circ\text{C}$	$I_F @ V_F$ $T_j = 25^\circ\text{C}$	Q_{rr} @ $T_j = 125^\circ\text{C}$
	V	A	A	V	A	μC
1200 V - Freewheeling Diodes CAL High Density						
SKCD 06 C 120 I HD	1200	6	60	1.50	5	1.24
SKCD 11 C 120 I HD	1200	15	140	1.50	12	2.9
SKCD 14 C 120 I HD	1200	20	170	1.50	15	4
SKCD 18 C 120 I HD	1200	25	200	1.50	20	5
SKCD 31 C 120 I HD	1200	55	480	1.50	45	11
SKCD 47 C 120 I HD	1200	85	700	1.50	70	17.4
SKCD 61 C 120 I HD	1200	115	900	1.50	90	24.5
SKCD 81 C 120 I HD	1200	160	1150	1.50	130	34.4

Type	V_{RRM}	I_F @ $T_j = 175^\circ\text{C}$	I_{FSM} @ $T_j = 150^\circ\text{C}$ 10ms	V_F @ $T_j = 25^\circ\text{C}$	$I_F @ V_F$ $T_j = 25^\circ\text{C}$	E_{off} @ $T_j = 150^\circ\text{C}$
	V	A	A	V	A	mJ
1200 V - Freewheeling Diodes CAL I4 Fast						
SKCD 08 C 120 I4F	1200	8	36	2.33	8	0.4
SKCD 11 C 120 I4F	1200	15	65	2.38	15	0.6
SKCD 16 C 120 I4F	1200	25	100	2.41	25	1
SKCD 22 C 120 I4F	1200	35	170	2.30	35	1.6
SKCD 31 C 120 I4F	1200	50	270	2.22	50	2.6
SKCD 46 C 120 I4F	1200	75	430	2.17	75	4.2
SKCD 46 C 120 I4F R	1200	75	430	2.17	75	4.2
SKCD 53 C 120 I4F	1200	100	550	2.20	100	5.4
SKCD 81 C 120 I4F	1200	150	900	2.14	150	8.7

Type	V_{RRM}	I_F @ $T_j = 175^\circ\text{C}$	I_{FSM} @ $T_j = 150^\circ\text{C}$ 10ms	V_F @ $T_j = 25^\circ\text{C}$	$I_F @ V_F$ $T_j = 25^\circ\text{C}$	E_{off} @ $T_j = 150^\circ\text{C}$
	V	A	A	V	A	mJ
1200 V - Freewheeling Diodes CAL I4 High Density						
SKCD 46 C 120 I4 HD	1200	75	430	1.72	75	6.2
SKCD 53 C 120 I4 HD	1200	100	550	1.77	100	8
SKCD 81 C 120 I4 HD	1200	150	900	1.72	150	13.4

Discretes - Chips - SEMICELL

Type	V_{RRM}	I_F @ $T_j = 150^\circ\text{C}$	I_{FSM} @ $T_j = 150^\circ\text{C}$ 10ms	V_F @ $T_j = 25^\circ\text{C}$	$I_F @ V_F$ $T_j = 25^\circ\text{C}$	Q_{rr} @ $T_j = 125^\circ\text{C}$
	V	A	A	V	A	μC
1700 V - Freewheeling Diodes CAL Fast						
SKCD 47 C 170 I	1700	55	550	2.05	55	15
SKCD 61 C 170 I	1700	75	720	2.05	75	19

Type	V_{RRM}	I_F @ $T_j = 150^\circ\text{C}$	I_{FSM} @ $T_j = 150^\circ\text{C}$ 10ms	V_F @ $T_j = 25^\circ\text{C}$	$I_F @ V_F$ $T_j = 25^\circ\text{C}$	Q_{rr} @ $T_j = 125^\circ\text{C}$
	V	A	A	V	A	μC
1700 V - Freewheeling Diodes CAL High Density						
SKCD 47 C 170 I HD	1700	75	650	1.73	75	19
SKCD 61 C 170 I HD	1700	100	710	1.73	100	26
SKCD 81 C 170 I HD	1700	150	1070	1.73	150	44

Type	V_{RRM}	I_F @ $T_j = 175^\circ\text{C}$	I_{FSM} @ $T_j = 150^\circ\text{C}$ 10ms	V_F @ $T_j = 25^\circ\text{C}$	$I_F @ V_F$ $T_j = 25^\circ\text{C}$	E_{off} @ $T_j = 150^\circ\text{C}$
	V	A	A	V	A	mJ
1700 V - Freewheeling Diodes CAL I4 Fast						
SKCD 28 C 170 I4F ¹⁾	1700	40	280	1.71	23	12
SKCD 46 C 170 I4F ¹⁾	1700	75	450	1.71	43	17
SKCD 56 C 170 I4F ¹⁾	1700	100	580	1.71	57	22.2
SKCD 81 C 170 I4F ¹⁾	1700	150	860	1.71	89	31.5

Discretes - Chips - SEMICELL


Type	V_{RRM}	$I_{F(DC)}$ @ $T_j = 150^\circ\text{C}$	I_{FSM} @ $T_j = 150^\circ\text{C}$ 10ms	V_F @ $T_j = 25^\circ\text{C}$	$I_F @ V_F$ $T_j = 25^\circ\text{C}$	t_{rr} @ $T_j = 25^\circ\text{C}$
	V	A	A	V	A	μs
1600 V - Rectifier						
SKR 3,5 Qu bond ⁵⁾	1600	25	200	1	8	20
SKR 4,2 Qu bond ⁵⁾	1600	35	270	1	13	20
SKR 4,8 Qu bond ⁵⁾	1600	45	350	1	18	21
SKR 5,6 Qu bond ⁵⁾	1600	50	490	1	25	22
SKR 6,2 Qu bond ⁵⁾	1600	65	600	1	33	22
SKR 7,0 Qu bond ⁵⁾	1600	75	890	1	45	23
SKR 8,9 Qu bond ⁵⁾	1600	140	1380	1	77	26
SKR 10,3 Qu bond ⁵⁾	1600	170	1650	1	106	29
SKR 12,4 Qu bond ⁵⁾	1600	235	2300	1	160	34
SKR 15,2 Qu bond ⁵⁾	1600	330	3800	1	245	42
SKR 16,3 x 18,2 Qu bond ⁵⁾	1600	365	5100	1	320	49
SKR 18,2 Qu bond ⁵⁾	1600	380	5500	1	360	53
SKR 22,4 Qu bond ⁵⁾	1600	770	9450	1	550	72

Type	V_{RRM} V_{DRM}	$I_{T(DC)}$ @ $T_c = 80^\circ\text{C}$, $T_j = 130^\circ\text{C}$	I_{TSM} @ $T_j = 130^\circ\text{C}$ 10ms	V_{GT} @ $T_j = 25^\circ\text{C}$	I_{GT} @ $T_j = 25^\circ\text{C}$	t_q @ $T_j = 130^\circ\text{C}$
	V	A	A	V	mA	μs
1600 V - Thyristor Central Gate						
SKT 8,9 Qu ZG bond. ⁵⁾	1600	105	1000	1.98	100	150
SKT 10,3 Qu ZG bond. ⁵⁾	1600	125	1250	1.98	100	150
SKT 12,4 Qu ZG bond. ⁵⁾	1600	165	1800	1.98	100	150
SKT 13,5 Qu ZG bond. ⁵⁾	1600	185	2300	1.98	100	135
SKT 15,2 Qu ZG bond. ⁵⁾	1600	215	3200	1.98	100	150
SKT 18,2 Qu ZG bond. ⁵⁾	1600	250	5000	1.98	100	150
SKT 24,3 Qu ZG bond. ⁵⁾	1600	480	8200	1.98	150	150
1600 V - Thyristor Corner Gate						
SKT 5,6 Qu RG bond. ⁵⁾	1600	60	280	1.98	100	150
SKT 7,0 Qu RG bond. ⁵⁾	1600	75	450	1.98	100	150
SKT 8,9 Qu RG bond. ⁵⁾	1600	105	1000	1.98	100	150
SKT 10,3 Qu RG bond. ⁵⁾	1600	125	1250	1.98	100	150
SKT 12,4 Qu RG bond. ⁵⁾	1600	165	1800	1.98	100	150

Footnotes

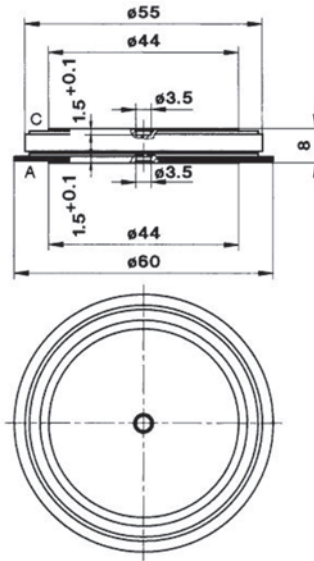
- 1) New
- 5) solderable top metallization on request

Discretes - Diodes - Capsule

Type	V_{RRM} V	I_{FAV} @ T_C A	T_C °C	I_{FSM} @ $T_j = 25^\circ C$ A	V_F @ I_F $T_j = 25^\circ C$ V	$I_F - V_F$ A	$R_{th(j-c)}$ per chip K/W	T_j °C	Case	Circuit
SKN 6000	200-600	6000	85	60000	1.30	14000	0.012	-40 ... +180	E35	

Cases

E35



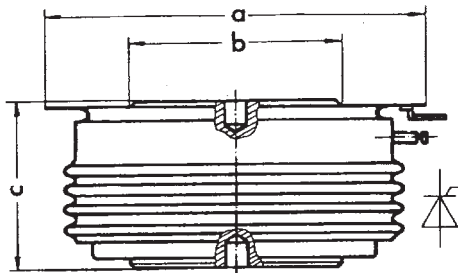
Dimensions in mm

Discretes - Thyristor - Capsule

Type	V_{RRM} V_{DRM}	I_{TAV} @ T_C	T_C	I_{TSM} @ $T_j = 25^\circ C$	$V_T @ I_T$ $T_j = 25^\circ C$	$I_T - V_T$	$R_{th(j-c)}$ @sin. 180°	T_j	Case	Circuit
	V	A	°C	A	V	A	K/W	°C		
SKT 340	1200-1800	340	82	5700	1.9	1000	0.072	-40 ... +125	B8	
SKT 551	1200-1800	550	85	9000	1.65	1500	0.047	-40 ... +125	B11	
SKT 760	1200-1800	760	80	15000	1.65	2400	0.04	-40 ... +125	B10	
SKT 1200	1200-1800	1200	85	30000	1.65	3600	0.022	-40 ... +125	B14	

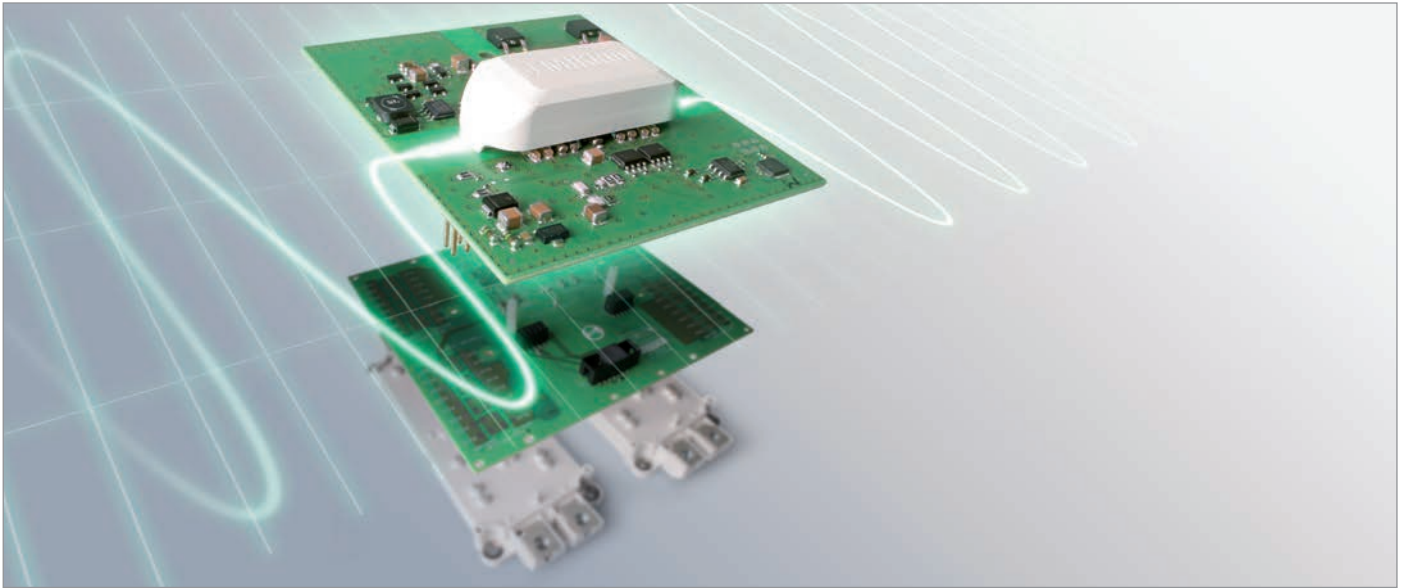
Cases

B8 ... B14



Cases	a	b	c
B 8	41	19	14
B 10	57,3	34	26
B 11	41	25	14
B 14	73	47	26

Dimensions in mm



Robust IGBT Driver

Applications

The new SKYPER 42 LJ offers the benefits of digital signal consistency while maintaining full performance. Ambitious applications such as medical or large drives are securely powered. SKYPER 32 is the perfect solution for industrial drives and process control applications. Boasting a mean time between failures of more over five million hours, the service life of this driver is triple that of standard IGBT drivers. The SKYPER platform can drive 600 V, 1200 V and 1700 V IGBT modules.

Product range driver cores

SKYPER 32/ PRO/ UL	1W
SKYPER 42 LJ	2W
SKYPER 42	4W
SKYPER 52	9W

Benefits

Robust driving technology

- Adjustable filter time for optimised performance
- High signal accuracy with +/- 1.25 ns jitter
- Safe signal transmission with rectangle pulses and seperated channels
- Low coupling capacitance with 100 kV/dt ruggedness
- Steady stabilised gate voltage for safe switching characteristics
- Safe gate control with SoftOff and adjustable failure management
- EMC with unique interlayer connection and short-pulse suppression
- Adapter boards for easy paralleling of SEMIKRON modules
- Assembly service for gate resistors and V_{CE} components for adaptor boards on request
- Adapter boards with integrated DC link measurement and excess temperature control

Driver Electronics - SEMIDRIVER

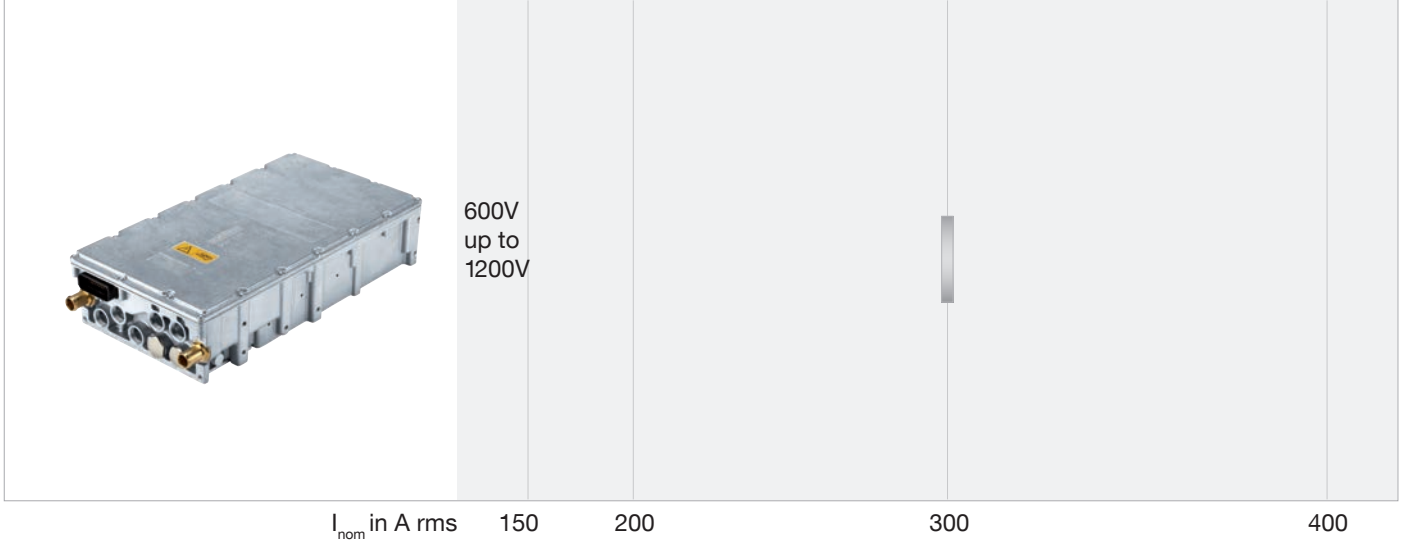
Type	Channels	V _{CE} V	V _{G(on)} V	V _{G(off)} V	I _{outPEAK} A	Q _{out/pulse} μC	f _{max} kHz	V _{isolIO} kV	dv/dt kV/μs
Driver									
SKHI 10/12 R	1	1200	15	-8	8	9.6	100	2500	75
SKHI 10/17 R	1	1700	15	-8	8	9.6	100	4000	75
SKHI 23/12 R	2	1200	15	-8	8	4.8	100	2500	75
SKHI 23/17 R	2	1700	15	-8	8	4.8	100	4000	75
SKHIT 01 R ⁵⁾	3	528	-	-	-	-	10	2500	-
Driver Core									
SKHI 21A R ⁶⁾	2	1200	15	0	8	4	50	2500	50
SKHI 22 A/B H4 R	2	1700	15	-7	8	4	50	4000	50
SKHI 22 A/B R	2	1200	15	-7	8	4	50	2500	50
SKHI 24 R	2	1700	15	-8	15	5	50	4000	50
SKYPER 32 PRO R	2	1700	15	-7	15	6.3	50	4000	50
SKYPER 32 PRO R UL	2	1700	15	-7	15	6.3	50	4000	50
SKYPER 32 R	2	1700	15	-7	15	2.5	50	4000	50
SKYPER 32 R UL	2	1700	15	-7	15	2.5	50	4000	50
SKYPER 42 R	2	1700	15	-8	30	50	100	4000	100
SKYPER 52 R	2	1700	15	-15	50	100	100	4000	100
SKHI 61 R	6	900	14.9	-6.5	2	1	50	2500	15
SKHI 71 R	7	900	14.9	-6.5	2	1	50	2500	15
Adaptor Board									
Board 1 SKYPER 32 R	2	1700	15	-7	15	2.5	50	4000	50
Board 1 SKYPER 32PRO R	2	1700	15	-7	15	6.3	50	4000	50
Board 2 // 4S SKYPER 42 R	2	1200	15	-8	30	50	100	4000	100
Board 2 generic SKYPER 42 R	2	1700	15	-8	30	50	100	4000	100
Board 2//3S SKYPER 42 R	2	1700	15	-8	30	50	100	4000	100
Board 2S SKYPER 32 PRO R Gold	2	1700	15	-7	15	6.3	50	4000	50
Board 2S SKYPER 32 R Gold	2	1700	15	-7	15	2.5	50	4000	50
Board 3S SKYPER 32 PRO R Gold	2	1700	15	-7	15	6.3	50	4000	50
Board 3S SKYPER 32 R Gold	2	1700	15	-7	15	2.5	50	4000	50
Board 4S SKYPER 32 PRO R Gold	2	1700	15	-7	15	6.3	50	4000	50
Board 4S SKYPER 32 R Gold	2	1700	15	-7	15	2.5	50	4000	50
Board 63 GB SKYPER 42 R	2	1700	15	-8	30	50	100	4000	100
Board 93 GB SKYPER 42 R	2	1700	15	-8	30	50	100	4000	100

Footnotes

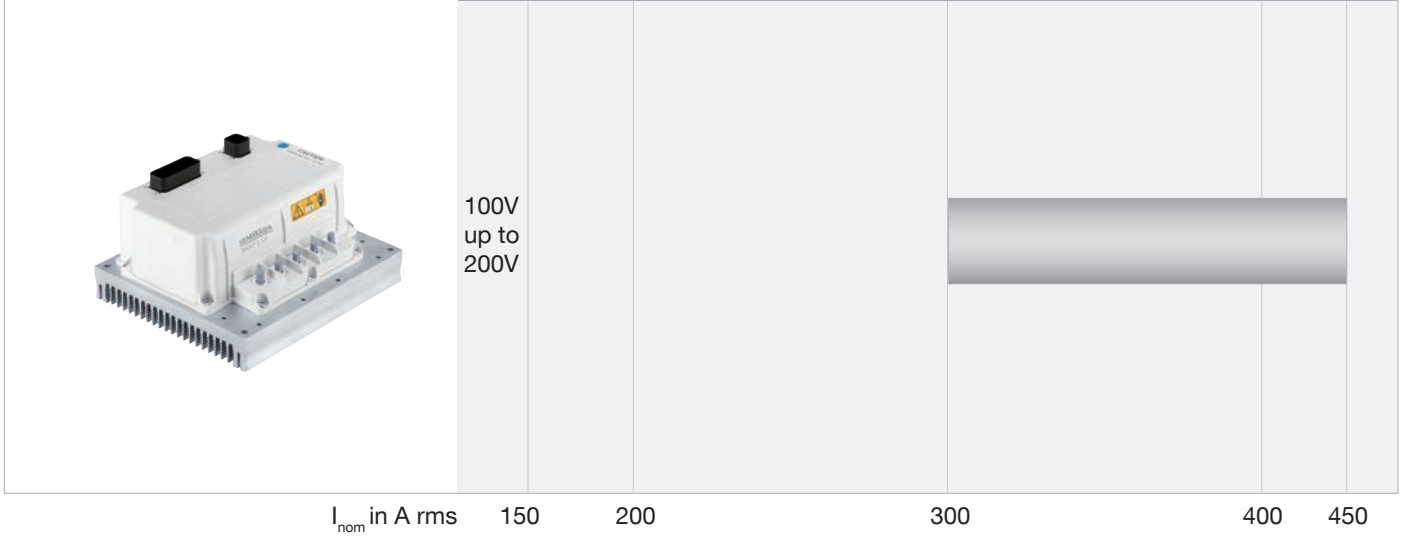
- ⁵⁾ Thyristor Driver
⁶⁾ MOSFET Driver

Systems for vehicle applications

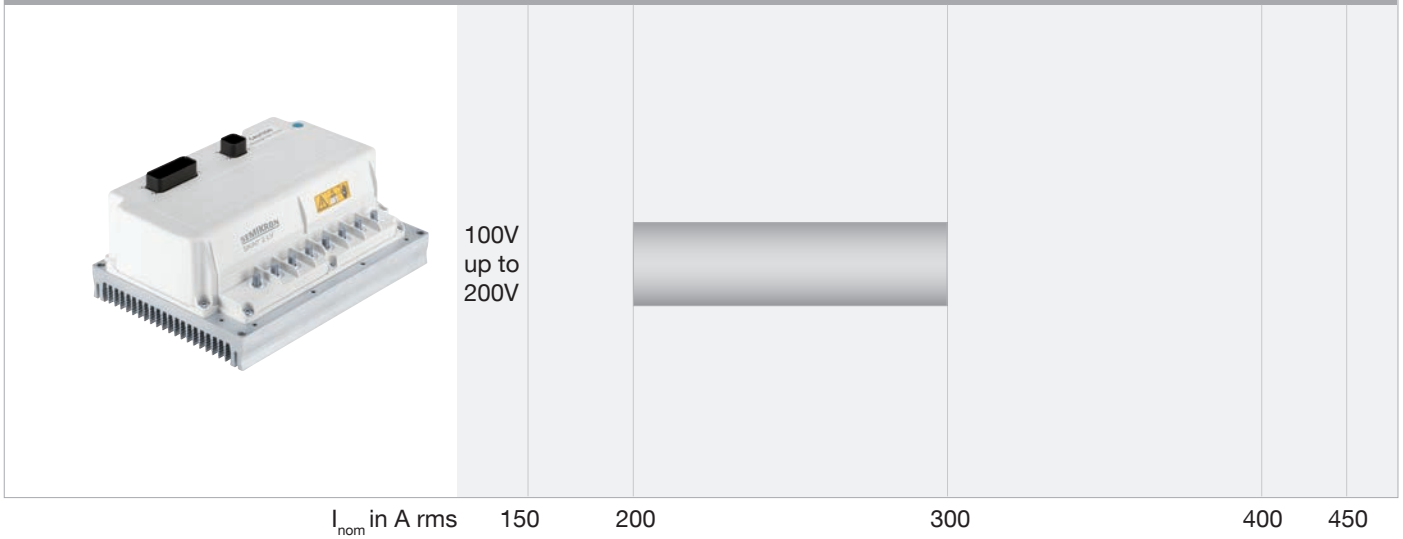
SKAI®2 IGBT Inverter



SKAI®2 MOSFET Single Inverter



SKAI®2 MOSFET Dual Inverter





3-phase inverter systems up to 250 kVA for vehicle applications

Applications

SEMIKRON's SKAI2 product platform is predestined for use in vehicle applications. The systems are designed to operate with battery voltages of 24 - 800 V and output power ratings of 10 - 250 kVA. The standard systems are supplied with low-voltage MOSFETs or high-voltage IGBTs in single or dual configuration.

Product range

The IGBT-based SKAI2 is available as a liquid-cooled 3-phase inverter in voltage classes 600 V or 1200 V, with or without DSP and a power output of up to 250 kVA. The MOSFET-based SKAI2 is available as forced-air cooled, liquid-cooled or baseplate type, for nominal battery voltages of 48V, 80V and 120V, in single or dual 3-phase inverter topology with a power output of up to 55 kVA.

Benefits

The high-voltage SKAI2 is available as a liquid-cooled 600 V or 1200 V IGBT-based 3-phase inverter system. It has been optimised for electrification of commercial vehicles and mobile working machine drive trains. This system is based on the proven, sintered, and 100 % solder-free power semiconductor technology for a power output of up to 250 kVA. It features a polypropylene film DC-link capacitor, driver electronics, a state of the art DSP controller, EMC filters and sensors for current, voltage and temperature monitoring. All system components are protected against environmental impacts by a waterproof IP67 metal case. The system can communicate with the vehicle master controller via CANbus.

The low-voltage SKAI2 MOSFET 3-phase inverter systems are available in different configurations regarding cooling, battery voltage and topology. They are mainly deployed in medium-power electric vehicle applications with a motor power of up to 55 kVA. The extremely low inductive internal power routing between DC-link capacitance and MOSFET switches results in low switching losses and a very low voltage overshoot. This allows an optimised utilisation of the maximum MOSFET drain-source voltage and hence, operation and high switching frequencies and maximum power densities. The inverter is integrated in a waterproof IP67 enclosure, except for the open power terminals. Thermal and electrical contact of SKAI2 systems are based on the proven and mature SKiiP pressure-contact technology. This results in extended service life and high load cycling capability. The SKAI2 family is fitted with a CAN bus and a large number of digital and analog I/Os for communication and control purposes. In addition, 3 PWM-controllable power outputs are installed to directly control auxiliary systems, such as cooling fans, valves or lights.

Systems - SKAI2

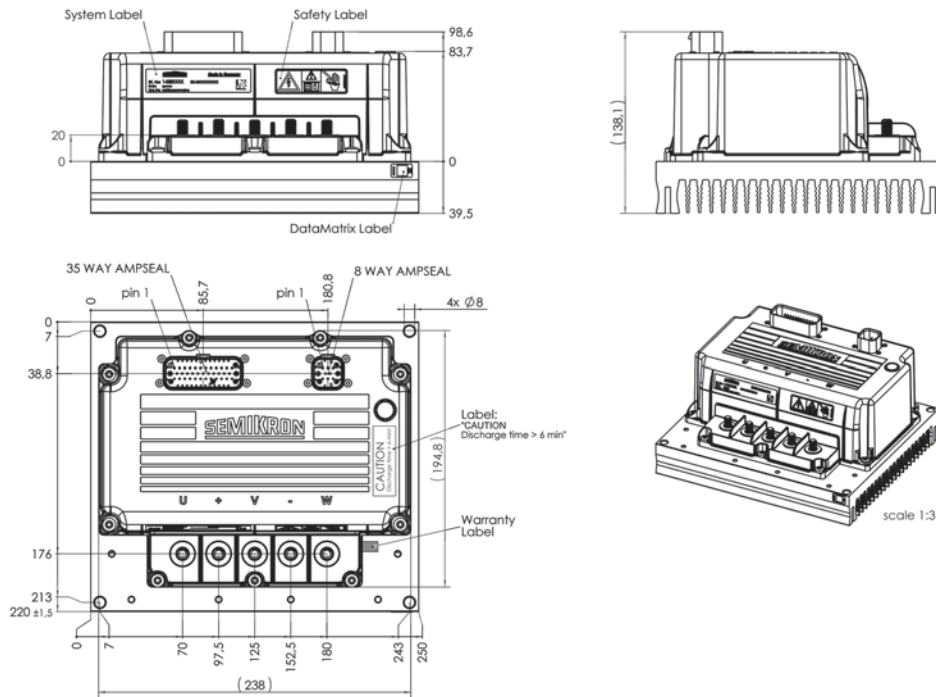
Type	V _{battery (max)} V	I _{nom} A rms	Topology	Cooling	DSP	Case	Circuit
MOSFET - Three-phase inverter							
SKAI 60 A2 MD10-P ¹⁾	72	365	3-Phase	Baseplate	Yes	3	
SKAI 70 A2 MD15-W ¹⁾	115	450	3-Phase	Liquid	Yes	2	
SKAI 50 A2 MD20-L ¹⁾	160	300	3-Phase	Forced Air	Yes	1	
SKAI 50 A2 MD20-W ¹⁾	160	350	3-Phase	Liquid	Yes	2	
SKAI 70 A2 MM15-L ¹⁾	115	250	Dual 3-Phase	Forced Air	Yes	4	
SKAI 70 A2 MM15-P ¹⁾	115	250	Dual 3-Phase	Baseplate	Yes	6	
SKAI 70 A2 MM15-W ¹⁾	115	300	Dual 3-Phase	Liquid	Yes	5	
SKAI 50 A2 MM20-L ¹⁾	160	200	Dual 3-Phase	Forced Air	Yes	4	
SKAI 50 A2 MM20-W ¹⁾	160	250	Dual 3-Phase	Liquid	Yes	5	
IGBT - Three-phase inverter							
SKAI 90 A2 GD06-WCI ¹⁾	450	300	3-Phase	Liquid	Yes	7	
SKAI 45 A2 GD12-WCI ¹⁾	800	300	3-Phase	Liquid	Yes	7	
SKAI 90 A2 GD06-WDI ¹⁾	450	300	3-Phase	Liquid	No	7	
SKAI 45 A2 GD12-WDI ¹⁾	800	300	3-Phase	Liquid	No	7	

footnotes

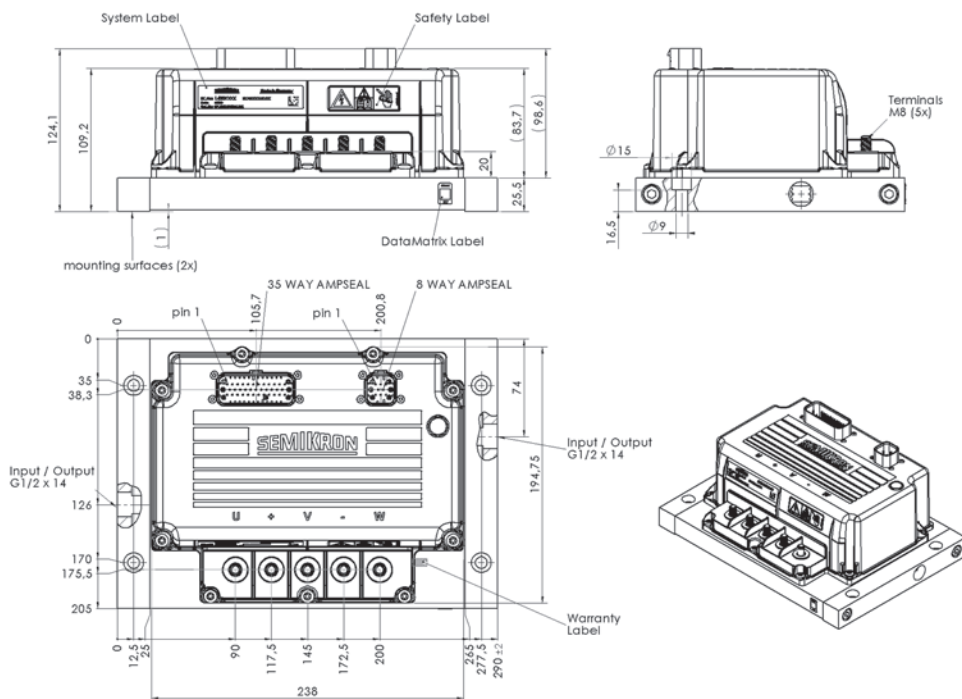
¹⁾ New

Cases

Case 1



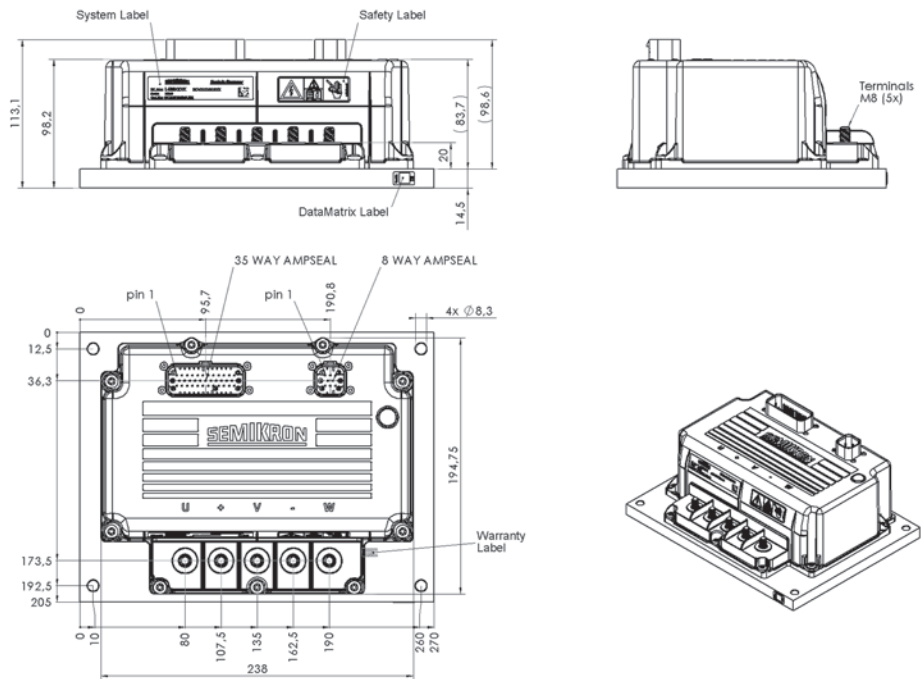
Case 2



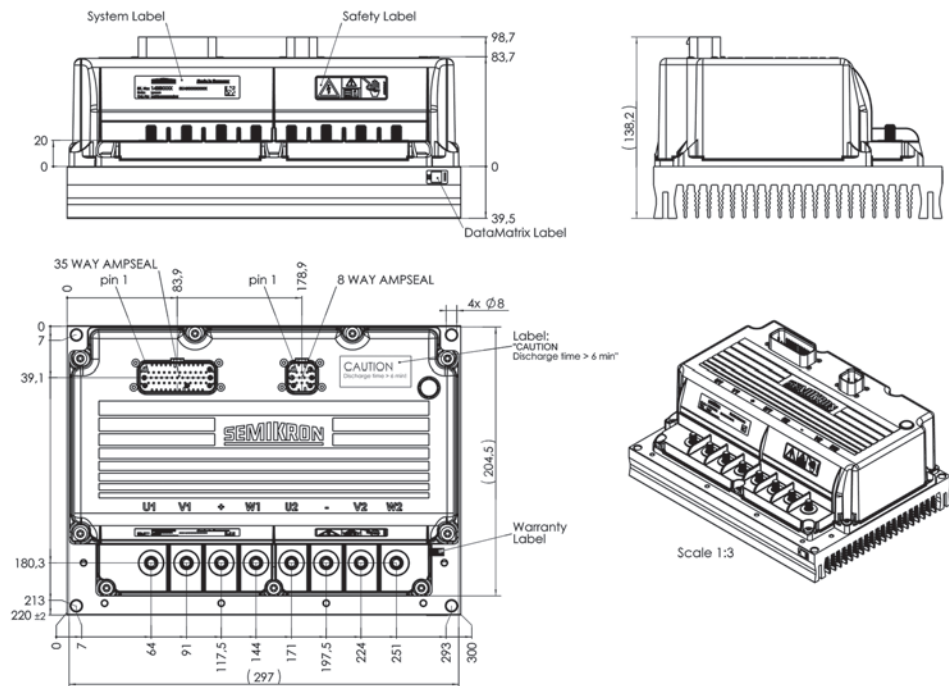
Dimensions in mm

Cases

Case 3



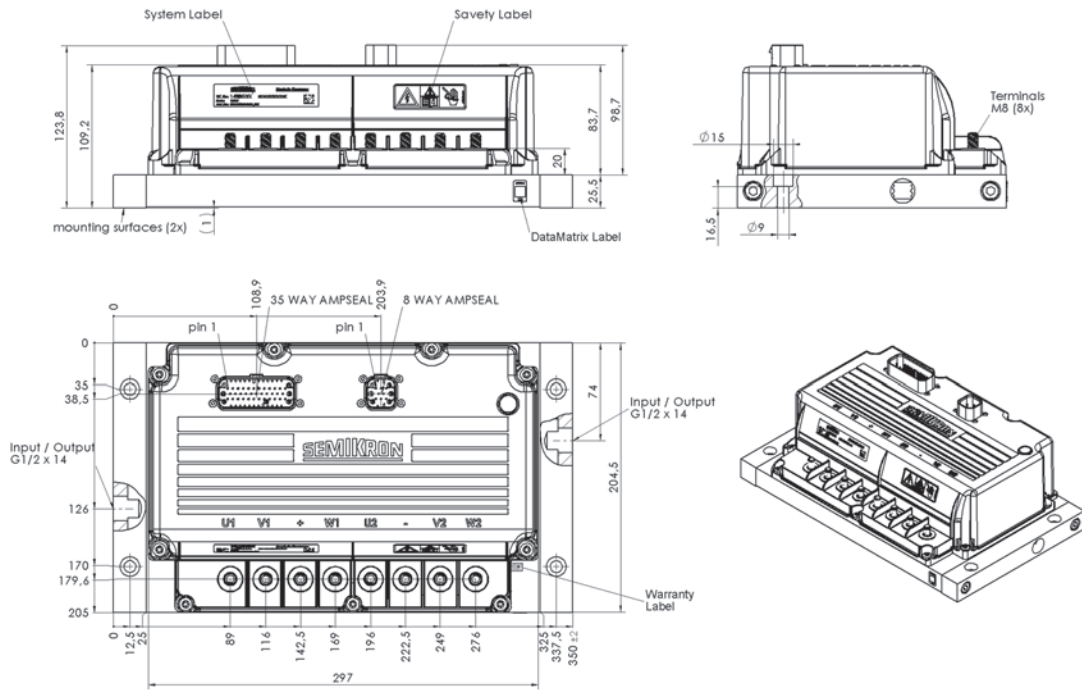
Case 4



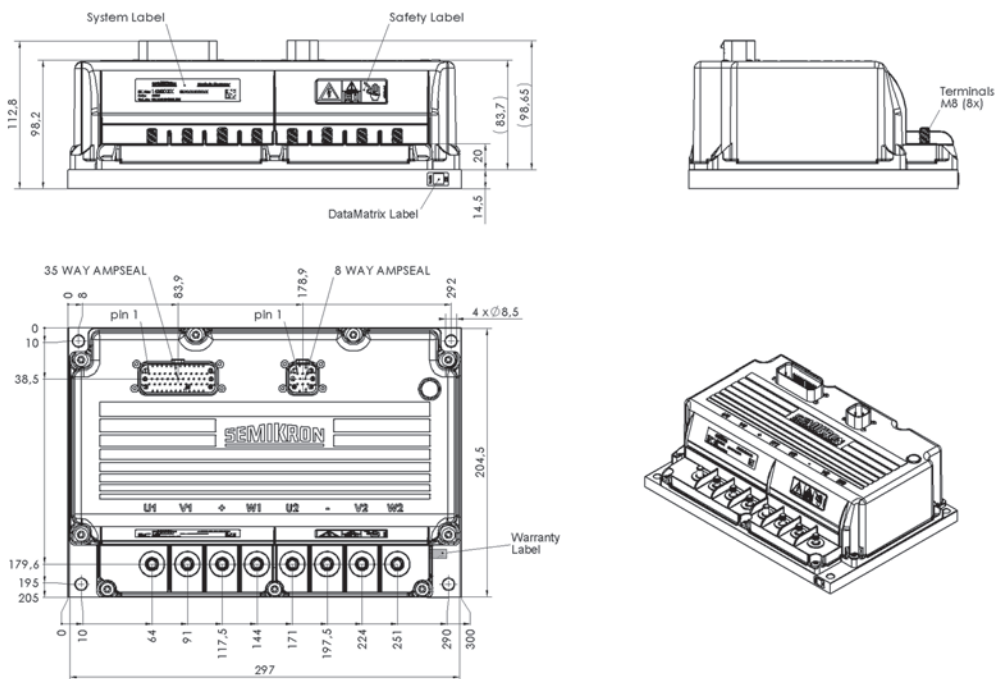
Dimensions in mm

Cases

Case 5



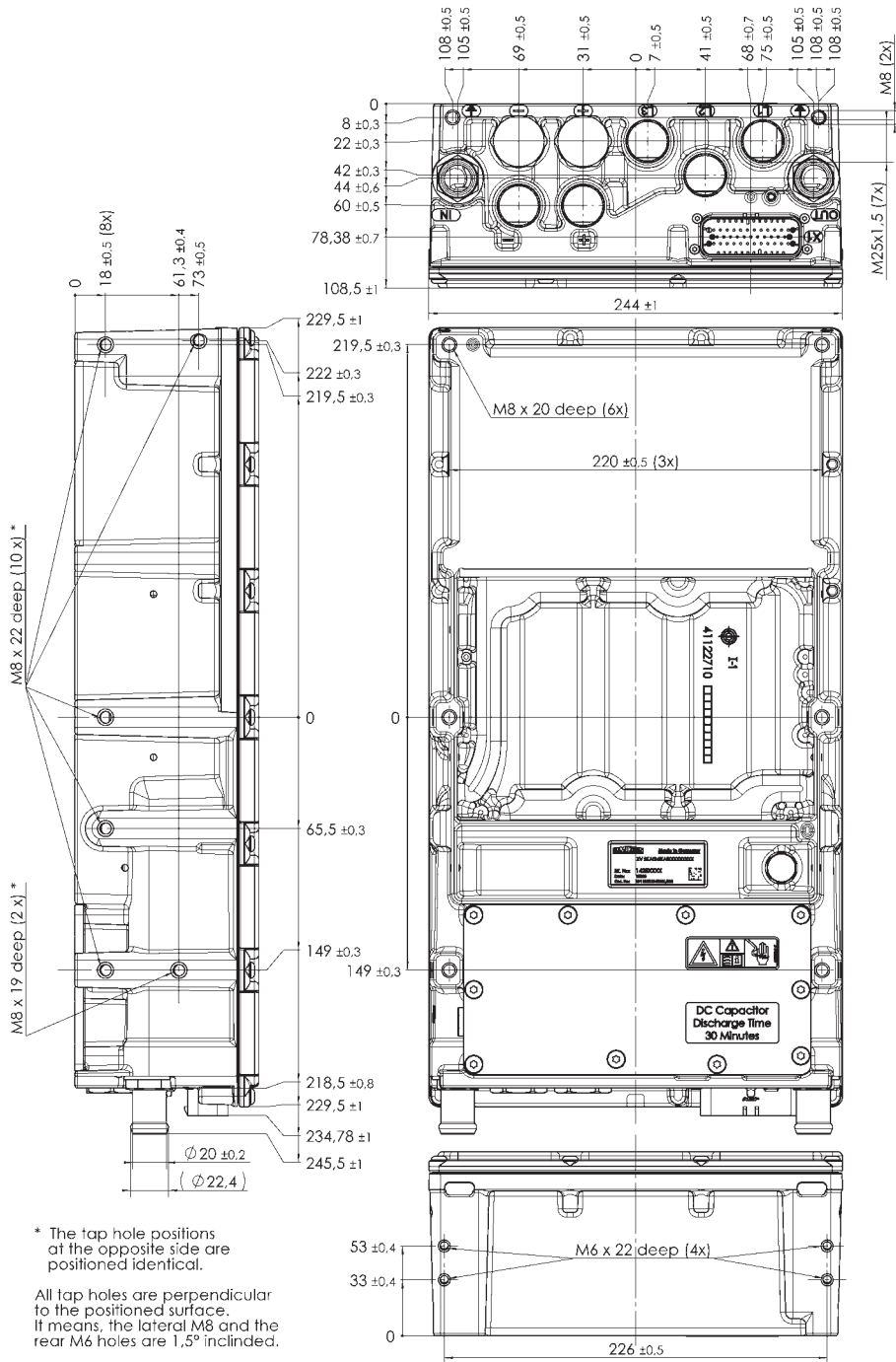
Case 6



Dimensions in mm

Cases

Case 7



Dimensions in mm

Solutions - IGBT Platforms

SEMISTACK Renewable Energy

Synchronous wind generators
 Double-fed wind generators
 Solar inverters



Power in kW 50 75 100 500 1000 2000 3000 4000 5000 6000



SKiiPRACK

Synchronous wind generators
 Double-fed wind generators
 High power AC drives



Power in kW 50 75 100 500 1000 2000 3000 4000 5000 6000



SEMIKUBE

Solar inverters
 Pump & compressor drives



Power in kW 50 75 100 500 1000 2000 3000 4000 5000 6000



Modules

Discretes

Driver Electronics

Systems for vehicle applications

Solutions

Accessories



Optimized converter for solar and wind

Applications

The new SEMISTACK RE is a new high-power converter for use in renewable energy applications, such as wind and solar power installations. The SEMISTACK RE will typically be deployed in synchronous and double-fed induction generators (DFIG) in wind turbines, as well as in central solar PV inverters. Up to four SEMISTACK RE converters can be connected in parallel and support applications of up to 6 MVA.

Benefits

The SEMISTACK RE family features the SKiiP 4, the latest generation of SEMIKRON's SKiiP intelligent power module family that integrates power components, driver and heat sink in a single case. SKiiP 4 modules allows for increased power over the predecessor generation from 1.4 to 1.7 MVA. While the current carrying capacity of the smaller SEMISTACK RE solution featuring 3-bay SKiiP modules is 900 A, the bigger 4-bay SKiiP version has a current rating of between 1000 A and 1400 A, resulting in a power density increase of 17% greater than in the predecessor version with combined SKiiP 3 modules.

Owing to the very low inductance planar DC bus bar of the SEMISTACK RE, and the internal design of the SKiiP 4, nominal DC voltage can now be extended up to 1250 Vdc with the 1700 Vdc modules, even when short circuit conditions are considered.

Signal processing on the SKiiP 4 is handled by a newly designed digital driver incorporating the standard control, monitoring and protection functions of the SKiiP 3 plus new additional functions of parameter configuration and diagnostic/fault memory. Further advantages include improved isolation, noise immunity inherent in digital control and the functionality and flexibility of the CANopen interface.

Owing to its 100% solder-free sintering process and innovative pressure contact system, the thermal cycling capability of the SKiiP 4 is increased by a factor of 5 and the maximum junction temperature is raised to 175° C. These enhancements to the SKiiP 4 are combined with long lifetime polypropylene capacitors to ensure that the SEMISTACK RE meets the severe requirements in today's grid-connected power generation applications.

Solutions - SEMISTACK Renewable Energy

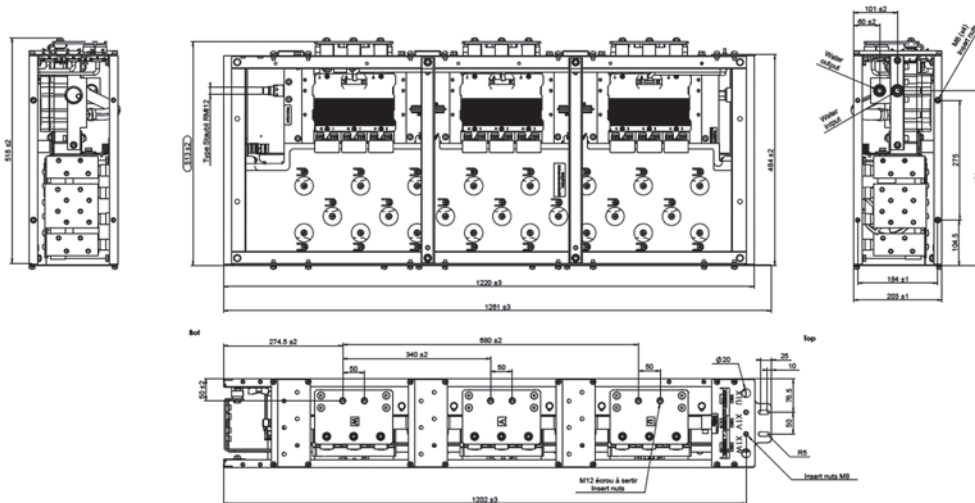
Type	V_{AC}	V_{DC}	Current	Component Family	Cooling	Heatsink profile	Iso-lated	Circuit
	V	V	A					
4-Quadrant converter								
SKS B2 120 GDD 69/11 - A11 MA PB ¹⁾	690	1100	1200	SKiiP 3	Water/ Glycol	-	yes	
SKS B2 140 GDD 69/12 U - A11 MA PB ¹⁾	690	1250	1400	SKiiP 4	Water/ Glycol	-	yes	
Three-phase inverter								
SKS B1 090 GD 69/11 - MA PB	690	1100	900	SKiiP 3	Water/ Glycol	-	yes	
SKS B2 100 GD 69/11 - MA PB	690	1100	1000	SKiiP 3	Water/ Glycol	-	yes	
SKS B2 120 GD 69/11 - MA PB	690	1100	1200	SKiiP 3	Water/ Glycol	-	yes	
SKS B2 140 GD 69/12 U - MA PB ¹⁾	690	1250	1400	SKiiP 4	Water/ Glycol	-	yes	

Footnotes

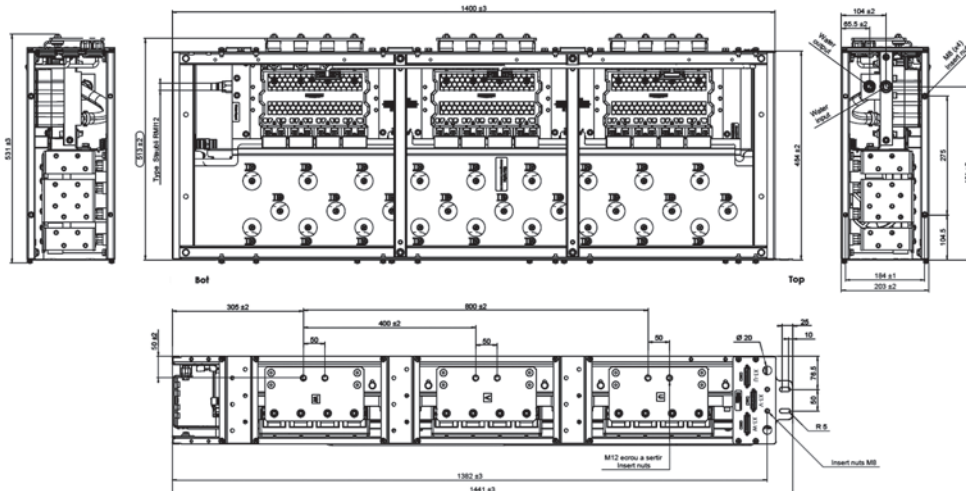
¹⁾ New

Cases

SKS 090 GD 69/11 - MA PB

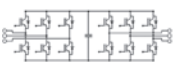


SKS B2 100 GD 69/11 - MA PB, SKS B2 120 GD 69/11 - MA PB, and SKS B2 140 GD 69/12 - MA PB



Dimensions in mm

Solutions - SKiiPRACK

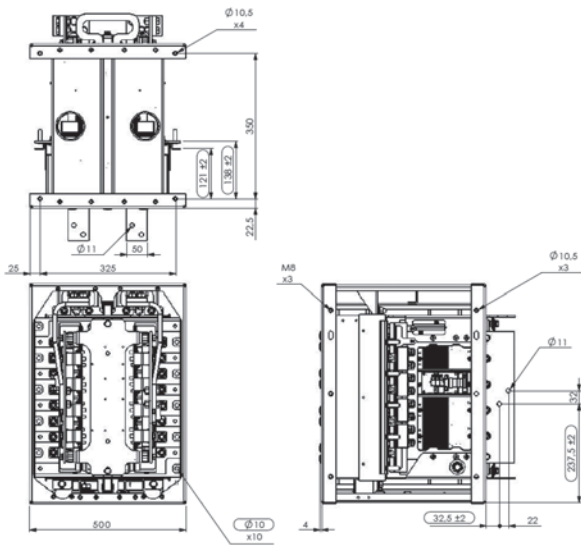
Type	V _{AC} V	V _{DC} V	Current A	Component Family	Cooling	Heatsink profile	Iso-lated	Circuit
4-Quadrant converter								
SKS C 120 GDD 69/11 - A3A WA B1B	690	1100	1200	SKiiP 3	Water/ Glycol	-	yes	
SKS C 240 GDD 69/11 - A6A MA B1C ¹⁾	690	1100	2400	SKiiP 3	Water/ Glycol	-	yes	

Footnotes

¹⁾ New

Cases

SKiiPRACK basic stack element, the CELL



3-Cell vertical integration



Dimensions in mm

Type	V_{AC}	V_{DC}	Current	Component Family	Cooling	Heatsink profile	Iso-lated	Circuit
	V	V	A					
Three-phase inverter								
IGD-1-424-P1N4-DL-FA	460	750	200	SEMITRANS	Forced-air cooled	PX 308	yes	
IGD-2-424-P1N6-DH-FA	460	750	350	SEMITRANS	Forced-air cooled	PX 308	yes	
IGD-4-424-P1F7-BL-FA	460	750	750	SEMITRANS	Forced-air cooled	PX 308	yes	
IGD-8-326-E1F12-BH-FA	460	750	1230	SEMITRANS	Forced-air cooled	PX 308	yes	
IGD-8-424-P1F9-BH-FA	460	750	1470	SEMITRANS	Forced-air cooled	PX 308	yes	
IGD-8-426-E1F12-BH-FA	460	750	1470	SEMITRANS	Forced-air cooled	PX 308	yes	
Three-phase rectifier and inverter								
IGDD6-1-326-D1616-E1N6-DL-FA	460	750	150	SEMITRANS/ SEMIPACK	Forced-air cooled	PX 308	yes	
IGDD6-1-426-D1616-E1N6-DL-FA	460	750	180	SEMITRANS/ SEMIPACK	Forced-air cooled	PX 308	yes	
IGDD6-2-326-D1616-E1F12-DH-FA	460	750	280	SEMITRANS/ SEMIPACK	Forced-air cooled	PX 308	yes	
IGDD6-2-426-D1616-E1F12-DH-FA	460	750	330	SEMITRANS/ SEMIPACK	Forced-air cooled	PX 308	yes	
IGDD6-4-326-D3816-E1F12-BL-FA	460	750	570	SEMITRANS/ SEMIPACK	Forced-air cooled	PX 308	yes	
IGDD6-4-426-D3816-E1F12-BL-FA	460	750	680	SEMITRANS/ SEMIPACK	Forced-air cooled	PX 308	yes	

Cases

SEMIKUBE size range

SIZE 0.5

SIZE 3H

SIZE 1

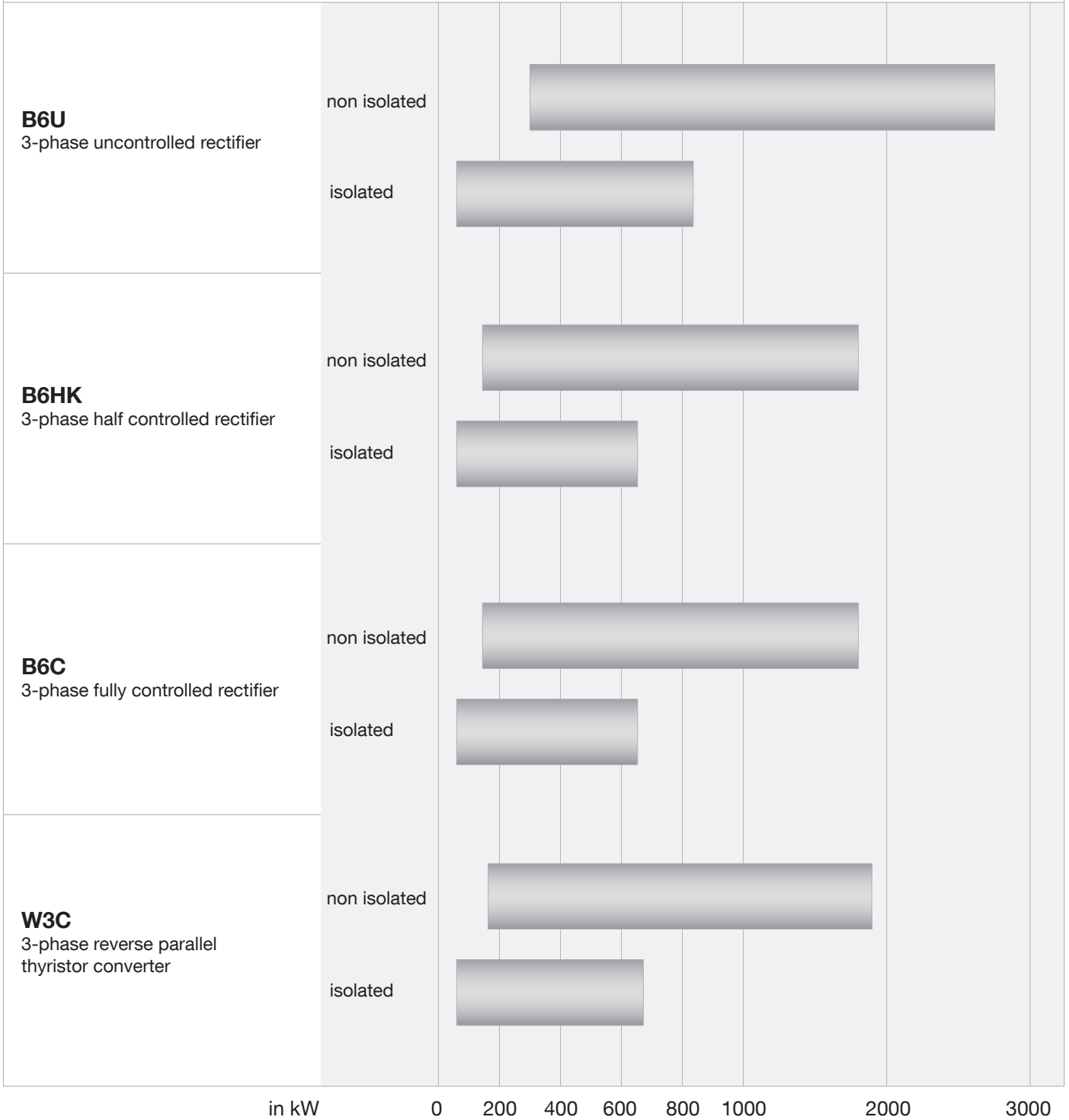
SIZE 2H

Size 1

Dimensions in mm

Solutions - Diode / Thyristor Standards

SEMISTACK CLASSICS

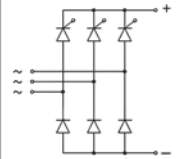


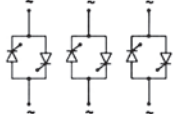
Modules
 Discretes
 Driver Electronics
 Systems for vehicle applications
 Solutions
 Accessories

Type	V _{AC} V	V _{DC} V	Current A	Component Family	Cooling	Heatsink profile	Iso- lated	Circuit
Three-phase fully-controlled thyristor bridge rectifier								
SKS 88N B6C 60 V16	500	670	88	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 88N B6C 60 V16 SU	500	670	88	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 180F B6C 120 V16	500	670	180	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 180F B6C 120 V16 SU	500	670	180	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 215N B6C 145 V16	500	670	215	Stud devices	Natural cooled	P1/150	no	
SKS 215N B6C 145 V16 SU	500	670	215	Stud devices	Natural cooled	P1/150	no	
SKS 250F B6C 170 V16	500	670	250	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 250F B6C 170 V16 SU	500	670	250	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 355N B6C 240 V16	500	670	355	Stud devices	Natural cooled	P1/200	no	
SKS 355N B6C 240 V16 SU	500	670	355	Stud devices	Natural cooled	P1/200	no	
SKS 365F B6C 245 V16	500	670	365	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 365F B6C 245 V16 SU	500	670	365	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 570F B6C 380 V16	500	670	570	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 570F B6C 380 V16 SU	500	670	570	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 640F B6C 430 V16	500	670	640	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 640F B6C 430 V16 SU	500	670	640	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 700N B6C 470 V16	500	670	700	Capsules	Natural cooled	P11/415	no	
SKS 700N B6C 470 V16 SU	500	670	700	Capsules	Natural cooled	P11/415	no	
SKS 845N B6C 570 V16	500	670	845	Capsules	Natural cooled	U3/515	no	
SKS 845N B6C 570 V16 SU	500	670	845	Capsules	Natural cooled	U3/515	no	
SKS 970F B6C 650 V16	500	670	970	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 970F B6C 650 V16 SU	500	670	970	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 1000N B6C 670 V16	500	670	1000	Capsules	Natural cooled	U3/515	no	
SKS 1000N B6C 670 V16 SU	500	670	1000	Capsules	Natural cooled	U3/515	no	
SKS 1200F B6C 800 V16	500	670	1200	Capsules	Forced-air cooled	P17/130	no	
SKS 1200F B6C 800 V16 SU	500	670	1200	Capsules	Forced-air cooled	P17/130	no	
SKS 1500F B6C 1010 V16	500	670	1500	Capsules	Forced-air cooled	P17/130	no	
SKS 1500F B6C 1010 V16 SU	500	670	1500	Capsules	Forced-air cooled	P17/130	no	
SKS 1890F B6C 1270 V16	500	670	1890	Capsules	Forced-air cooled	P18/180	no	
SKS 1890F B6C 1270 V16 ZU	500	670	1890	Capsules	Forced-air cooled	P18/180	no	
SKS 2580F B6C 1730 V16	500	670	2580	Capsules	Forced-air cooled	N4/250	no	
SKS 2580F B6C 1730 V16 ZU	500	670	2580	Capsules	Forced-air cooled	N4/250	no	

Solutions - CLASSICS

Type	V_{AC}	V_{DC}	Current	Component Family	Cooling	Heatsink profile	Isolated	Circuit
	V	V	A					
Three-phase half-controlled bridge rectifier								
SKS 88N B6HK 60 V16	500	670	88	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 88N B6HK 60 V16 SU	500	670	88	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 180F B6HK 120 V16	500	670	180	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 180F B6HK 120 V16 SU	500	670	180	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 215N B6HK 145 V16	500	670	215	Stud devices	Natural cooled	P1/150	no	
SKS 215N B6HK 145 V16 SU	500	670	215	Stud devices	Natural cooled	P1/150	no	
SKS 250F B6HK 170 V16	500	670	250	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 250F B6HK 170 V16 SU	500	670	250	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 355N B6HK 240 V16	500	670	355	Stud devices	Natural cooled	P1/200	no	
SKS 355N B6HK 240 V16 SU	500	670	355	Stud devices	Natural cooled	P1/200	no	
SKS 365F B6HK 245 V16	500	670	365	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 365F B6HK 245 V16 SU	500	670	365	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 570F B6HK 380 V16	500	670	570	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 570F B6HK 380 V16 SU	500	670	570	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 640F B6HK 430 V16	500	670	640	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 640F B6HK 430 V16 SU	500	670	640	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 700N B6HK 470 V16	500	670	700	Capsules	Natural cooled	P11/415	no	
SKS 700N B6HK 470 V16 SU	500	670	700	Capsules	Natural cooled	P11/415	no	
SKS 845N B6HK 570 V16	500	670	845	Capsules	Natural cooled	U3/515	no	
SKS 845N B6HK 570 V16 SU	500	670	845	Capsules	Natural cooled	U3/515	no	
SKS 970F B6HK 650 V16	500	670	970	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 970F B6HK 650 V16 SU	500	670	970	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 1000N B6HK 670 V16	500	670	1000	Capsules	Natural cooled	U3/515	no	
SKS 1000N B6HK 670 V16 SU	500	670	1000	Capsules	Natural cooled	U3/515	no	
SKS 1200F B6HK 800 V16	500	670	1200	Capsules	Forced-air cooled	P17/130	no	
SKS 1200F B6HK 800 V16 SU	500	670	1200	Capsules	Forced-air cooled	P17/130	no	
SKS 1500F B6HK 1010 V16	500	670	1500	Capsules	Forced-air cooled	P17/130	no	
SKS 1500F B6HK 1010 V16 SU	500	670	1500	Capsules	Forced-air cooled	P17/130	no	
SKS 1890F B6HK 1270 V16	500	670	1890	Capsules	Forced-air cooled	P18/180	no	
SKS 1890F B6HK 1270 V16 ZU	500	670	1890	Capsules	Forced-air cooled	P18/180	no	
SKS 2580F B6HK 1730 V16	500	670	2580	Capsules	Forced-air cooled	N4/250	no	
SKS 2580F B6HK 1730 V16 ZU	500	670	2580	Capsules	Forced-air cooled	N4/250	no	



Type	V _{AC} V	V _{DC} V	Current A	Component Family	Cooling	Heatsink profile	Iso- lated	Circuit
Three-phase reverse parallel thyristor converter								
SKS 67N W3C 60 V16 ¹⁾	500	-	67	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 67N W3C 60 V16 SU ¹⁾	500	-	67	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 140F W3C 120 V16	500	-	140	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 140F W3C 120 V16 SU ¹⁾	500	-	140	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 170N W3C 150 V16 ¹⁾	500	-	170	Stud devices	Natural cooled	P1/150	no	
SKS 170N W3C 150 V16 SU ¹⁾	500	-	170	Stud devices	Natural cooled	P1/150	no	
SKS 195F W3C 170 V16 ¹⁾	500	-	195	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 195F W3C 170 V16 SU ¹⁾	500	-	195	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 275N W3C 240 V16 ¹⁾	500	-	275	Stud devices	Natural cooled	P1/200	no	
SKS 275N W3C 240 V16 SU ¹⁾	500	-	275	Stud devices	Natural cooled	P1/200	no	
SKS 290F W3C 250 V16 ¹⁾	500	-	290	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 290F W3C 250 V16 SU ¹⁾	500	-	290	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 450F W3C 390 V16 ¹⁾	500	-	450	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 450F W3C 390 V16 SU ¹⁾	500	-	450	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 520F W3C 450 V16 ¹⁾	500	-	520	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 520F W3C 450 V16 SU ¹⁾	500	-	520	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 545N W3C 470 V16 ¹⁾	500	-	545	Capsules	Natural cooled	P11/415	no	
SKS 545N W3C 470 V16 SU ¹⁾	500	-	545	Capsules	Natural cooled	P11/415	no	
SKS 650N W3C 560 V16 ¹⁾	500	-	650	Capsules	Natural cooled	U3/515	no	
SKS 650N W3C 560 V16 SU ¹⁾	500	-	650	Capsules	Natural cooled	U3/515	no	
SKS 760F W3C 660 V16 ¹⁾	500	-	760	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 760F W3C 660 V16 SU ¹⁾	500	-	760	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 780N W3C 675 V16 ¹⁾	500	-	780	Capsules	Natural cooled	U3/515	no	
SKS 780N W3C 675 V16 SU ¹⁾	500	-	780	Capsules	Natural cooled	U3/515	no	
SKS 950F W3C 825 V16 ¹⁾	500	-	950	Capsules	Forced-air cooled	P17/130	no	
SKS 950F W3C 825 V16 SU ¹⁾	500	-	950	Capsules	Forced-air cooled	P17/130	no	
SKS 1180F W3C 1020 V16 ¹⁾	500	-	1180	Capsules	Forced-air cooled	P17/130	no	
SKS 1180F W3C 1020 V16 SU ¹⁾	500	-	1180	Capsules	Forced-air cooled	P17/130	no	
SKS 1540F W3C 1335 V16 ¹⁾	500	-	1540	Capsules	Forced-air cooled	P18/180	no	
SKS 1540F W3C 1335 V16 SU ¹⁾	500	-	1540	Capsules	Forced-air cooled	P18/180	no	
SKS 2150F W3C 1860 V16 ¹⁾	500	-	2150	Capsules	Forced-air cooled	N4/250	no	
SKS 2150F W3C 1860 V16 ZU ¹⁾	500	-	2150	Capsules	Forced-air cooled	N4/250	no	

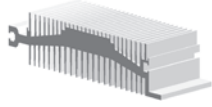
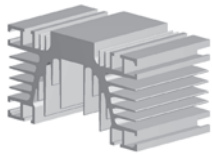
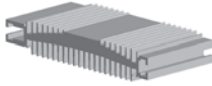
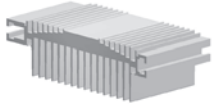

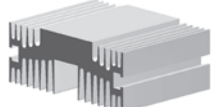
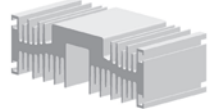

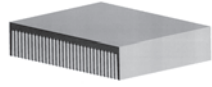
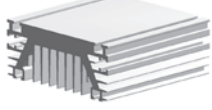
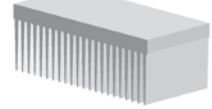
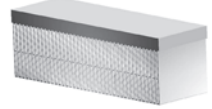
Solutions - CLASSICS

Type	V_{AC}	V_{DC}	Current	Component Family	Cooling	Heatsink profile	Isolated	Circuit
	V	V	A					
Three-phase uncontrolled diode bridge rectifier								
SKS 91N B6U 60 V16	500	670	91	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 91N B6U 60 V16 SU	500	670	91	SEMIPACK 1	Natural cooled	P3/180	yes	
SKS 185F B6U 125 V16	500	670	185	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 185F B6U 125 V16 SU	500	670	185	SEMIPACK 1	Forced-air cooled	P3/180	yes	
SKS 290F B6U 195 V16	500	670	290	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 290F B6U 195 V16 SU	500	670	290	SEMIPACK 2	Forced-air cooled	P3/265	yes	
SKS 425N B6U 285 V16	500	670	425	Stud devices	Natural cooled	P1/150	no	
SKS 425N B6U 285 V16 SU	500	670	425	Stud devices	Natural cooled	P1/150	no	
SKS 430F B6U 290 V16	500	670	430	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 430F B6U 290 V16 SU	500	670	430	SEMIPACK 2	Forced-air cooled	P16/200	yes	
SKS 535N B6U 360 V16	500	670	535	Stud devices	Natural cooled	P1/200	no	
SKS 535N B6U 360 V16 SU	500	670	535	Stud devices	Natural cooled	P1/200	no	
SKS 660F B6U 440 V16	500	670	660	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 660F B6U 440 V16 SU	500	670	660	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 850F B6U 570 V16	500	670	850	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 850F B6U 570 V16 SU	500	670	850	SEMIPACK 3	Forced-air cooled	P16/200	yes	
SKS 1185N B6U 795 V16	500	670	1185	Capsules	Natural cooled	P11/415	no	
SKS 1185N B6U 795 V16 SU	500	670	1185	Capsules	Natural cooled	P11/415	no	
SKS 1220F B6U 820 V16	500	670	1220	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 1220F B6U 820 V16 SU	500	670	1220	SEMIPACK 5	Forced-air cooled	P16/300	yes	
SKS 1630N B6U 1090 V16	500	670	1630	Capsules	Natural cooled	U3/515	no	
SKS 1630N B6U 1090 V16 ZU	500	670	1630	Capsules	Natural cooled	U3/515	no	
SKS 1910N B6U 1280 V16	500	670	1910	Capsules	Natural cooled	U3/515	no	
SKS 1910N B6U 1280 V16 ZU	500	670	1910	Capsules	Natural cooled	U3/515	no	
SKS 1950F B6U 1305 V16	500	670	1950	Capsules	Forced-air cooled	P17/130	no	
SKS 1950F B6U 1305 V16 ZU	500	670	1950	Capsules	Forced-air cooled	P17/130	no	
SKS 2300F B6U 1540 V16	500	670	2300	Capsules	Forced-air cooled	P18/180	no	
SKS 2300F B6U 1540 V16 ZU	500	670	2300	Capsules	Forced-air cooled	P18/180	no	
SKS 4015F B6U 2690 V16	500	670	4015	Capsules	Forced-air cooled	N4/250	no	

Footnotes

¹⁾ New

Accessories - Heatsinks

Type	Suitable for	R_{thsa} natural cooling K/W	R_{thsa} forced air or water cooling K/W	w kg	w kg/m	Picture
Forced-air cooled						
N 4	Capsules	-	0.04	-	25.1	
P 11	Capsules	0.2	0.05	-	15	
P 17	Capsules	0.45	0.12	-	10.6	
P 18	Capsules	0.37	0.08	-	12.2	
P 8⁵⁾	Capsules	0.35	0.07	-	9.6	
P 8,5⁵⁾	Capsules	0.3	0.08	-	9.5	
P 9⁵⁾	Capsules	0.21	0.06	-	17.8	
U 3	Capsules	0.14	0.06	-	23.7	
P 21⁵⁾	Isolated base modules	-	0.02	-	40.8	
R 4A	Isolated base modules	1.4	0.38	0.6	-	
P 16	SKiiP or modules	-	0.06	-	23.5	
Px 308⁵⁾	SKiiP or modules	-	0.013	-	12.2	

Modules

Discretes


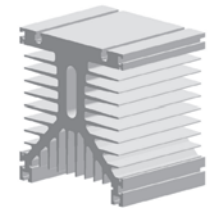
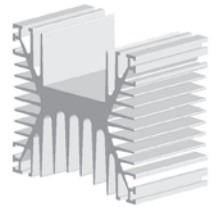
Driver Electronics

Systems for vehicle applications

Solutions

Accessories



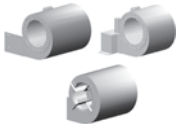

Accessories - Heatsinks

Type	Suitable for	R_{thsa} natural cooling K/W	R_{thsa} forced air or water cooling K/W	w kg	w kg/m	Picture
Forced-air cooled						
P 1	Studs or modules	0.7	0.4	-	11.3	
P 3	Isolated base modules	0.45	0.14	-	17.6	
Natural cooled						
P 4 ⁵⁾	Stud device	0.27	-	-	20.6	

footnotes

⁵⁾ Non standard item, available on request only, typical minimum batch quantities of 60 pieces will apply

Accessories - Fans

Type	V _{in} V	f Hz	V _{air} / t m ³ /h	P _{max} V	T _{Amax} °C	w kg	Noise dB	Picture
Axial Fans								
SKF 3-230-01	230	50	159 / 190	15 / 14	70	0.55	37 / 41	
Centrifugal Fans								
SKF 17A-230-11	230	50	850 / 930	110 / 120	70	2	74	
SKF N4-230-01	230	50	1500 / 1700	210 / 280	80 / 70	3.1	76 / 78	
Radial Fans								
SKF 16A-230-11	230	50	615 / 575	135 / 154	50 / 40	3.6	55 / 57	
SKF 16O-230-02	230	50	1150	260	40	4.2	-	
SKF 16B-230-01	230	50	640	167	70	3.75	58	

Modules

Discretes

Driver Electronics

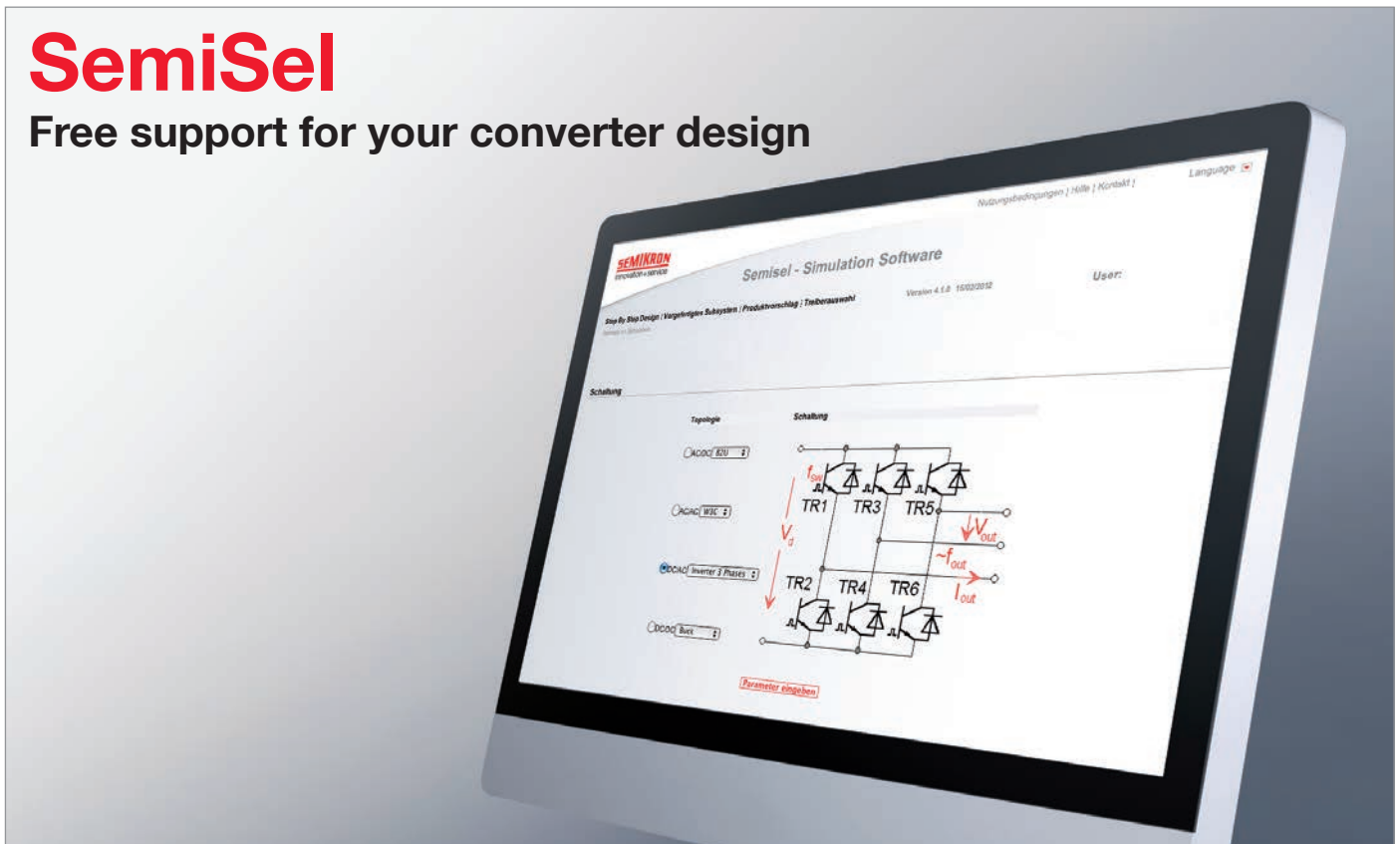
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Solutions

Accessories

SemiSel

Free support for your converter design



Applications

SemiSel is the SEMIKRON online calculation and simulation tool for losses, temperatures and optimal choice of power electronic components (www.semikron.com). Due to the ever-present cost pressure, the optimal choice of power conductor components is a must-have. The days when a module was purchased solely on the basis of its nominal current are over. Today, increased product diversity in the field of power semiconductors calls for comparisons beyond the information contained in data sheets. Only a comparison under application-oriented conditions, such as voltage level, switching frequency or cooling conditions, can demonstrate differences in the performance of the devices available. Miniaturisation combined with higher power densities makes it essential to have the right thermal design for heat dissipation.

Benefits

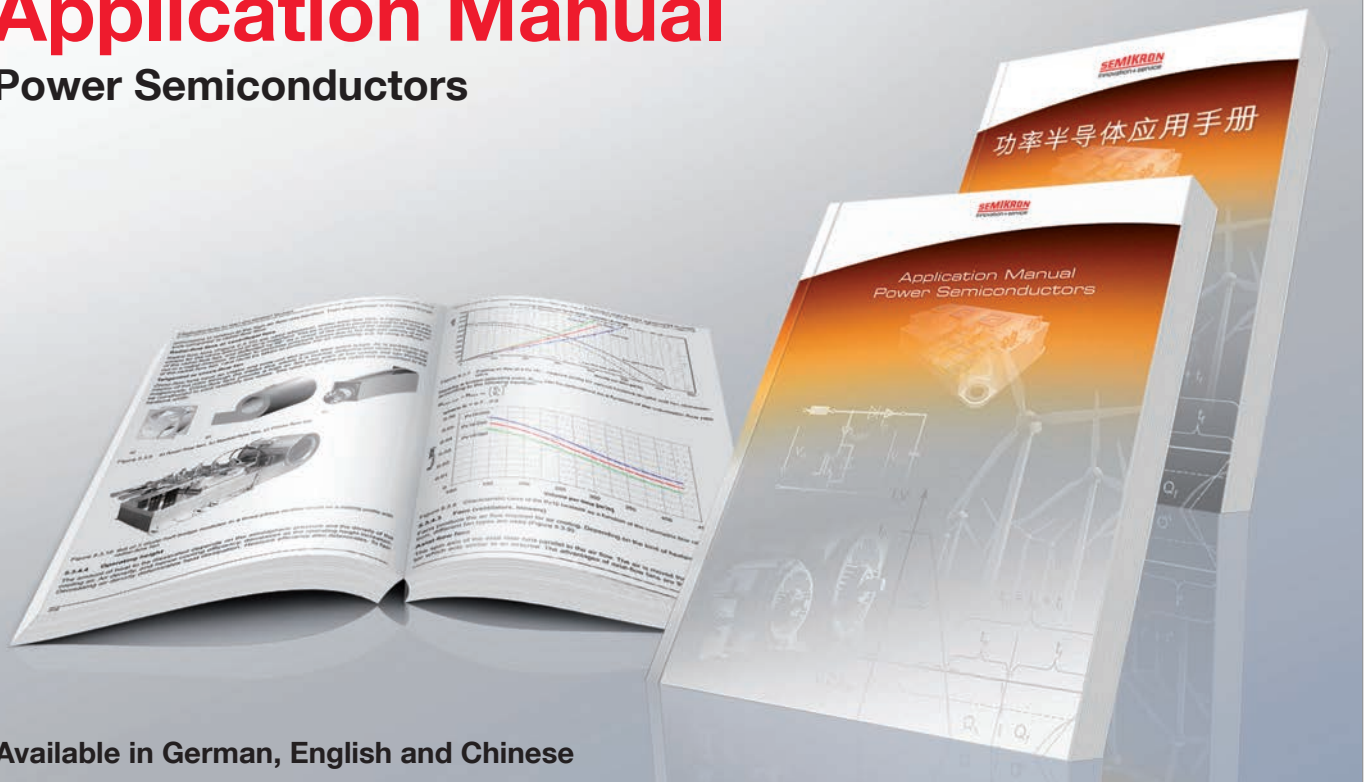
The risk arising from variations in both component and electrical circuit parameters should be considered in proper circuit design. These facts are only a few of the many points that need to be considered when developing a power electronics system. And this is where efficient support is provided by SemiSel to enable developers to make the right decision. Many manufacturers of power semiconductors offer tools for device selection, yet, SemiSel is still the most comprehensive free tool of its kind that can be used to investigate different power electronic circuits under different operating conditions. This programme has been available online since 2001, and it has been continually improved and expanded since its introduction. It provides a good compromise of user-friendliness, applications and speed. The calculation functions range from product proposal for nominal operating conditions to drivers and heat sink specifications and product selections for specific overload conditions and complex calculations, such as complete load cycles that take into account temperature cycling problems.

Abbreviations

Acronym	English
E_{off}	Energy dissipation during turn-off
E_{on}	Energy dissipation during turn-on
E_{rr}	Energy dissipation during reverse recovery (diode)
f	Operating frequency
f_{max}	Maximum frequency
I_C	Continuous collector current
I_{Cnom}	Nominal collector current
I_D	Direct output current (of a rectifier connection)
I_D	Continuous drain current (MOSFET)
I_F	Forward current (actual value)
I_{FAV}	Mean forward current
I_{FSM}	Surge forward current
I_{GT}	Minimum guaranteed gate trigger current
$I_{outPEAK}$	Output peak current (driver)
$I_{overload}$	Overload current for a specified time
i_T	On-State current (instantaneous value)
I_{TAV}	Mean on-state current
I_{TSM}	Surge on-state current
Qout/pulse	Output charge per pulse (Driver)
Q_{rr}	Reverse recovery charge
$R_{DS(on)}$	Drain-source on-resistance (MOSFET)
r_T	On-state slope resistance, forward slope resistance (Thyristor)
$R_{th(c-s)}$	thermal resistance case to heat sink
$R_{th(j-a)}$	Thermal resistance junction to ambient
$R_{th(j-c)}$	Thermal resistance junction to case
$R_{th(j-s)}$	Thermal resistance junction to sink
$R_{th(s-a)}$	Thermal resistance heat sink to ambient
T_c	Case temperature
T_j	Junction temperature
t_q	Circuit commutated turn-off time (thyristor)
T_s	Heatsink temperature
V_{air}/t	Air flow
V_{CE}	Collector-emitter voltage
V_{CEsat}	Collector-emitter saturation voltage
V_{DRM}	Repetitive peak off-state voltage
V_{DS}	Drain-source voltage
V_F	Forward voltage
$V_{G(off)}$	Turn-off gate voltage level (driver)
$V_{G(on)}$	Turn-on gate voltage level (driver)
V_{GT}	Gate trigger voltage
V_{in}	Input voltage
$V_{isol(IO)}$	Isolation test voltage (r.m.s. /1 min.) input-output (driver)
V_{RRM}	Repetitive peak reverse voltage
V_T	On-state voltage (Thyristor)
W	Weight

Application Manual

Power Semiconductors



Available in German, English and Chinese

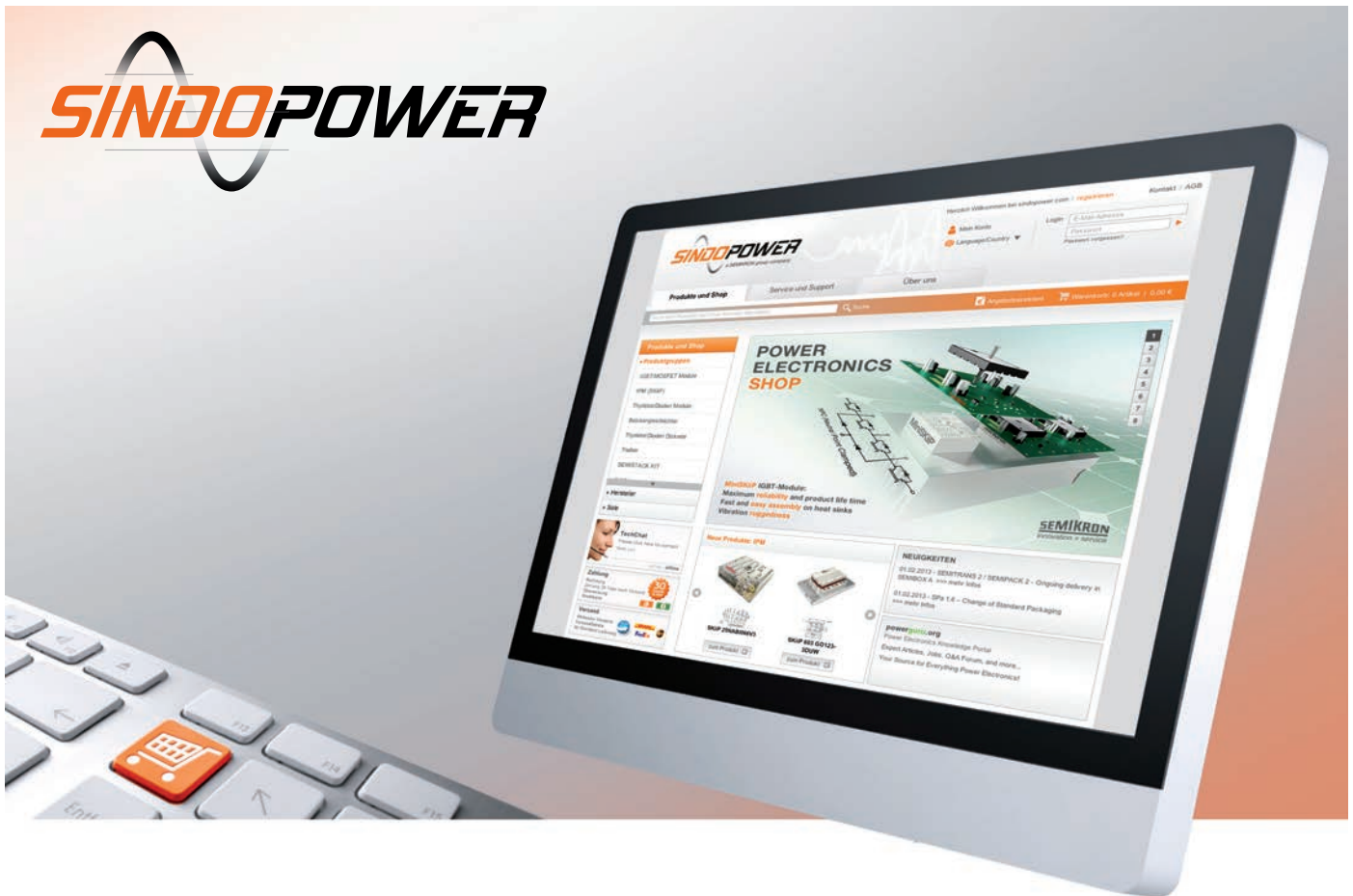
465 pages of acquired knowledge

IGBT's and MOSFET's integrated in power modules are the key components of power electronic circuits today and are continuously finding their way into new fields of application. This goes hand in hand with the ever increasing call for line rectifier diodes and thyristors as a cost-effective way of connecting the circuits to the power grid. The aim of the application manual is to provide users with support in selecting and using such devices. The manual contains basic background knowledge on semiconductors in order to enable a better understanding of application possibilities and limits. More in-depth explanations are given on packaging and assembly technologies, because of the major influence they have on module properties and limitations in field applications. Statements on reliability data, life cycle analyses and key test processes round off the chapter. The Application Manual also explains the structure of datasheets and provides notes to help users better understand datasheet parameters.

The Application Manual contains detailed application-related information on electrical configuration under important operating conditions, driver and protection elements for semiconductors; thermal dimensioning and cooling, tips on parallel and series connection, assembly tips for optimized power layouts with regard to parasitic elements and the requirements arising from specific ambient conditions.

This book is written for users and provides help with component selection and design-in work. It couples a vast wealth of experience with detailed practical knowledge, the result being a vast pool of information which up till now has been spread across various individual articles or in the minds of experts only.

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